RENESAS

RL78/L13

RENESAS MCU

Datasheet

R01DS0168EJ0232 Rev.2.32 Jan 31, 2025

Integrated LCD controller/driver, True Low Power Platform (as low as 71 µA/MHz, and 0.61 µA for RTC + LVD), 1.6 V to 5.5 V operation, 16 to 128 Kbyte Flash, 31 DMIPS at 24 MHz, for All LCD Based Applications

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- V_{DD} = single power supply voltage of 1.6 to 5.5 V which can operate a 1.8 V device at a low voltage
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.04167 μs: @ 24 MHz operation with highspeed on-chip oscillator) to ultra-low speed (30.5 μs: @ 32.768 kHz operation with subsystem clock)
- Address space: 1 MB
- General-purpose registers: (8-bit register × 8) × 4 banks
- On-chip RAM: 1 to 8 KB

Code flash memory

- Code flash memory: 16 to 128 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

Data flash memory

- Data flash memory: 4 KB
- Back ground operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: VDD = 1.8 to 5.5 V

High-speed on-chip oscillator

- Select from 48 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: ±1.0 % (V_{DD} = 1.8 to 5.5 V, T_A = -20 to +85°C)

Operating ambient temperature

- T_A = -40 to +85°C (A: Consumer applications)
- $T_A = -40$ to $+105^{\circ}C$ (G: Industrial applications)

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 14 levels)

DMA (Direct Memory Access) controller

- 4 channels
- Number of clocks during transfer between 8/16-bit SFR and internal RAM: 2 clocks

Multiplier and divider/multiply-accumulator

- 16 bits × 16 bits = 32 bits (Unsigned or signed)
- 32 bits ÷ 32 bits = 32 bits (Unsigned)
- 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)

Serial interface

- Simplified SPI (CSI Note1): 2 channels
- UART/UART (LIN-bus supported): 3, 4 channels/1 channel
- I²C/Simplified I²C communication: 1 channel/2 channels

Timer

- 16-bit timer: 8 channels (with remote control output function)
- 16-bit timer KB20 (IH): 1 channel
 (IH-only PWM output function)
- 12-bit interval timer: 1 channel
- Real-time clock 2: 1 channel (calendar for 99 years, alarm function, and clock correction function)
- Watchdog timer: 1 channel (operable with the dedicated lowspeed on- chip oscillator)

A/D converter

- 8/10-bit resolution A/D converter (VDD = 1.6 to 5.5 V)
- Analog input: 9 to 12 channels
- \bullet Internal reference voltage (1.45 V) and temperature sensor^{Note 2}

Comparator

- 2 channels
- Operation mode: Comparator high-speed mode, comparator low-speed mode, or window mode
- External reference voltage and internal reference voltage are selectable

LCD controller/driver

- Segment signal output: 36 (32)^{Note 3} to 51 (47)^{Note 3}
- Common signal output: 4 (8)Note 3
- Internal voltage boosting method, capacitor split method, and external resistance division method are switchable

I/O port

- I/O port: 49 to 65 (N-ch open drain I/O [withstand voltage of 6 V]: 2, N-ch open drain I/O [VDD withstand voltage]: 12 to 18)
- Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5/3 V device
- On-chip key interrupt function
- On-chip clock output/buzzer output controller

Others

- On-chip BCD (binary-coded decimal) correction circuit
- **Notes 1.** Although the CSI function is generally called SPI, it is also called CSI in this product, so it is referred to as such in this manual.
 - 2. Can be selected only in HS (high-speed main) mode
 - **3.** The values in parentheses are the number of signal outputs when 8 com is used.
- Remark The functions mounted depend on the product. See **1.6 Outline of Functions**.

* There are differences in specifications between every product. Please refer to specification for details.

• ROM, RAM capacities

Flash ROM	Data Flash	RAM	RL78	3/L13
			64 pins	80 pins
128 KB	4 KB	8 KB ^{Note}	R5F10WLG	R5F10WMG
96 KB	4 KB	6 KB	R5F10WLF	R5F10WMF
64 KB	4 KB	4 KB	R5F10WLE	R5F10WME
48 KB	4 KB	2 KB	R5F10WLD	R5F10WMD
32 KB	4 KB	1.5 KB	R5F10WLC	R5F10WMC
16 KB	4 KB	1 KB	R5F10WLA	R5F10WMA

Note This is about 7 KB when the self-programming function and data flash function are used. (For details, see **CHAPTER 3** in the RL78/L13 User's Manual.)



1.2 List of Part Numbers

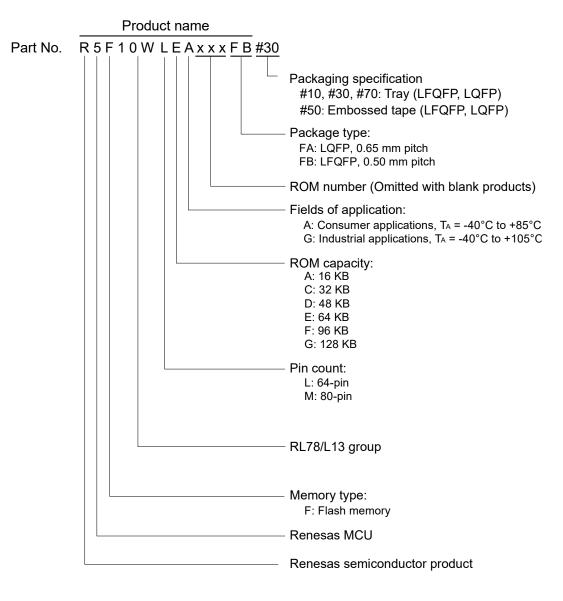


Figure 1-1. Part Number, Memory Size, and Package of RL78/L13



Pin Count	Package	Data Flash	Fields of	Ordering Part	Number	RENESAS CODE
			Application ^{Note}	part number	Packaging specification	
64 pins	64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)	Mounted	A	R5F10WLAAFA, R5F10WLCAFA, R5F10WLDAFA, R5F10WLEAFA, R5F10WLFAFA, R5F10WLGAFA	#10, #30, #50, #70	PLQP0064JA-A PLQP0064JB-A
	64-pin plastic LFQFP (10 × 10	Mounted	A	R5F10WLAAFB, R5F10WLCAFB,	#10, #50, #70	PLQP0064KB-C PLQP0064KL-A
	mm, 0.5 mm pitch)			R5F10WLDAFB, R5F10WLEAFB, R5F10WLFAFB, R5F10WLGAFB	#30	PLQP0064KB-C
			G	R5F10WLAGFB, R5F10WLCGFB,	#10, #50, #70	PLQP0064KB-C PLQP0064KL-A
				R5F10WLDGFB, R5F10WLEGFB, R5F10WLFGFB, R5F10WLGGFB	#30	PLQP0064KB-C
80 pins	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	Mounted	A	R5F10WMAAFA, R5F10WMCAFA, R5F10WMDAFA, R5F10WMEAFA, R5F10WMFAFA, R5F10WMGAFA	#10, #30, #50, #70	PLQP0080JB-E
	80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)	Mounted	A	R5F10WMAAFB, R5F10WMCAFB, R5F10WMDAFB,	#10, #50, #70	PLQP0080KB-B PLQP0080KE-A PLQP0080KJ-A
				R5F10WMEAFB, R5F10WMFAFB, R5F10WMGAFB,	#30	PLQP0080KB-B
			G	R5F10WMAGFB, R5F10WMCGFB, R5F10WMDGFB,	#10, #50, #70	PLQP0080KB-B PLQP0080KJ-A
				R5F10WMEGFB, R5F10WMFGFB, R5F10WMGGFB	#30	PLQP0080KB-B

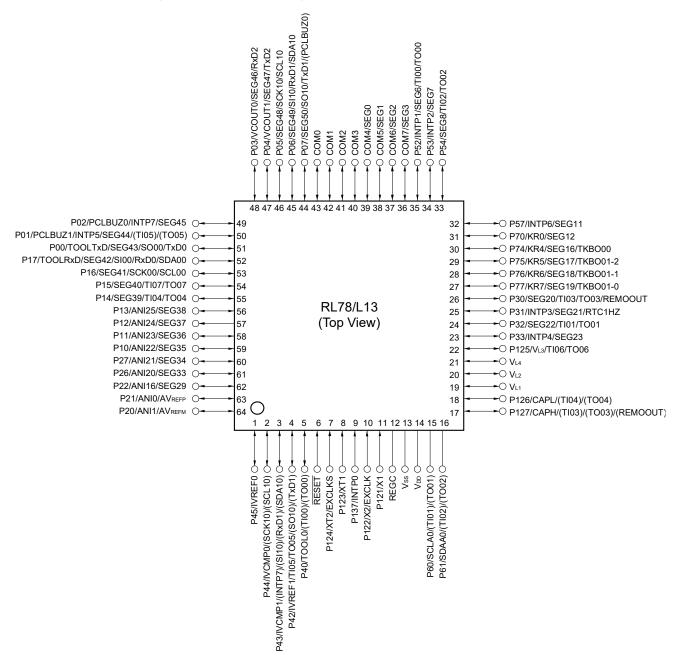
Note For the fields of application, see Figure 1-1 Part Number, Memory Size, and Package of RL78/L13.

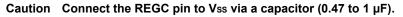


1.3 Pin Configuration (Top View)

1.3.1 64-pin products

- 64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)
- 64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)





Remarks 1. For pin identification, see 1.4 Pin Identification.

 Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/L13 User's Manual.

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Pin	I/O	×	Analog		HMI			Timer			Communications	
No.		clo					_				Interface	-
64LQFP, 64LFQFP	Digital port	Power supply, system clock, debug	A/D converter	Comparator	Interrupt function	Key Interrupt function	LCD controller/driver	Timer array unit	16-bit timer KB20	Real-time clock 2	Serial array unit	Serial interface IICA
1	P45			IVREF0								
2	P44			IVCMP0							(SCK10)/(SCL10)	
3	P43			IVCMP1	(INTP7)						(SI10)/(RxD1)/(S DA10)	
4	P42			IVREF1				TI05/TO05			(SO10)/(TxD1)	
5	P40	TOOL0						(TI00)/(TO00)				
6		RESET										
7	P124	XT2/EXCLKS										
8	P123	XT1										
9	P137				INTP0							
10	P122	X2/EXCLK										
11	P121	X1										
12		REGC										
13		V _{SS}										
14		V _{DD}										
15	P60							(TI01)/(TO01)				SCLA0
16	P61							(TI02)/(TO02)				SDAA0
17	P127						CAPH	(TI03)/(TO03)/ (REMOOUT)				
18	P126						CAPL	(TI04)/(TO04)				
19							V _{L1}					
20							V _{L2}					
21							VL4					
22	P125						V _{L3}	TI06/TO06				
23	P33				INTP4		SEG23					
24	P32					_	SEG22	TI01/TO01				
25	P31				INTP3		SEG21			RTC1HZ		
26	P30						SEG20	TI03/TO03/RE MOOUT				
27	P77					KR7	SEG19		ТКВО 01-0			
28	P76					KR6	SEG18		TKBO 01-1			
29	P75					KR5	SEG17		ткво 01-2			
30	P74					KR4	SEG16		ткво 00			
31	P70					KR0	SEG12					
32	P57				INTP6		SEG11	1				
33	P54						SEG8	TI02/TO02				
34	P53				INTP2		SEG7					
35	P52				INTP1		SEG6	TI00/TO00				

Table 1-1. Alternate function of 64-pin products (1/2)



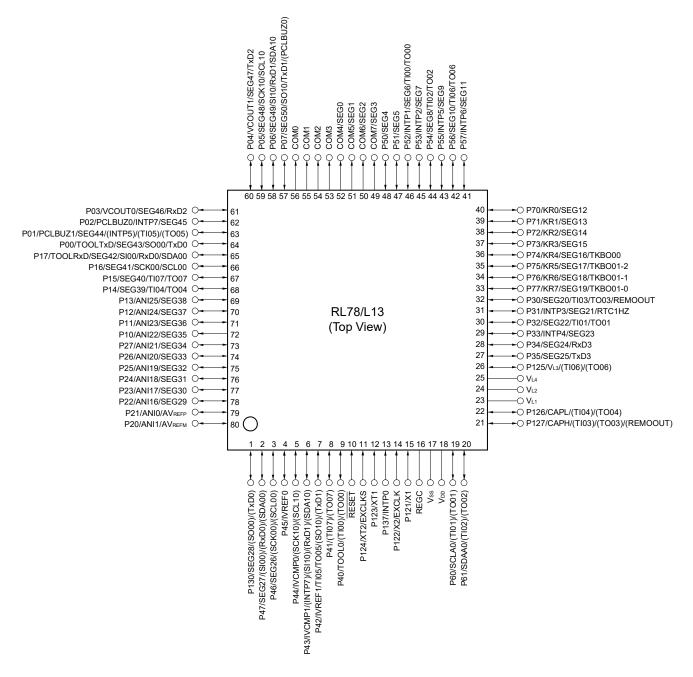
Pin No.	I/O	clock,	Analog		НМІ			Timer			Communication Interface	s
64LQFP, 64LFQFP	Digital port	Power supply, system clock, debug	A/D converter	Comparator	Interrupt function	Key Interrupt function	LCD controller/driver	Timer array unit	16-bit timer KB20	Real-time clock 2	Serial array unit	Serial interface IICA
36							COM7/S EG3					
37							COM6/S EG2					
38							COM5/S EG1					
39							COM4/S EG0					
40							COM3					
41							COM2					
42							COM1					
43							COM0					
44	P07	(PCLBUZ0)					SEG50				SO10/TxD1	
45	P06						SEG49				SI10/RxD1/SD A10	
46	P05						SEG48				SCK10/SCL10	
47	P04			VCOUT1			SEG47				TxD2	
48	P03			VCOUT0			SEG46				RxD2	
49	P02	PCLBUZ0			INTP7		SEG45					
50	P01	PCLBUZ1			INTP5		SEG44	(TI05)/(TO05)				
51	P00	TOOLTxD					SEG43				SO00/TxD0	
52	P17	TOOLRxD					SEG42				SI00/RxD0/SD A00	
53	P16						SEG41				SCK00/SCL00	
53 54	P16 P15						SEG41 SEG40	TI07/TO07			30K00/30L00	
54 55	P15					1	SEG40 SEG39	TI07/TO07				
56	P13	+	ANI25				SEG39	1104/1004				
57	P12		ANI23				SEG37					
58	P11		ANI24				SEG36					
59	P10		ANI23				SEG35					
60	P27		ANI21				SEG34					
61	P26		ANI20				SEG33					
62	P22		ANI16				SEG29			1		
63	P21		ANI0/A			1	-		1			ĺ
			V _{REFP}									
64	P20		ANI1/A						1		1	
			VREFM									

Table 1-1. Alternate function of 64-pin products (2/2)



1.3.2 80-pin products

- 80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)
- 80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

 Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/L13 User's Manual.

Pin	I/O	Ķ	Analog		НМІ			Timer			Communications	Interface
No.		i cloc		1		r	1		r	r		1
80LQFP, 80LFQFP	Digital port	Power supply, system clock, debug	A/D converter	Comparator	Interrupt function	Key Interrupt function	LCD controller/driver	Timer array unit	16-bit timer KB20	Real-time clock 2	Serial array unit	Serial interface IICA
1	P130						SEG28				(SO00)/(TxD0)	
2	P47						SEG27				(SI00)/(RxD0)/(S DA00)	
3	P46						SEG26				(SCK00)/(SCL00)	
4	P45			IVREF0								
5	P44			IVCMP0							(SCK10)/(SCL10)	
6	P43			IVCMP1	(INTP7)						(SI10)/(RxD1)/(S DA10)	
7	P42			IVREF1				TI05/TO05			(SO10)/(TxD1)	
8	P41							(TI07)/(TO07)				
9	P40	TOOL0						(TI00)/(TO00)				
10		RESET										
11	P124	XT2/EXCLKS										
12	P123	XT1										
13	P137				INTP0							
14	P122	X2/EXCLK										
15	P121	X1										
16		REGC										
17		Vss										
18		V _{DD}										
19	P60							(TI01)/(TO01)				SCLA0
20	P61							(TI02)/(TO02)				SDAA0
21	P127						CAPH	(TI03)/(TO03)/(REMOOUT)				
22	P126						CAPL	(TI04)/(TO04)				
23							V _{L1}					
24							V _{L2}					
25				l			VL4					
26	P125						V _{L3}	(TI06)/(TO06)				
27	P35						SEG25				TxD3	
28	P34			l			SEG24				RxD3	
29	P33				INTP4		SEG23					
30	P32						SEG22	TI01/TO01				



Pin	I/O	¥	Analog		НМІ			Timer			Communications Interface	
No.		cloc		r		1	ſ		1	1		T
80LQFP, 80LFQFP	Digital port	Power supply, system clock, debug	A/D converter	Comparator	Interrupt function	Key Interrupt function	LCD controller/driver	Timer array unit	16-bit timer KB20	Real-time clock 2	Serial array unit	Serial interface IICA
31	P31				INTP3		SEG21			RTC1 HZ		
32	P30						SEG20	TI03/TO03/RE MOOUT				
33	P77					KR7	SEG19		TKBO01 -0			
34	P76					KR6	SEG18		ТКВО01 -1			
35	P75					KR5	SEG17		ТКВО01 -2			
36	P74					KR4	SEG16		TKBO00			
37	P73					KR3	SEG15					
38	P72					KR2	SEG14					
39	P71					KR1	SEG13					
40	P70					KR0	SEG12					
41	P57				INTP6		SEG11					
42	P56						SEG10	TI06/TO06				
43	P55				INTP5		SEG9					
44	P54						SEG8	TI02/TO02				
45	P53				INTP2		SEG7					
46	P52				INTP1		SEG6	TI00/TO00				
47	P51						SEG5					
48	P50						SEG4					
49							COM7/S EG3					
50							COM6/S					
51							EG2 COM5/S					
52							EG1 COM4/S					
							EG0					
53							COM3					
54							COM2					
55							COM1					
56							COM0					
57	P07	(PCLBUZ0)					SEG50				SO10/TxD1	

Table 1-2. Alternate function of 80-pin products (2/3)



Pin	I/O 🛫 Analog HMI Timer Communications Interface										Communications	Interface
No.		cloch										
80LQFP, 80LFQFP	Digital port	Power supply, system clock, debug	A/D converter	Comparator	Interrupt function	Key Interrupt function	LCD controller/driver	Timer array unit	16-bit timer KB20	Real-time clock 2	Serial array unit	Serial interface IICA
58	P06						SEG49				SI10/RxD1/SDA 10	
59	P05						SEG48				SCK10/SCL10	
60	P04			VCOUT1			SEG47				TxD2	
61	P03			VCOUT0			SEG46				RxD2	
62	P02	PCLBUZ0			INTP7		SEG45					
63	P01	PCLBUZ1			(INTP5)		SEG44	(TI05)/(TO05)				
64	P00	TOOLTxD					SEG43				SO00/TxD0	
65	P17	TOOLRxD					SEG42				SI00/RxD0/SDA	
66	P16						SEG41				SCK00/SCL00	
67	P15						SEG40	TI07/TO07				
68	P14						SEG39	TI04/TO04				
69	P13		ANI25				SEG38					
70	P12		ANI24				SEG37					
71	P11		ANI23				SEG36					
72	P10		ANI22				SEG35					
73	P27		ANI21				SEG34					
74	P26		ANI20				SEG33					
75	P25		ANI19				SEG32					
76	P24		ANI18				SEG31					
77	P23		ANI17				SEG30					
78	P22		ANI16				SEG29					
79	P21		ANI0/AV									
80	P20		ANI1/AV									

Table 1-2. Alternate function of 80-pin products (3/3)



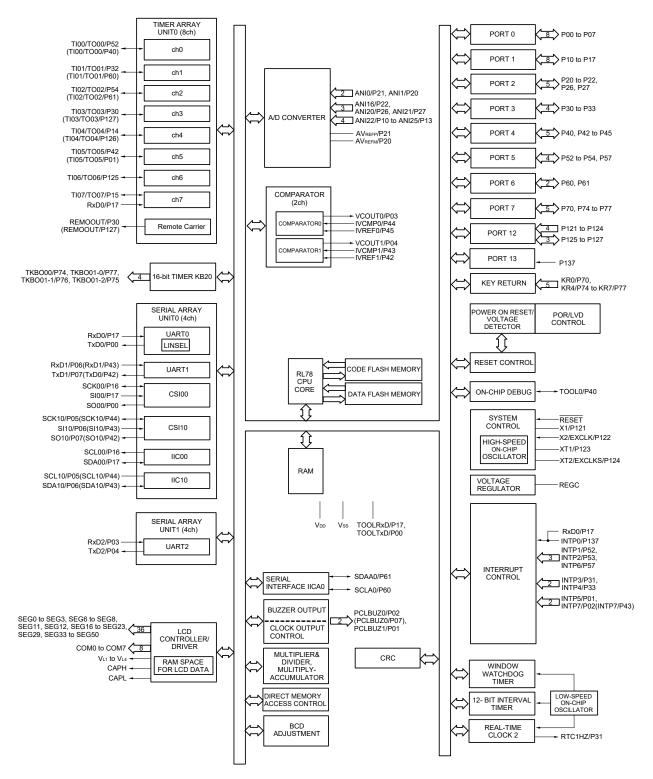
1.4 Pin Identification

ANIO, ANI1,		PCLBUZ0, PCLBUZ1:	Programmable Clock Output/
ANI16 to ANI25:	Analog Input		Buzzer Output
AVREFM:	Analog Reference Voltage	REGC:	Regulator Capacitance
	Minus	REMOOUT:	Remote control Output
AVREFP:	Analog Reference Voltage	RESET:	Reset
	Plus	RTC1HZ:	Real-time Clock 2 Correction Clock
CAPH, CAPL:	Capacitor for LCD		(1 Hz) Output
COM0 to COM7:	LCD Common Output	RxD0 to RxD3:	Receive Data
EXCLK:	External Clock Input	SCK00, SCK10, SCLA0:	Serial Clock Input/Output
	(Main System Clock)	SCL00, SCL10:	Serial Clock Output
EXCLKS:	External Clock Input	SDAA0, SDA00, SDA10:	Serial Data Input/Output
	(Subsystem Clock)	SEG0 to SEG50:	LCD Segment Output
INTP0 to INTP7:	External Interrupt Input	SI00, SI10:	Serial Data Input
IVCMP0, IVCMP1	: Comparator Input	SO00, SO10:	Serial Data Output
IVREF0, IVREF1:	Comparator Reference Input	TI00 to TI07:	Timer Input
KR0 to KR7:	Key Return	TO00 to TO07,	
P00 to P07:	Port 0	TKBO00, TKBO01-0,	
P10 to P17:	Port 1	TKBO01-1, TKBO01-2:	Timer Output
P20 to P27:	Port 2	TOOL0:	Data Input/Output for Tool
P30 to P35:	Port 3	TOOLRxD, TOOLTxD:	Data Input/Output for External Device
P40 to P47:	Port 4	TxD0 to TxD3:	Transmit Data
P50 to P57:	Port 5	VCOUT0, VCOUT1:	Comparator Output
P60, P61:	Port 6	Vdd:	Power Supply
P70 to P77:	Port 7	VL1 to VL4:	LCD Power Supply
P121 to P127:	Port 12	Vss:	Ground
P130, P137:	Port 13	X1, X2:	Crystal Oscillator (Main System Clock)
		XT1, XT2:	Crystal Oscillator (Subsystem Clock)



1.5 Block Diagram

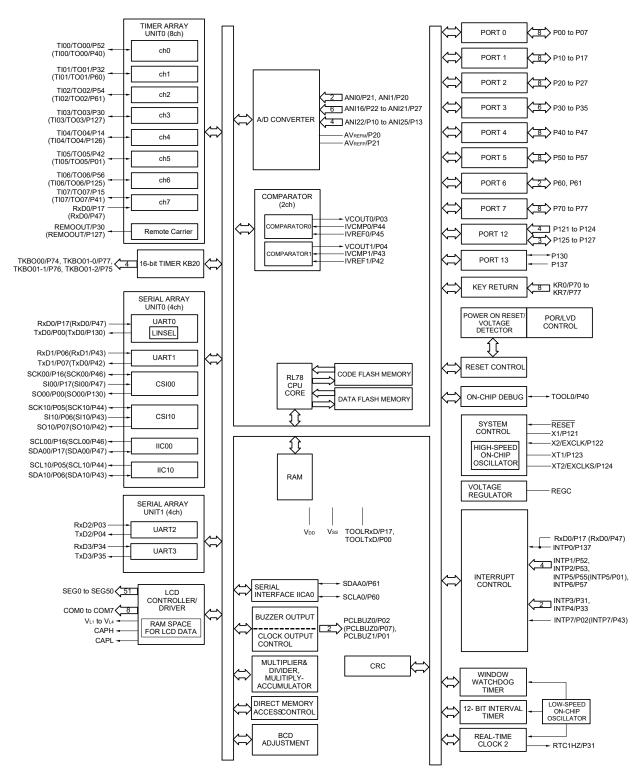
1.5.1 64-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8** Format of Peripheral I/O Redirection Register (PIOR) in the RL78/L13 User's Manual.

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1.5.2 80-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/L13 User's Manual.

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1.6 Outline of Functions

			(1/2)					
	Item	64-pin	80-pin					
		R5F10WLx (x = A, C-G)	R5F10WMx (x = A, C-G)					
Code flash m	emory (KB)	16 to 128	16 to 128					
Data flash me	emory (KB)	4	4					
RAM (KB)		1 to 8 ^{Note 1}	1 to 8 ^{Note 1}					
Address space	e	1 MB						
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main s HS (High-speed main) mode: 1 to 20 MHz (Vod HS (High-speed main) mode: 1 to 16 MHz (Vod LS (Low-speed main) mode: 1 to 8 MHz (Vod LV (Low-voltage main) mode: 1 to 4 MHz (Vod	= 2.7 to 5.5 V), = 2.4 to 5.5 V), 1.8 to 5.5 V), = 1.6 to 5.5 V)					
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 24 MHz (Vod HS (High-speed main) mode: 1 to 16 MHz (Vod LS (Low-speed main) mode: 1 to 8 MHz (Vod LV (Low-voltage main) mode: 1 to 4 MHz (Vod	o = 2.4 to 5.5 V), = 1.8 to 5.5 V),					
Clock for 16-b	oit timer KB20	48 MHz (TYP.): V _{DD} = 2.7 to 5.5 V						
Subsystem cl	ock	XT1 (crystal) oscillation, external subsystem clo 32.768 kHz (TYP.): V _{DD} = 1.6 to 5.5 V	ock input (EXCLKS)					
Low-speed or	n-chip oscillator	15 kHz (TYP.)						
General-purp	ose register	(8-bit register × 8) × 4 banks						
Minimum inst	ruction execution time	0.04167 μ s (High-speed on-chip oscillator: f _{IH} = 24 MHz operation)						
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)						
		30.5 µs (Subsystem clock: fsuв = 32.768 kHz op	peration)					
Instruction se	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 						
I/O port	Total	49	65					
	CMOS I/O	42 (N-ch O.D. I/O [V⊳⊳ withstand voltage]: 12)	58 (N-ch O.D. I/O [V⊳⊳ withstand voltage]: 18)					
	CMOS input	5	5					
	CMOS output	—	—					
	N-ch O.D I/O (withstand voltage: 6 V)	2	2					
Timer	16-bit timer TAU	8 cha	nnels					
	16-bit timer KB20	1 cha	nnel					
	Watchdog timer	1 cha	nnel					
	12-bit interval timer (IT)	1 cha	Innel					
	Real-time clock 2	1 cha	nnel					
	RTC2 output	1 • 1 Hz (subsystem clock: fsuв = 32.768 kHz)						
	Timer output	8 channels (PWM outputs: 7 ^{Note 2}) (TAU used) 1 channel (timer KB20 used)						
	Remote control output function	1 (TAU used)						

Notes 1. In the case of the 8 KB, this is about 7 KB when the self-programming function and data flash function are used.

2. The number of outputs varies depending on the setting of the channels in use and the number of master channels (see 6.9.3 Operation as multiple PWM output function in the RL78/L13 User's Manual).

(2/2)

	Item	64-pin	80-pin					
		R5F10WLx (x = A, C-G)	R5F10WMx (x = A, C-G)					
Clock output/l	buzzer output controller	2						
		 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation) 						
8/10-bit resolu	ution A/D converter	9 channels 12 channels						
Comparator		2 channels	•					
Serial interfac	се 	 [64-pin] Simplified SPI (CSI): 1 channel/UART (UAR 1 channel/simplified l²C: 1 channel Simplified SPI (CSI): 1 channel/UART: 1 ch UART: 1 channel [80-pin] Simplified SPI (CSI): 1 channel/UART (UAR 1 channel/simplified l²C: 1 channel Simplified SPI (CSI): 1 channel/UART: 1 ch UART: 2 channels 	annel/simplified I ² C: 1 channel RT supporting LIN-bus):					
	I ² C bus	1 channel						
LCD controlle	er/driver	Internal voltage boosting method, capacitor split method, and external resistance division method are switchable.						
Se	gment signal output	36 (32) ^{Note 1}	51 (47) ^{Note 1}					
Co	ommon signal output	4 (8	3)Note 1					
Multiplier and	divider/multiply-	• 16 bits × 16 bits = 32 bits (Unsigned or sign	ed)					
accumulator		• 32 bits + 32 bits = 32 bits (Unsigned)						
		• 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)						
DMA controlle	er	4 channels						
Vectored	Internal	32	35					
interrupt sour	ces External	11	11					
Key interrupt	I	5	8					
Reset		 Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution^{Note 2} Internal reset by RAM parity error Internal reset by illegal-memory access 						
Power-on-res	et circuit	 Power-on-reset: 1.51 V (TYP.) Power-down-reset: 1.50 V (TYP.) Rising edge: 1.67 V to 4.06 V (14 steps) Falling edge: 1.63 V to 3.98 V (14 steps) 						
Voltage detec	ctor							
On-chip debu	g function	Provided						
Power supply	voltage	V _{DD} = 1.6 to 5.5 V (TA = -40 to +85°C)						
		V _{DD} = 2.4 to 5.5 V (TA = -40 to +105°C)						
Operating am	bient temperature	Consumer applications: $T_A = -40$ to $+85^{\circ}C$ Industrial applications: $T_A = -40$ to $+105^{\circ}C$						

Notes 1. The values in parentheses are the number of signal outputs when 8 com is used.

2. This reset occurs when instruction code FFH is executed.

This reset does not occur during emulation using an in-circuit emulator or an on-chip debugging emulator.

2. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to +85°C)

Target productsA: Consumer applications; TA = -40 to +85°CR5F10WLAAFA, R5F10WLCAFA, R5F10WLDAFA,R5F10WLEAFA, R5F10WLFAFA, R5F10WLGAFA,R5F10WLAAFB, R5F10WLCAFB, R5F10WLDAFB,R5F10WLEAFB, R5F10WLFAFB, R5F10WLGAFB,R5F10WMAAFA, R5F10WMCAFA, R5F10WMDAFA,R5F10WMEAFA, R5F10WMCAFA, R5F10WMGAFA,R5F10WMEAFB, R5F10WMCAFB, R5F10WMGAFA,R5F10WMEAFB, R5F10WMCAFB, R5F10WMGAFA,R5F10WMEAFB, R5F10WMCAFB, R5F10WMGAFA,R5F10WMEAFB, R5F10WMCAFB, R5F10WMGAFA,R5F10WMEAFB, R5F10WMCAFB, R5F10WMGAFB,R5F10WMEAFB, R5F10WMCAFB, R5F10WMGAFB,

G: Industrial applications; when using T_A = -40 to +105°C specification products at T_A = -40 to +85°C R5F10WLAGFB, R5F10WLCGFB, R5F10WLDGFB, R5F10WLEGFB, R5F10WLFGFB, R5F10WLGGFB R5F10WMAGFB, R5F10WMCGFB, R5F10WMDGFB, R5F10WMEGFB, R5F10WEGFB, R5F10WEGFB,

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 With functions for each product in the RL78/L13 User's Manual.



2.1 Absolute Maximum Ratings

Absolute	Maximum	Ratings	(1/3)
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Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
REGC pin input voltage	Viregc	REGC	-0.3 to +2.8 and -0.3 to V_DD +0.3^Note 1	V
Input voltage	VI1	P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P121 to P127, P130, P137	–0.3 to V _{DD} +0.3 ^{Note 2}	V
	VI2	P60 and P61 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	V ₀₁	P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P121 to P127, P130, P137	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	VAI1	ANI0, ANI1, ANI16 to ANI26	-0.3 to V_DD +0.3 and -0.3 to AV_{REF(+)} +0.3^{Notes 2, 3} $$	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed $AV_{REF(+)}$ + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - 2. AVREF (+): + side reference voltage of the A/D converter.
 - 3. Vss: Reference voltage



Parameter	Symbol		Conditions	Ratings	Unit
LCD voltage	V _{L1}	V _{L1} voltage ^{Note 1}		–0.3 to +2.8 and –0.3 to V∟4 +0.3	V
	VL2	VL2 voltage ^{Note 1}		-0.3 to V _{L4} +0.3 ^{Note 2}	V
	VL3	VL3 voltage ^{Note 1}	-0.3 to V _{L4} +0.3 ^{Note 2}	V	
	VL4	VL4 voltage ^{Note 1}		-0.3 to +6.5	V
	VLCAP	CAPL, CAPH volt	CAPL, CAPH voltage ^{Note 1}		V
	Vout	COM0 to COM7	External resistance division method	-0.3 to V _{DD} +0.3 ^{Note 2}	V
		SEG0 to SEG50	Capacitor split method	-0.3 to V _{DD} +0.3 ^{Note 2}	V
		output voltage	Internal voltage boosting method	–0.3 to VL4 +0.3 $^{\rm Note\ 2}$	V

Absolute Maximum Ratings (2/3)

- Notes 1. This value only indicates the absolute maximum ratings when applying voltage to the V_{L1}, V_{L2}, V_{L3}, and V_{L4} pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to Vss via a capacitor (0.47 μF ± 30%) and connect a capacitor (0.47 μF ± 30%) between the CAPL and CAPH pins.
 - 2. Must be 6.5 V or lower.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Vss: Reference voltage



Absolute Maximum Ratings (3/3)

Parameter	Symbol		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P125 to P127, P130	-40	mA
		Total of all pins –170 mA	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P125 to P127, P130	-170	mA
	Іон2	Per pin	P20, P21	-0.5	mA
		Total of all pins		-1	mA
Output current, low	lol1	Per pin	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P125 to P127, P130	40	mA
		Total of all pins	P40 to P47, P130	70	mA
		170 mA	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P50 to P57, P60, P61, P70 to P77, P125 to P127	100	mA
	IOL2	Per pin	P20, P21	1	mA
		Total of all pins		2	mA
Operating ambient temperature	TA	In normal operation	on mode orogramming mode	-40 to +85	°C
Storage temperature	Tstg			–65 to +150	°C

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



2.2 Oscillator Characteristics

2.2.1 X1 and XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	1.0		20.0	MHz
frequency (fx) ^{Note}	crystal resonator	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	1.0		16.0	
		$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.4 \text{ V}$	1.0	8.0		
		$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}$	1.0		4.0	
XT1 clock oscillation frequency (fxT) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- Remark When using the X1 oscillator and XT1 oscillator, see 5.4 System Clock Oscillator in the RL78/L13 User's Manual.



2.2.2 On-chip oscillator characteristics

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	fін			1		24	MHz
High-speed on-chip oscillator		–20 to +85°C	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	-1.0		+1.0	%
clock frequency accuracy			$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}$	-5.0		+5.0	%
		-40 to -20°C	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	-1.5		+1.5	%
			$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}$	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. The high-speed on-chip oscillator frequency is selected by bits 0 to 4 of the option byte (000C2H/010C2H) and bits 0 to 2 of the HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for the instruction execution time.



2.3 DC Characteristics

2.3.1 Pin characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, I _{OH1} high ^{Note 1}		Per pin for P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	$1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$			–10.0 ^{Note 2}	mA
		Total of P00 to P07, P10 to P17,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			-90.0	mA
		P22 to P27, P30 to P35, P40 to P47,	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} < 4.0~\textrm{V}$			-15.0	mA
		P50 to P57, P70 to P77, P125 to P127, P130	$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$			-7.0	mA
		(When duty = 70% ^{Note 3})	$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}$			-3.0	mA
	Іонг	Per pin for P20 and P21	$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty = 70% ^{Note 3})	$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			-0.2	mA

- Notes 1. Value of the current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin
 - 2. Do not exceed the total current value.
 - **3.** Output current value under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IOH × 0.7)/(n × 0.01)
- <Example> Where n = 80% and IoH = -90.0 mA

Total output current of pins = (-90.0 × 0.7)/(80 × 0.01) ≈ -78.75 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 do not output high level in N-ch open-drain mode.



Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	Iol1	Per pin for P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130				20.0 ^{Note 2}	mA
		Per pin for P60 and P61				15.0 ^{Note 2}	mA
		Total of P40 to P47, P130 (When duty = 70% ^{Note 3})	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			70.0	mA
			$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$			15.0	mA
			$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$			9.0	mA
			$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}$			4.5	mA
		Total of P00 to P07, P10 to P17, P22 to P27, P30 to P35, P50 to P57, P70 to P77, P125 to P127 (When duty = 70% ^{Note 3})	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			90.0	mA
			$2.7~\text{V} \leq \text{V}_{\text{DD}} < 4.0~\text{V}$			35.0	mA
			$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$			20.0	mA
			$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}$			10.0	mA
		Total of all pins (When duty = 70% ^{Note 3})				160.0	mA
	IOL2	Per pin for P20 and P21				0.4 ^{Note 2}	mA
		Total of all pins (When duty = 70% ^{Note 3})	$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			0.8	mA

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

- **Notes 1**. Value of the current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin
 - 2. Do not exceed the total current value.
 - Output current value under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).
 - Total output current of pins = (Io_L × 0.7)/(n × 0.01) <Example> Where n = 80% and Io_L = 70.0 mA

Total output current of pins = (70.0 × 0.7)/(80 × 0.01) ≈ 61.25 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.



Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130, P137	Normal input buffer	0.8Vdd		Vdd	V
	VIH2	P03, P05, P06, P16, P17, P34, P43, P44, P46, P47, P53, P55	TTL input buffer 4.0 V ≤ V _{DD} ≤ 5.5 V	2.2		Vdd	V
			TTL input buffer 3.3 V ≤ V _{DD} < 4.0 V	2.0		Vdd	V
			TTL input buffer 1.6 V ≤ V _{DD} < 3.3 V	1.5		Vdd	V
	Vінз	P20, P21	0.7V _{DD}		Vdd	V	
	VIH4	P60, P61	0.7V _{DD}		6.0	V	
	VIH5	P121 to P124, P137, EXCLK, EXCLKS	0.8Vdd		Vdd	V	
Input voltage, low	VIL1	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130, P137	Normal input buffer	0		0.2Vdd	V
	VIL2	P03, P05, P06, P16, P17, P34, P43, P44, P46, P47, P53, P55	TTL input buffer 4.0 V ≤ V _{DD} ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ V _{DD} < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ V _{DD} < 3.3 V	0		0.32	V
	VIL3	P20, P21		0		0.3VDD	V
	VIL4	P60, P61		0		0.3Vdd	V
	VIL5	P121 to P124, P137, EXCLK, EXCLKS	S, RESET	0		0.2Vdd	V

 $(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

- Caution The maximum value of V_I of pins P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 is V_{DD}, even in the N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57,	4.0 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −10.0 mA	Vdd - 1.5			V
		P70 to P77, P125 to P127, P130	4.0 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −3.0 mA	V _{DD} – 0.7			V
			2.7 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −2.0 mA	V _{DD} - 0.6			V
			1.8 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −1.5 mA	Vdd - 0.5			V
			1.6 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −1.0 mA	Vdd - 0.5			V
	V _{OH2}	P20 and P21	1.6 V ≤ V _{DD} ≤ 5.5 V, Іон₂ = −100 µА	Vdd - 0.5			V
Output voltage, low	V _{OL1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57,	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 20 \text{ mA}$			1.3	V
		P70 to P77, P125 to P127, P130	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 8.5 \text{ mA}$			0.7	V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 3.0 \text{ mA}$			0.6	V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 1.5 \text{ mA}$			0.4	V
			$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 0.6 \text{ mA}$			0.4	V
			$1.6 V \le V_{DD} < 1.8 V,$ $I_{OL1} = 0.3 mA$			0.4	V
	Vol2	P20 and P21	1.6 V ≤ V _{DD} ≤ 5.5 V, I _{OL2} = 400 μA			0.4	V
	Vol3	P60 and P61	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol3 = 15.0 mA			2.0	V
			$4.0 V \le V_{DD} \le 5.5 V$, $I_{OL3} = 5.0 mA$			0.4	V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL3}} = 3.0 \text{ mA}$			0.4	V
			$1.8 V \le V_{DD} \le 5.5 V$, $I_{OL3} = 2.0 \text{ mA}$			0.4	V
			$1.6 V \le V_{DD} < 1.8 V$, $I_{OL3} = 1.0 mA$			0.4	V

Caution P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 do not output high level in N-ch open-drain mode.

$(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Con	ditions		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ilih1	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P125 to P127, P130, P137	VI = VDD				1	μA
	ILIH2	P20 and P21, RESET	$V_{I} = V_{DD}$				1	μA
	Іцнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port mode and when external clock is input			1	μA
				Resonator connected			10	μA
Input leakage current, low	ILIL1	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P125 to P127, P130, P137	VI = VSS				-1	μA
		P20 and P21, RESET	VI = Vss				-1	μA
	Ililis	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vi = Vss	In input port mode and when external clock is input			-1	μA
				Resonator connected			-10	μA
On-chip pull-up	Ruı	P00 to P07, P10 to P17,	VI = Vss	$2.4 V \le V_{DD} < 5.5 V$	10	20	100	kΩ
resistance	P	P22 to P27, P30 to P35, P45 to P47, P50 to P57, P70 to P77, P125 to P127, P130		$1.6 V \le V_{DD} < 2.4 V$	10	30	100	kΩ
	Ru2	P40 to P44	VI = Vss		10	20	100	kΩ



2.3.2 Supply current characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply current ^{Note 1}	IDD1	Operating	HS (high-	fносо = 48 MHz ^{Note 3} ,	Basic	V _{DD} = 5.0 V		2.0		mA
		mode	speed main)	f _{IH} = 24 MHz ^{Note 3}	operation	V _{DD} = 3.0 V		2.0		mA
			mode ^{Note 5}		Normal	V _{DD} = 5.0 V		3.8	6.5	mA
					operation	V _{DD} = 3.0 V		3.8	6.5	m/
				fHOCO = 24 MHz ^{Note 3} ,	Basic	V _{DD} = 5.0 V		1.7		m/
				fı⊢ = 24 MHz ^{Note 3}	operation	V _{DD} = 3.0 V		1.7		m/
					Normal	V _{DD} = 5.0 V		3.6	6.1	m/
					operation	V _{DD} = 3.0 V		3.6	6.1	m/
				fносо = 16 MHz ^{Note 3} , f _{IH} = 16 MHz ^{Note 3}	Normal operation	V _{DD} = 5.0 V		2.7	4.7	m/
						V _{DD} = 3.0 V		2.7	4.7	m/
			LS (low- speed main) mode ^{Note 5}	fHOCO = 8 MHZ ^{Note 3}	Normal operation	V _{DD} = 3.0 V		1.2	2.1	m/
				f⊮ = 8 MHz ^{Note 3}		V _{DD} = 2.0 V		1.2	2.1	m/
			LV (low-	fносо = 4 MHz ^{Note 3} ,	Normal	V _{DD} = 3.0 V		1.2	1.8	m/
			voltage main) mode ^{Note 5}	f⊮ = 4 MHz ^{Note 3}	operation	V _{DD} = 2.0 V		1.2	1.8	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.0	5.1	m/
			Speed main) mode ^{Note 5} LS (low- speed main) mode ^{Note 5}	V _{DD} = 5.0 V	operation	Resonator connection		3.2	5.2	m/
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$ $V_{\text{DD}} = 3.0 \text{ V}$	Normal operation	Square wave input		2.9	5.1	m/
						Resonator connection		3.2	5.2	m
				f _{MX} = 16 MHz ^{Note 2} , V _{DD} = 5.0 V	Normal	Square wave input		2.5	4.4	m
					operation	Resonator connection		2.7	4.5	m
				f _{MX} = 16 MHz ^{Note 2} ,	Normal	Square wave input		2.5	4.4	m/
				V _{DD} = 3.0 V	operation	Resonator connection		2.7	4.5	m/
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$ $V_{\text{DD}} = 5.0 \text{ V}$	Normal operation	Square wave input		1.9	3.0	m/
						Resonator connection		1.9	3.0	m/
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$ $V_{\text{DD}} = 3.0 \text{ V}$	Normal operation	Square wave input		1.9	3.0	m/
						Resonator connection		1.9	3.0	m/
				f _{MX} = 8 MHz ^{Note 2} , V _{DD} = 3.0 V	Normal operation	Square wave input		1.1	2.0	m/
						Resonator connection		1.1	2.0	m/
				f _{MX} = 8 MHz ^{Note 2} , V _{DD} = 2.0 V	Normal operation	Square wave input		1.1	2.0	m/
						Resonator connection		1.1	2.0	m/
			Subsystem clock operation	fsue = 32.768 kHz ^{Note 4} ,	Normal	Square wave input		4.0	5.4	μA
				$T_A = -40^{\circ}C$	operation	Resonator connection		4.3	5.4	μA
			operation	fsue = 32.768 kHz ^{Note 4} ,	Normal	Square wave input		4.0	5.4	μA
				T _A = +25°C	operation	Resonator connection		4.3	5.4	μA
				f _{SUB} = 32.768 kHz ^{Note 4} , T _A = +50°C	Normal operation	Square wave input		4.1	7.1	μA
						Resonator connection		4.4	7.1	μA
				f _{SUB} = 32.768 kHz ^{Note 4} , T _A = +70°C	Normal operation	Square wave input		4.3	8.7	μA
						Resonator connection		4.7	8.7	μA
				fsue = 32.768 kHz ^{Note 4} ,	Normal	Square wave input		4.7	12.0	μA
				T _A = +85°C	operation	Resonator connection		5.2	12.0	μA

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main), LS (low-speed main), and LV (low-voltage main) modes.
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the LCD controller/driver, A/D converter, LVD circuit, comparator, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the real-time clock 2.

- 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- 3. When high-speed system clock and subsystem clock are stopped.
- **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When setting ultra-low power consumption oscillation (AMPHS1 = 1).
- 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}_{\text{@1}} \text{ MHz}$ to 24 MHz

2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz

- LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}@1 \text{ MHz}$ to 8 MHz
- LV (low-voltage main) mode: 1.6 V \leq V_DD \leq 5.5 V@1 MHz to 4 MHz
- **Remarks 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fHOCO: High-speed on-chip oscillator clock frequency (48 MHz max.)
 - 3. fin: High-speed on-chip oscillator clock frequency (24 MHz max.)
 - **4.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

(2/2)

Parameter	Symbol			MIN.	TYP.	MAX.	Uni		
Supply current ^{Note 1}	DD2 ^{Note 2}	HALT mode	HS (high-speed	fносо = 48 MHz ^{Note 4} , V _{DD} = 5.0 V			0.71	1.95	mA
			main) mode Note 6	fı⊢ = 24 MHz ^{Note 4}	V _{DD} = 3.0 V		0.71	1.95	
				fносо = 24 MHz ^{Note 4} ,	V _{DD} = 5.0 V		0.49	1.64	mA
				fı⊢ = 24 MHz ^{Note 4}	V _{DD} = 3.0 V		0.49	1.64	
				fносо = 16 MHz ^{Note 4} ,	V _{DD} = 5.0 V		0.43	1.11	mA
				fı⊢ = 16 MHz ^{Note 4}	V _{DD} = 3.0 V		0.43	1.11	
			LS (low-speed main) mode Note 6	fносо = 8 MHz ^{Note 4} ,	V _{DD} = 3.0 V		280	770	μA
				f⊪ = 8 MHz ^{Note 4}	V _{DD} = 2.0 V		280	770	-
			LV (low-voltage main) mode ^{Note 6}	fносо = 4 MHz ^{Note 4} ,	V _{DD} = 3.0 V		430	700	μA
				f _{IH} = 4 MHz ^{Note 4}	V _{DD} = 2.0 V		430	700	
			HS (high-speed main) mode Note 6	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.31	1.42	mA
					Resonator connection		0.48	1.42	
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.29	1.42	m
				V _{DD} = 3.0 V	Resonator connection		0.48	1.42	
				f _{MX} = 16 MHz ^{Note 3} ,	Square wave input		0.26	0.86	m
				V _{DD} = 5.0 V	Resonator connection		0.45	1.15	
				f _{MX} = 16 MHz ^{Note 3} ,	Square wave input		0.25	0.86	m
				V _{DD} = 3.0 V	Resonator connection		0.44	1.15	
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.20	0.63	mA
				V _{DD} = 5.0 V	Resonator connection		0.28	0.71	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.19	0.63	m
					Resonator connection		0.28	0.71	
			LS (low-speed main) mode ^{Note 6}	f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		100	560	μA
				V _{DD} = 3.0 V	Resonator connection		160	560	
				f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 2.0 V	Square wave input		100	560	μA
					Resonator connection		160	560	
			Subsystem clock operation	fsuв = 32.768 kHz ^{Note 5} ,	Square wave input		0.34	0.62	μA
				$T_A = -40^{\circ}C$	Resonator connection		0.51	0.80	
		1		fsue = 32.768 kHz ^{Note 5} ,	Square wave input		0.38	0.62	μA
				T _A = +25°C	Resonator connection		0.57	0.80	1
				fsuв = 32.768 kHz ^{Note 5} ,	Square wave input		0.46	2.30	μA
				T _A = +50°C	Resonator connection		0.67	2.49	
				fsuв = 32.768 kHz ^{Note 5} ,	Square wave input		0.65	4.03	μA
				T _A = +70°C	Resonator connection		0.91	4.22	
				fsuв = 32.768 kHz ^{Note 5} ,	Square wave input		1.00	8.04	μA
				T _A = +85°C Resonator connection			1.31	8.23	
	IDD3	STOP mode ^{Note 7}	T _A = -40°C				0.18	0.52	μA
			T _A = +25°C				0.24	0.52	
			T _A = +50°C				0.33	2.21	
			T _A = +70°C				0.53	3.94	
			T _A = +85°C				0.93	7.95	

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main), LS (low-speed main), and LV (low-voltage main) modes.
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the LCD controller/driver, A/D converter, LVD circuit, comparator, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the real-time clock 2.

In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- 2. During HALT instruction execution by flash memory.
- 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- 4. When high-speed system clock and subsystem clock are stopped.
- When high-speed on-chip oscillator and high-speed system clock are stopped.
 When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 24 MHz
 - 2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
 - LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}@1 \text{ MHz}$ to 8 MHz
 - LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}@1 \text{ MHz}$ to 4 MHz
- 7. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fHOCO: High-speed on-chip oscillator clock frequency (48 MHz max.)
 - **3.** fin: High-speed on-chip oscillator clock frequency (24 MHz max.)
 - 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C



$(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol		Condition	MIN.	TYP.	MAX.	Unit		
Low-speed on- chip oscillator operating current	_{FIL} Note 1			0.20		μA			
RTC2 operating current	_{RTC} ^{Notes 1, 2,} 3	fsuв = 32.768 kHz		0.02		μA			
12-bit interval timer operating current	_{TMKA} Notes 1, 2, 4			0.04		μA			
Watchdog timer operating current	WDT ^{Notes 1, 2, 5}	fi∟ = 15 kHz					0.22		μA
A/D converter operating current	ADC ^{Notes 1, 6}	When conversion at maximum speed						1.7 0.7	mA mA
A/D converter reference voltage current	ADREF ^{Note 1}				75.0		μA		
Temperature sensor operating current	I _{TMPS} Note 1						75.0		μA
LVD operating current	LVD ^{Notes 1, 7}						0.08		μA
Comparator	_{CMP} Notes 1, 11	$V_{DD} = 5.0 V$, Regulator output	Window mode	e			12.5		μA
operating current			Comparator h	igh-speed mo	ode		6.5		μA
		voltage = 2.1 V	Comparator lo	ow-speed mo	de		1.7		μA
		V _{DD} = 5.0 V, Regulator output voltage = 1.8 V	Window mode	Э			8.0		μA
			Comparator h		4.0		μA		
			Comparator lo	ow-speed mo	de		1.3		μA
Self- programming operating current	FSP ^{Notes 1, 9}						2.00	12.20	mA
BGO operating current	BGO ^{Notes 1, 8}				2.00	12.20	mA		
SNOOZE	ISNOZ ^{Note 1}	ADC operation	ote 10		0.50	0.60	mA		
operating current				1.20	1.44	mA			
		Simplified SPI (CSI)/		0.70	0.84	mA			
LCD operating current	_{LCD1} Notes 1, 12, 13	External resistance division method	f _{LCD} = f _{SUB} LCD clock = 128 Hz	1/3 bias, four time slices	$V_{DD} = 5.0 V,$ $V_{L4} = 5.0 V$		0.04	0.20	μA
	_{LCD2} Note 1, 12	Internal voltage boosting method	f _{LCD} = fsuв LCD clock = 128 Hz	1/3 bias, four time slices	$V_{DD} = 3.0 V,$ $V_{L4} = 3.0 V$ $(V_{LCD} = 04H)$		0.85	2.20	μA
					$V_{DD} = 5.0 V,$ $V_{L4} = 5.1 V$ $(V_{LCD} = 12H)$		1.55	3.70	μA
	I _{LCD3} Note 1, 12	Capacitor split method	f _{LCD} = fsuв LCD clock = 128 Hz	1/3 bias, four time slices	V _{DD} = 3.0 V, V _{L4} = 3.0 V		0.20	0.50	μA

(Notes and Remarks are listed on the next page.)



- Notes 1. Current flowing to VDD.
 - 2. When high speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the real-time clock 2 (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The value of the current for the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock 2 operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of real-time clock 2.
 - 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The value of the current for the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and ITMKA, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
 - 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.
 - **6.** Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.
 - 7. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit operates.
 - 8. Current flowing only during data flash rewrite.
 - 9. Current flowing only during self programming.
 - 10. For shift time to the SNOOZE mode, see 21.3.3 SNOOZE mode in the RL78/L13 User's Manual.
 - **11.** Current flowing only to the comparator circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ICMP when the comparator circuit operates.
 - 12. Current flowing only to the LCD controller/driver. The value of the current for the RL78 microcontrollers is the sum of the supply current (IDD1 or IDD2) and LCD operating current (ILCD1, ILCD2, or ILCD3), when the LCD controller/driver operates in operation mode or HALT mode. However, not including the current flowing into the LCD panel. Conditions of the TYP. value and MAX. value are as follows.
 - Setting 20 pins as the segment function and blinking all
 - Selecting fsub for system clock when LCD clock = 128 Hz (LCDC0 = 07H)
 - Setting four time slices and 1/3 bias
 - **13.** Not including the current flowing into the external division resistor when using the external resistance division method.
- $\label{eq:result} \textbf{Remarks 1.} \hspace{0.1 in fill:} \hspace{0.1 in Low-speed on-chip oscillator clock frequency}$
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fcLK: CPU/peripheral hardware clock frequency
 - **4.** The temperature condition for the TYP. value is $T_A = 25^{\circ}C$.



2.4 AC Characteristics

(TA = -40 to +85°C, 1.6 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсү	Main system			$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.0417		1	μs
instruction execution time)		clock (f _{MAIN}) operation	main) mode	Э	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs
			LS (low-speed main) mode		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.125		1	μs
			LV (low-vol main) mode		$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.25		1	μs
		Subsystem clock (fsub) operation ^{Note}			$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	28.5	30.5	31.3	μs
		In the self programming mode			$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.0417		1	μs
			main) mode	9	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 2.7 \text{ V}$	0.0625		1	μs
			LS (low-spe main) mode		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.125		1	μs
			LV (low-vol main) mode	•	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.25		1	μs
External system clock	fex	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$			1.0		20.0	MHz	
frequency		$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$			1.0		16.0	MHz	
		$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 2.4 \text{ V}$			1.0		8.0	MHz	
		1.6 V ≤ V _{DD} < 1.8 V				1.0		4.0	MHz
	fexs		32		35	kHz			
External system clock input	t _{EXH} ,	$2.7 V \leq V_{DD} \leq 3$	24			ns			
high-level width, low-level width	texl	$2.4 V \leq V_{DD} < 2$	30			ns			
WIGHT		$1.8 V \leq V_{DD} < 2$	2.4 V			60			ns
		$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}$				120			ns
	texhs, texls					13.7			μs
TI00 to TI07 input high-level width, low-level width	tтıн, tтı∟					1/fмск+10			ns
TO00 to TO07, TKBO00,	fто	HS (high-speed main)		4.0	$V \le V_{DD} \le 5.5 V$			12	MHz
TKBO01-0 to TKBO01-2		mode	2.7		$V \leq V_{DD} < 4.0 V$			8	MHz
output frequency			ĺ	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$				4	MHz
		LV (low-voltage main) mode		1.6 V ≤ V _{DD} ≤ 5.5 V				2	MHz
		LS (low-speed main) mode		$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$				4	MHz
PCLBUZ0, PCLBUZ1 output	f PCL	HS (high-spee	ed main)	4.0	$V \le V_{DD} \le 5.5 V$			16	MHz
frequency		mode LV (low-voltage main) mode		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}$				8	MHz
				$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$				4	MHz
				$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$				4	MHz
				1.6 V ≤ V _{DD} < 1.8 V				2	MHz
		LS (low-speed main) mode		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$				4	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0 to INTP7 1.6		$V \le V_{DD} \le 5.5 V$	1			μs	
Key interrupt input high-level	tkrh, tkrl	KR0 to KR7		1.8	$V \leq V_{DD} \leq 5.5 V$	250			ns
width, low-level width				$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}$		1			μs
IH-PWM output restart input high-level width				2			fclk		
TMKB2 forced output stop input high-level width	tihr	INTP0 to INTP2			2			fс∟к	
RESET low-level width	tRSL					10			μs

(Note and Remark are listed on the next page.)



Note Operation is not possible if 1.6 V ≤ V_{DD} < 1.8 V in LV (low-voltage main) mode while the system is operating on the subsystem clock.

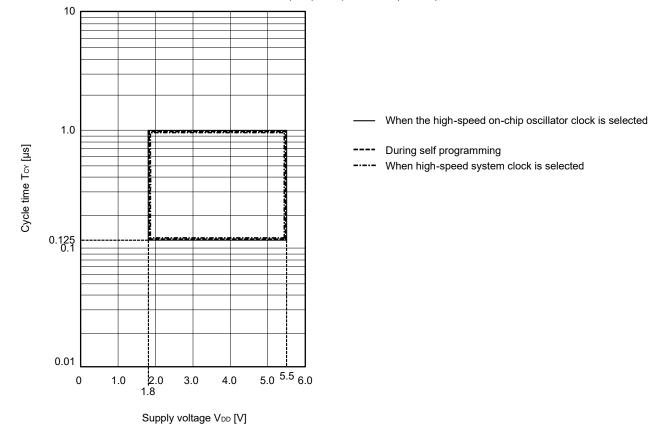
Remark fMCK: Timer array unit operation clock frequency (Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn) m: Unit number (m = 0), n: Channel number (n = 0 to 7))

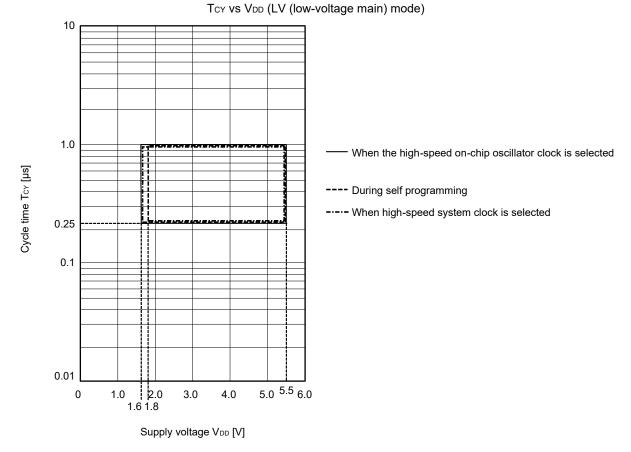
Minimum Instruction Execution Time during Main System Clock Operation

10 1.0 When the high-speed on-chip oscillator clock is selected Cycle time Tcv [µs] During self programming When high-speed system clock is selected ----0.1 0.0625 0.05 0.01 5.0 5.5 6.0 0 3.0 2.7 4.0 1.0 20 2.4 Supply voltage VDD [V]

TCY vs VDD (HS (high-speed main) mode)



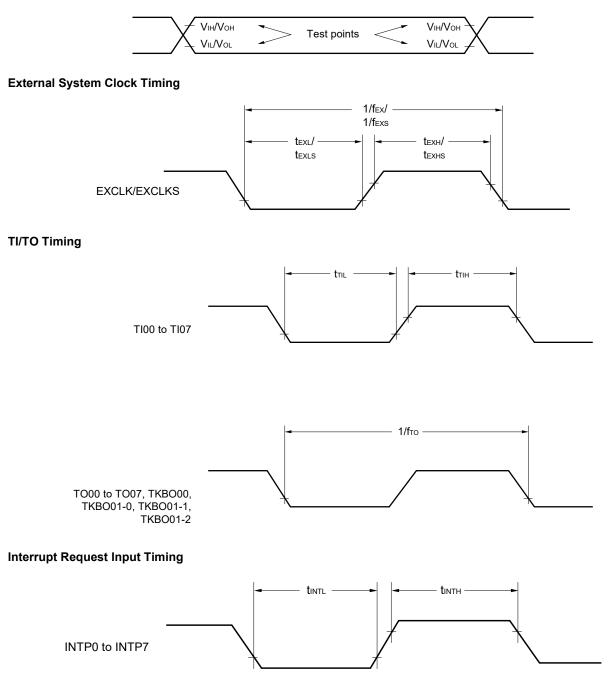




TCY vs VDD (LS (low-speed main) mode)

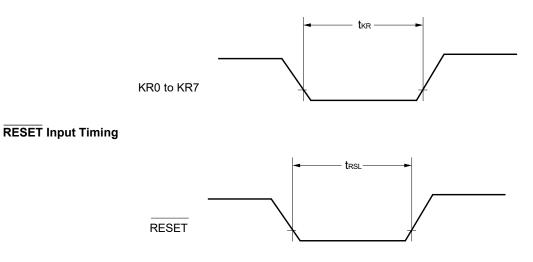


AC Timing Test Points





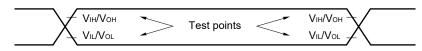
Key Interrupt Input Timing





2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode) ($T_A = -40$ to +85°C, 1.6 V $\leq V_{DD} \leq 5.5$ V, Vss = 0 V)

Parameter	Symbol	Conditions	, U			LS (low-speed main) Mode		LV (low-voltage main) Mode		
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Transfer rate ^{Note 1}		2.4 V≤ V _{DD} ≤ 5.5 V		fмск/6		fмск/6		fмск/6	bps	
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		4.0		1.3		0.6	Mbps	
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		-		fмск/6		fмск/6	bps	
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		-		1.3		0.6	Mbps	
		$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		_		-		f мск/6	bps	
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		_		-		0.6	Mbps	

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

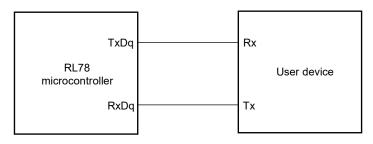
 HS (high-speed main) mode:
 $24 \text{ MHz} (2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V})$
 $16 \text{ MHz} (2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V})$

 LS (low-speed main) mode:
 $8 \text{ MHz} (1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V})$

 LV (low-voltage main) mode:
 $4 \text{ MHz} (1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V})$

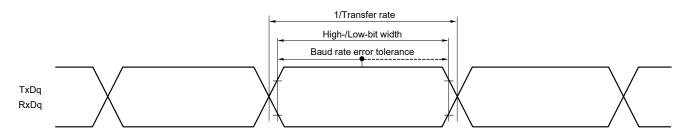
Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)





UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)

fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))



(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Co	onditions	HS (high- main) N	•	LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	167 ^{Note 1}		500 ^{Note 1}		1000 ^{Note 1}		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	250 ^{Note 1}		500 ^{Note 1}		1000 ^{Note 1}		ns
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	_		500 ^{Note 1}		1000 ^{Note 1}		ns
		$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	_		_		1000 ^{Note 1}		ns	
SCKp high-/low-level	t кн1,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	tkcy1/2-12		tkcy1/2-50		tkcy1/2-50		ns
width	t ĸ∟1	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	tkcy1/2-18		tkcy1/2-50		tkcy1/2-50		ns	
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	tkcy1/2-38		tkcy1/2-50		tkcy1/2-50		ns	
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	_		tkcy1/2-50		tkcy1/2-50		ns
		$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	_		_		tkcy1/2-100		ns
SIp setup time	tsik1	$2.7 V \leq V_{DD} \leq 5.$	5 V	44		110		110		ns
(to SCKp↑) ^{Note 2}		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	75		110		110		ns
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	_		110		110		ns
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	_		_		220		ns
SIp hold time	tksi1	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	19		19		19		ns
(from SCKp↑) ^{Note 3}		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	_		19		19		ns
		$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	_		_		19		ns
Delay time from	tkso1	C = 30 pF ^{Note 5}	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		25		25		25	ns
SCKp↓ to			$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		-		25		25	ns
SOp output ^{Note 4}			1.6 V ≤ V _{DD} ≤ 5.5 V		-		-		25	ns

Notes 1. The value must also be equal to or more than 2/fclk for CSI00 and equal to or more than 4/fclk for CSI10.

- **2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 10), m: Unit number (m = 0), n: Channel number (n = 0, 2), g: PIM and POM numbers (g = 0, 1)

> fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02))



(3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Cor	nditions		h-speed Mode	``	/-speed Mode	``	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	t ксү2	$4.0 V \leq V_{DD} \leq 5.5$	5 V fмск > 20 MHz	8/fмск		_		_		ns
time ^{Note 5}			fмск ≤ 20 MHz	6/f мск		6/fмск		6/fмск		ns
		$2.7 V \leq V_{DD} \leq 5.5$	5 V fмск > 16 MHz	8/f мск		_		_		ns
			fмск ≤ 16 MHz	6/fмск		6/fмск		6/fмск		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5$	6/fмск and 500		6/fмск		6/fмск		ns	
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5$	5 V	_		6/fмск		6/fмск		ns
		$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5$	_		_		6/fмск		ns	
SCKp high-/low-	SCKp high-/low- tkH2, 4.0		$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			tксү2/2-7		tксү2/2-7		ns
level width	tĸL2	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5$	5 V	tксү2/2-8		tксү2/2-8		tксү2/2-8		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5$	5 V	tксү2/2–18		tксү2/2–18		tксү2/2–18		ns
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.8$	5 V	_		tксү2/2–18		tксү2/2–18		ns
		$1.6 V \le V_{DD} \le 5.5$	5 V	_		-		tксү2/2–66		ns
SIp setup time	tsik2	$2.7 V \leq V_{DD} \leq 5.5$	1/fмск+20		1/fмск+30		1/fмск+30		ns	
(to SCKp↑) ^{Note 1}		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5$	5 V	1/fмск+30		1/fмск+30		1/fмск+30		ns
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.8$	5 V	-		1/fмск+30		1/fмск+30		ns
		$1.6 V \le V_{DD} \le 5.5$	5 V	-		-		1/fмск+40		ns
SIp hold time	tKSI2	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5$	5 V	1/fмск+31		1/fмск+31		1/fмск+31		ns
(from		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.8$	5 V	-		1/fмск+31		1/fмск+31		ns
SCKp↑) ^{Note 2}		$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5$	5 V	_		-		1/fмск+250		ns
Delay time from	tĸso2	C = 30 pF ^{Note 4}	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		2/fмск+44		2/fмск+110		2/fмск+110	ns
SCKp↓ to SOp output ^{Note 3}			$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		2/fмск+75		2/fмск+110		2/fмск+110	ns
ouiputione			$1.8~V \le V_{\text{DD}} \le 5.5~V$		-		2/fмск+110		2/fмск+110	ns
			$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		-		-		2/fмск+220	ns

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

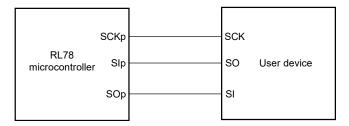
Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- **2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SOp output lines.
- 5. Transfer rate in SNOOZE mode: MAX. 1 Mbps

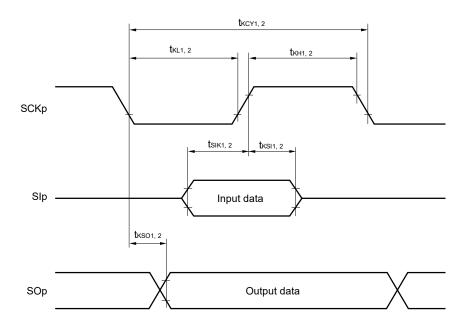
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 10), m: Unit number (m = 0), n: Channel number (n = 0, 2), g: PIM number (g = 0, 1)
 - fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02))

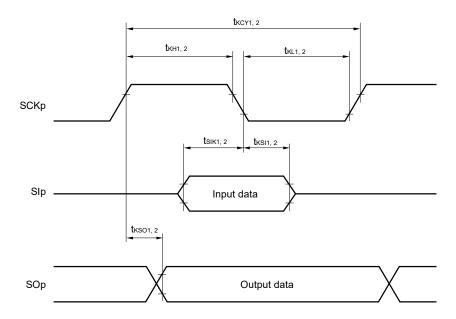
Simplified SPI (CSI) mode connection diagram (during communication at same potential)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 10)

2. m: Unit number, n: Channel number (mn = 00, 02)

(4) During communication at same potential (simplified I²C mode)

Parameter	Symbol	Conditions		h-speed Mode	-	v-speed Mode		-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fsc∟	2.7 V \leq V _{DD} \leq 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 ^{Note 1}		400 ^{Note 1}		400 ^{Note 1}	kHz
		$\begin{array}{l} 1.8 \ V \ (2.4 \ V^{\text{Note 3}}) \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{array}$		400 ^{Note 1}		400 ^{Note 1}		400 ^{Note 1}	kHz
		$1.8 \text{ V} (2.4 \text{ V}^{\text{Note 3}}) \le \text{V}_{\text{DD}} < 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$		300 ^{Note 1}		300 ^{Note 1}		300 ^{Note 1}	kHz
		1.6 V ≤ V _{DD} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ		-		-		250 ^{Note 1}	kHz
Hold time when t∟ow SCLr = "L"	t LOW	$\begin{array}{l} 2.7 \ V \leq V_{DD} \leq 5.5 \ V, \\ C_{b} = 50 \ pF, \ R_{b} = 2.7 \ k\Omega \end{array}$	475		1150		1150		ns
		$\begin{array}{l} 1.8 \; V \; (2.4 \; V^{\text{Note 3}}) \leq V_{\text{DD}} \leq 5.5 \; V, \\ C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 3 \; \text{k}\Omega \end{array}$	1150		1150		1150		ns
		$\begin{array}{l} 1.8 \; V \; (2.4 \; V^{\text{Note 3}}) \leq V_{\text{DD}} < 2.7 \; V, \\ C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 5 \; \text{k}\Omega \end{array}$	1550		1550		1550		ns
		$1.6 V ≤ V_{DD} < 1.8 V,$ C _b = 100 pF, R _b = 5 kΩ	-		-		1850		ns
Hold time when thick SCLr = "H"	tніgн	$2.7 V ≤ V_{DD} ≤ 5.5 V,$ C _b = 50 pF, R _b = 2.7 kΩ	475		1150		1150		ns
		1.8 V (2.4 V ^{Note 3}) \leq V _{DD} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		1150		1150		ns
		$\begin{array}{l} 1.8 \; V \; (2.4 \; V^{\text{Note 3}}) \leq V_{\text{DD}} < 2.7 \; V, \\ C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 5 \; \text{k}\Omega \end{array}$	1550		1550		1550		ns
		$1.6 V \le V_{DD} < 1.8 V,$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	-		-		1850		ns
Data setup time (reception)	tsu:dat	$\begin{array}{l} 2.7 \ V \leq V_{DD} \leq 5.5 \ V, \\ \mathbf{C}_{b} = 50 \ pF, \ R_{b} = 2.7 \ k\Omega \end{array}$	1/fмск+ 85 ^{Note 2}		1/fмск+ 145 ^{Note 2}		1/fмск+ 145 ^{Note 2}		ns
		$\begin{array}{l} 1.8 \; V \; (2.4 \; V^{\text{Note 3}}) \leq V_{\text{DD}} \leq 5.5 \; V, \\ C_{\text{b}} = 100 \; pF, \; R_{\text{b}} = 3 \; k\Omega \end{array}$	1/fмск+ 145 ^{Note 2}		1/fмск+ 145 ^{Note 2}		1/fмск+ 145 ^{Note 2}		ns
		$\label{eq:VDD} \begin{array}{l} 1.8 \; V \; (2.4 \; V^{\text{Note 3}}) \leq V_{\text{DD}} < 2.7 \; V, \\ C_{\text{b}} = 100 \; p\text{F}, \; R_{\text{b}} = 5 \; k\Omega \end{array}$	1/fмск+ 230 ^{Note 2}		1/f _{MCK} + 230 ^{Note 2}		1/fмск+ 230 ^{Note 2}		ns
		$1.6 V \le V_{DD} < 1.8 V,$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	-		-		1/f _{МСК} + 290 ^{Note 2}		ns
Data hold time (transmission)	thd:dat	$\begin{array}{l} 2.7 \ V \leq V_{DD} \leq 5.5 \ V, \\ C_{b} = 50 \ pF, \ R_{b} = 2.7 \ k\Omega \end{array}$	0	305	0	305	0	305	ns
		$\begin{array}{l} 1.8 \; V \; (2.4 \; V^{\text{Note 3}}) \leq V_{\text{DD}} \leq 5.5 \; V, \\ C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 3 \; \text{k}\Omega \end{array}$	0	355	0	355	0	355	ns
		$\begin{array}{l} 1.8 \; V \; (2.4 \; V^{\text{Note 3}}) \leq V_{\text{DD}} < 2.7 \; V, \\ C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 5 \; \text{k}\Omega \end{array}$	0	405	0	405	0	405	ns
		1.6 V ≤ V _{DD} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	-	-	-	_	0	405	ns

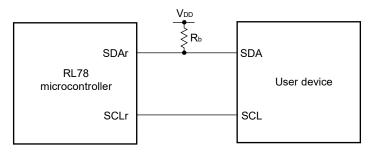
$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

(Notes, Caution, and Remarks are listed on the next page.)

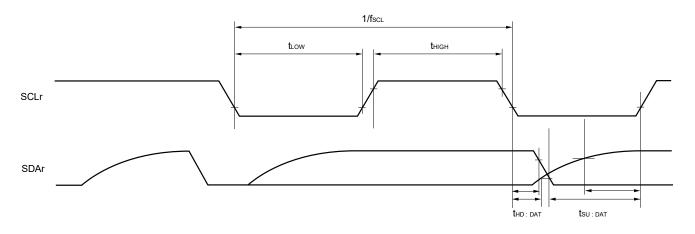


- Notes 1. The value must also be equal to or less than $f_{MCK}/4$.
 - 2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".
 - 3. Condition in the HS (high-speed main) mode
- Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- **Remarks 1.** R_b[Ω]: Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance
 - **2.** r: IIC number (r = 00, 10), g: PIM and POM number (g = 0, 1)
 - fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0-3), mn = 00-03, 10-13)



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

Parameter	Symbol	Conditions			HS (high-speed main) Mode		LS (low-speed main) Mode		LV (lo [.] mair	Unit	
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate	te Reception			$V \le V_{DD} \le 5.5 V,$ $V \le V_b \le 4.0 V$		f _{мск} /6 ^{Note 1}		fмск/6 ^{Note 1}		fмск/6 ^{Note 1}	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		4.0		1.3		0.6	Mbps	
				$7 V \le V_{DD} < 4.0 V,$ $3 V \le V_b \le 2.7 V$		f _{мск} /6 ^{Note 1}		fмск/6 ^{Note 1}		fмск/6 ^{Note 1}	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		4.0		1.3		0.6	Mbps	
			V,	$3 \vee (2.4 \vee^{Note 4}) \le \vee_{DD} < 3.3$ $5 \vee \le \vee_{b} \le 2.0 \vee$		fмск/6 Note s1, 2		fмск/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		4.0		1.3		0.6	Mbps	

Notes 1. Transfer rate in SNOOZE mode is 4800 bps only.

2. Use it with $V_{DD} \ge V_b$.

3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode:	24 MHz (2.7 V \leq V _{DD} \leq 5.5 V)
	16 MHz (2.4 V ≤ V _{DD} ≤ 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq V _{DD} \leq 5.5 V)
LV (low-voltage main) mode:	4 MHz (1.6 V \leq VDD \leq 5.5 V)

- 4. Condition in the HS (high-speed main) mode
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (Vbb tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** Vb[V]: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)
 - fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$
--

Parameter	Symbol			Conditions	Conditions HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate	ransfer rate Trans miss			$0 V \le V_{DD} \le 5.5 V$, .7 V $\le V_b \le 4.0 V$		Note 1		Note 1		Note 1	bps
				$\label{eq:transfer} \hline \begin{tabular}{lllllllllllllllllllllllllllllllllll$		2.8 ^{Note 2}		2.8 ^{Note 2}		2.8 ^{Note 2}	Mbps
				$.7 V \le V_{DD} < 4.0 V,$ $.3 V \le V_b \le 2.7 V$		Note 3		Note 3		Note 3	bps
				Theoretical value of the maximum transfer rate $(C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V})$		1.2 ^{Note 4}		1.2 ^{Note 4}		1.2 ^{Note 4}	Mbps
			1.8 V (2.4 V ^{Note 8}) \leq V _{DD} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V		Notes 5, 6		Notes 5, 6		Notes 5, 6	bps	
		$\label{eq:transfer} \begin{array}{l} \mbox{Theoretical value of the maximum} \\ \mbox{transfer rate} \\ \mbox{(C}_b = 50 \mbox{ pF}, \mbox{ R}_b = 5.5 \mbox{ k}\Omega, \mbox{ V}_b = 1.6 \mbox{ V}) \end{array}$		0.43 ^{Note 7}		0.43 ^{Note 7}		0.43 ^{Note 7}	Mbps		

Notes 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ and $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- **3.** The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq V_DD < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate } \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
- **5.** Use it with $V_{DD} \ge V_b$.

Notes 6. The smaller maximum transfer rate derived by using fMck/6 or the following expression is the valid maximum transfer rate.

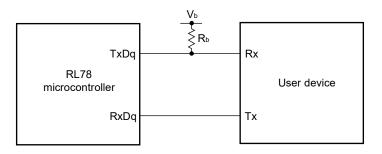
Expression for calculating the transfer rate when 1.8 V (2.4 V^{Note 8}) \leq V_{DD} < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

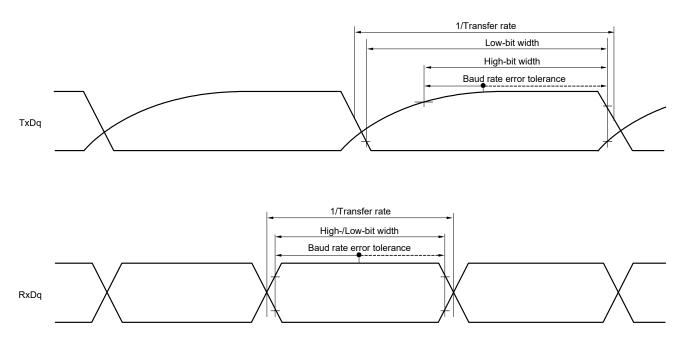
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.
- 8. Condition in the HS (high-speed main) mode
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)







UART mode bit width (during communication at different potential) (reference)

- Remarks 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)
 - **3.** fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))



RL78/L13

(6) Communication at different potential (2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Symbol	Conditions			h-speed Mode	``	/-speed Mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t ксү1	tксү1 ≥ 2/fclк	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 20 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	200		1150		1150		ns
			$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 20 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	300		1150		1150		ns
SCKp high-level width	tкнı	$4.0 V \le V_{DD} \le 5$ $C_b = 20 \text{ pF, } R_b$	5.5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ	tксү1/2 — 50		tксү1/2 — 50		tксү1/2 — 50		ns
		2.7 V ≤ V _{DD} < 4 C _b = 20 pF, R _b	$k.0 V, 2.3 V \le V_b \le 2.7 V,$ = 2.7 kΩ	tkcy1/2 - 120		tксү1/2 — 120		tксү1/2 — 120		ns
SCKp low-level width	tĸ∟ı	$4.0 V \le V_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b$	tkcy1/2 - 7		tксү1/2 — 50		tксү1/2 — 50		ns	
		2.7 V ≤ V _{DD} < 4 C _b = 20 pF, R _b	tксү1/2 — 10		tксү1/2 — 50		tксү1/2 — 50		ns	
SIp setup time (to SCKp↑) ^{Note 1}	•		5.5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ	58		479		479		ns
		$2.7 V \le V_{DD} < 4$ $C_b = 20 \text{ pF}, R_b$	l.0 V, 2.3 V ≤ V₅ ≤ 2.7 V, = 2.7 kΩ	121		479		479		ns
SIp hold time (from SCKp↑) ^{Note 1}	tksi1	$4.0 V \le V_{DD} \le 5$ $C_b = 20 \text{ pF, } R_b$	5.5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ	10		10		10		ns
		$2.7 V \le V_{DD} < 4$ $C_b = 20 \text{ pF}, R_b$	l.0 V, 2.3 V ≤ V₅ ≤ 2.7 V, = 2.7 kΩ	10		10		10		ns
Delay time from SCKp↓ to	tkso1	$4.0 V \le V_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b$	5.5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ		60		60		60	ns
SOp output ^{Note 1}		2.7 V ≤ V _{DD} < 4 C _b = 20 pF, R _b	l.0 V, 2.3 V ≤ V₅ ≤ 2.7 V, = 2.7 kΩ		130		130		130	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsik1	$4.0 V \le V_{DD} \le S_{C_b} = 20 \text{ pF, } R_b$	5.5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ	23		110		110		ns
		2.7 V ≤ V _{DD} < 4 C _b = 20 pF, R _b	l.0 V, 2.3 V ≤ V₅ ≤ 2.7 V, = 2.7 kΩ	33		110		110		ns
SIp hold time (from SCKp↓) ^{Note 2}	tksii	$4.0 V \le V_{DD} \le \xi$ $C_b = 20 \text{ pF, } R_b$	5.5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ	10		10		10		ns
		2.7 V ≤ V _{DD} < 4 C _b = 20 pF, R _b	$4.0 V, 2.3 V ≤ V_b ≤ 2.7 V,$ = 2.7 kΩ	10		10		10		ns
Delay time from SCKp↑ to	tkso1	$4.0 V \le V_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b$	5.5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ		10		10		10	ns
SOp output ^{Note 2}		2.7 V ≤ V _{DD} < 4 C _b = 20 pF, R _b	l.0 V, 2.3 V ≤ V _b ≤ 2.7 V, = 2.7 kΩ		10		10		10	ns

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

(Notes, Caution and Remarks are listed on the next page.)



- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
 - 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)
 - **3.** fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
 - **4.** This specification is valid only when CSI00's peripheral I/O redirect function is not used.



(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output) (1/2)

Parameter	Symbol			h-speed Mode	LS (low	/-speed Mode	LV (low main)	Unit		
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t ксү1	tксү1 ≥ 4/fc∟к	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	300		1150		1150		ns
			$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	500		1150		1150		ns
			$\begin{array}{l} 1.8 \; \forall \; (2.4 \; \forall^{\text{Note 1}}) \leq \forall_{\text{DD}} < 3.3 \\ \forall, \\ 1.6 \; \forall \leq \forall_{\text{b}} \leq 1.8 \; \forall^{\text{Note 2}}, \\ C_{\text{b}} = 30 \; \text{pF}, \; R_{\text{b}} = 5.5 \; \text{k}\Omega \end{array}$	1150		1150		1150		ns
SCKp high-level width	tĸн1	4.0 V ≤ V _{DD} ≤ C _b = 30 pF, R	5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, _{2b} = 1.4 kΩ	tксү1/2 — 75		tксү1/2 — 75		tксү1/2 — 75		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, R	tксү1/2 — 170		tксү1/2 — 170		tксү1/2 — 170		ns	
		$\begin{split} 1.8 \ V & (2.4 \ V^{\text{Note 1}}) \leq V_{\text{DD}} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ C_b &= 30 \ \text{pF}, \ R_b = 5.5 \ \text{k}\Omega \end{split}$				tксү1/2 — 458		tkcy1/2 — 458		ns
SCKp low-level tkL width	tĸ∟1	4.0 V ≤ V _{DD} ≤ C _b = 30 pF, R	tксү1/2 — 12		tксү1/2 — 50		tксү1/2 — 50		ns	
		2.7 V ≤ V _{DD} < C _b = 30 pF, R	4.0 V, 2.3 V \leq V _b \leq 2.7 V, $R_b = 2.7 \text{ k}\Omega$	tксү1/2 — 18		tксү1/2 — 50		tксү1/2 — 50		ns
		$1.8 V (2.4 V^{No})$ $1.6 V \le V_b \le 2$ $C_b = 30 \text{ pF, R}$		tkcy1/2 - 50		tксү1/2 — 50		tксү1/2 — 50		ns
SIp setup time (to SCKp↑) ^{Note 3}	tsıĸı	4.0 V ≤ V _{DD} ≤ C _b = 30 pF, R	5.5 V, 2.7 V \leq V _b \leq 4.0 V, B _b = 1.4 kΩ	81		479		479		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, R	4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	177		479		479		ns
		1.8 V (2.4 V ^N 1.6 V ≤ V _b ≤ 2 C _b = 30 pF, R		479		479		479		ns
SIp hold time (from SCKp↑) ^{Note 3}	tksi1	$4.0 V \le V_{DD} \le C_b = 30 \text{ pF, R}$	5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, _{Rb} = 1.4 kΩ	19		19		19		ns
		C₀ = 30 pF, R		19		19		19		ns
		1.8 V (2.4 V [№] 1.6 V ≤ V _b ≤ 2 C _b = 30 pF, R		19		19		19		ns
Delay time from SCKp↓ to	tkso1	$4.0 V \le V_{DD} \le C_b = 30 \text{ pF, R}$	$5.5 V, 2.7 V \le V_b \le 4.0 V,$ $R_b = 1.4 k\Omega$		100		100		100	ns
SOp output ^{Note 3}		2.7 V ≤ V _{DD} < C _b = 30 pF, R	4.0 V, 2.3 V \leq V _b \leq 2.7 V, $R_b = 2.7 \text{ k}\Omega$		195		195		195	ns
		1.8 V (2.4 V [№] 1.6 V ≤ V _b ≤ 2 C _b = 30 pF, R			483		483		483	ns

⁽TA = -40 to +85°C, 1.8 V \leq VDD \leq 5.5 V, Vss = 0 V)

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)



(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output) (2/2)

Parameter	Symbol	Conditions	、 U	h-speed Mode	``	/-speed Mode		-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note 4}	tsik1	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	44		110		110		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	44		110		110		ns
		$\begin{split} & 1.8 \ V \ (2.4 \ V^{\text{Note 1}}) \leq V_{\text{DD}} < 3.3 \ V, \\ & 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 2}}, \\ & C_{\text{b}} = 30 \ \text{pF}, \ R_{\text{b}} = 5.5 \ \text{k}\Omega \end{split}$	110		110		110		ns
SIp hold time (from SCKp↓) ^{Note 4}	t _{KSI1}	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$	19		19		19		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	19		19		19		ns
		$\begin{split} 1.8 \ V & (2.4 \ V^{\text{Note 1}}) \leq V_{\text{DD}} < 3.3 \ V, \\ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 2}}, \\ C_{\text{b}} &= 30 \ \text{pF}, \ R_{\text{b}} = 5.5 \ \text{k}\Omega \end{split}$	19		19		19		ns
Delay time from SCKp↑ to	tkso1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$		25		25		25	ns
SOp output ^{Note 4}		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		25		25		25	ns
		$\begin{split} 1.8 \ V & (2.4 \ V^{\text{Note 1}}) \leq V_{\text{DD}} < 3.3 \ V, \\ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 2}}, \\ C_{\text{b}} &= 30 \ \text{pF}, \ R_{\text{b}} = 5.5 \ \text{k}\Omega \end{split}$		25		25		25	ns

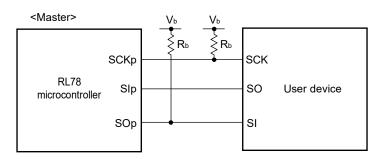
(TA = -40 to +85°C, 1.8 V \leq VDD \leq 5.5 V, Vss = 0 V)

Notes 1. Condition in HS (high-speed main) mode

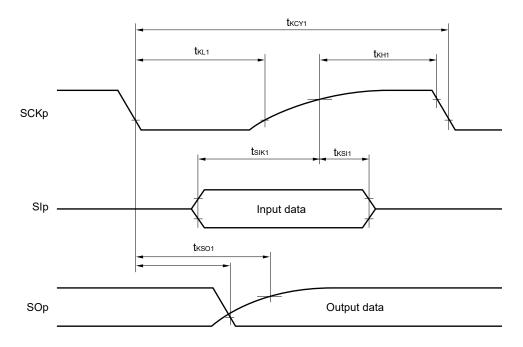
2. Use it with $V_{DD} \ge V_b$.

- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 4. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

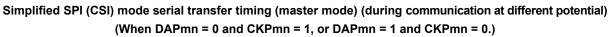
Simplified SPI (CSI) mode connection diagram (during communication at different potential)

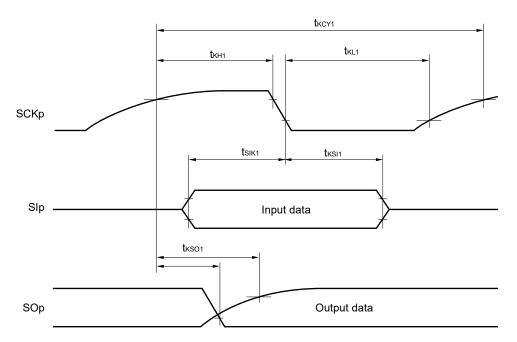






Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 10), m: Unit number , n: Channel number (mn = 00, 02), g: PIM and POM number (g = 0, 1)
 - **3.** fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

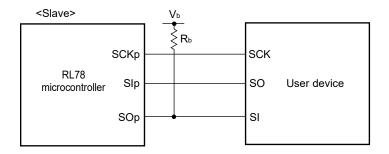
Parameter	Symbol	Co	nditions	HS (higl main)	•	•	/-speed Mode	LV (low main)	-	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	t ксү2	$4.0 V \le V_{DD} \le 5.5 V$,	20 MHz < fмск	12/fмск		_		_		ns
time ^{Note 1}		$2.7 V \leq V_b \leq$	8 MHz < fмск ≤ 20 MHz	10/ f мск		_		_		ns
		4.0 V	4 MHz < fмск ≤ 8 MHz	8/ f мск		16/fмск		_		ns
			fмск ≤ 4 MHz	6/fмск		10/fмск		10/fмск		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	20 MHz < fмск	16/ f мск		-		-		ns
		$2.3 V \leq V_b \leq$	16 MHz < fмск ≤ 20 MHz	14/fмск		-		_		ns
		2.7 V	8 MHz < fмск ≤ 16 MHz	12/fмск		-		_		ns
			4 MHz < fмск ≤ 8 MHz	8/fмск		16/fмск		-		ns
			fмск ≤ 4 MHz	6/fмск		10/fмск		10/ f мск		ns
		1.8 V (2.4 V ^{Note 2}) ≤	20 MHz < fмск	36/f мск		-		-		ns
		V _{DD} < 3.3 V,	16 MHz < fмск ≤ 20 MHz	32/fмск		-		_		ns
		1.6 V ≤ V _b ≤ 2.0 V ^{Note 3}	8 MHz < fмск ≤ 16 MHz	26/fмск		-		_		ns
		2.0 V	4 MHz < fмск ≤ 8 MHz	16/fмск		16/fмск		_		ns
			fмск ≤ 4 MHz	10/fмск		10/fмск		10/ f мск		ns
SCKp high-	tкн2,	$4.0 V \le V_{DD} \le 5.5 V, 2$	2.7 V ≤ V _b ≤ 4.0 V	tксү2/2		tксү2/2		tксү2/2		ns
/low-level width			- 12		- 50		- 50			
		$2.7 V \le V_{DD} < 4.0 V,$	$2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}$	tксү2/2 – 18		tксү2/2 - 50		tксү2/2 - 50		ns
		$1.8 \vee (2.4 \vee^{Note 2}) \leq \sqrt{1.6} \vee \leq \sqrt{b} \leq 2.0 \vee^{Note}$		tксү2/2 – 50		tксү2/2 - 50		tксү2/2 - 50		ns
SIp setup time (to SCKp↑) ^{Note 4}	tsık2	$4.0 V \le V_{DD} \le 5.5 V, 2$		1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	$2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$1.8 \vee (2.4 \vee^{Note 2}) \leq \vee$ $1.6 \vee \leq V_b \leq 2.0 \vee^{Note}$		1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
SIp hold time (from	tksi2	$4.0 V \le V_{DD} \le 5.5 V, 2$	$2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V}$	1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
SCKp↑) ^{Note 5}		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	$2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}$	1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
		$1.8 \vee (2.4 \vee^{Note 2}) \leq V$ $1.6 \vee \leq V_b \leq 2.0 \vee^{Note}$		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to	tĸso2	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 100 \text{ C}_{\text{b}} = 30 \text{ pF}, \text{R}_{\text{b}} = 1.4 \text{ C}_{\text{b}}$			2/fмск + 120		2/fмск + 573		2/fмск + 573	ns
SOp output ^{Note 6} 2.7 V	$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ cm}$			2/fмск + 214		2/fмск + 573		2/fмск + 573	ns	
		$\begin{array}{l} 1.8 \ V \ (2.4 \ V^{\text{Note 2}}) \leq V \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note}} \\ C_b = 30 \ p\text{F}, \ R_b = 5.5 \end{array}$	3 ,		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

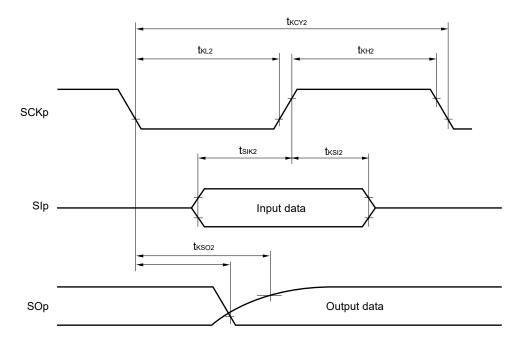
(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

- Notes 1. Transfer rate in SNOOZE mode: MAX. 1 Mbps
 - 2. Condition in HS (high-speed main) mode
 - **3.** Use it with $V_{DD} \ge V_b$.
 - **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **6.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[†]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

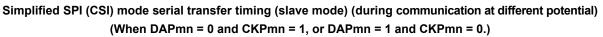
Simplified SPI (CSI) mode connection diagram (during communication at different potential)

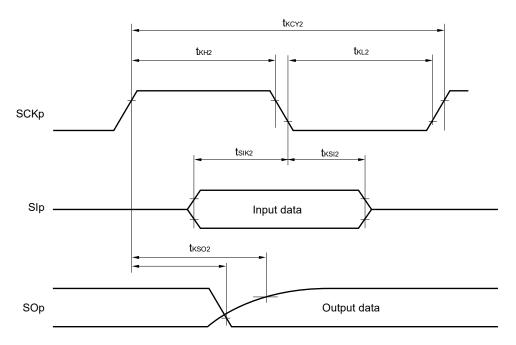


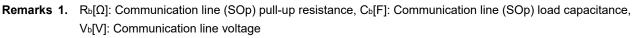




Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)







- p: CSI number (p = 00, 10), m: Unit number, n: Channel number (mn = 00, 02),
 g: PIM and POM number (g = 0, 1)
- fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn) m: Unit number, n: Channel number (mn = 00, 02))

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	,	gh-speed ı) Mode	-	w-speed) Mode		/-voltage) Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscl	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		1000 ^{Note 1}		300 ^{Note 1}		300 ^{Note 1}	kHz
		2.7 V \leq V _{DD} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 ^{Note 1}		300 ^{Note 1}		300 ^{Note 1}	kHz
		4.0 V \leq V _{DD} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ		400 ^{Note 1}		300 ^{Note 1}		300 ^{Note 1}	kHz
		$2.7 V \le V_{DD} < 4.0 V,$ $2.3 V \le V_b \le 2.7 V,$ $C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		400 ^{Note 1}		300 ^{Note 1}		300 ^{Note 1}	kHz
		$\begin{split} & 1.8 \ V \ (2.4 \ V^{\text{Note } 2}) \leq V_{\text{DD}} < 3.3 \ V, \\ & 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note } 3}, \\ & C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 5.5 \ \text{k}\Omega \end{split}$		300 ^{Note 1}		300 ^{Note 1}		300 ^{Note 1}	kHz
Hold time when SCLr = "L"	t∟ow	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	475		1550		1550		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	475		1550		1550		ns
		$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$	1150		1550		1550		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1150		1550		1550		ns
		$\begin{split} & 1.8 \ \text{V} \ (2.4 \ \text{V}^{\text{Note 2}}) \leq \text{V}_{\text{DD}} < 3.3 \ \text{V}, \\ & 1.6 \ \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \ \text{V}^{\text{Note 3}}, \\ & \text{C}_{\text{b}} = 100 \ \text{pF}, \ \text{R}_{\text{b}} = 5.5 \ \text{k}\Omega \end{split}$	1550		1550		1550		ns
Hold time when SCLr = "H"	tніgн	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	245		610		610		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	200		610		610		ns
		$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$	675		610		610		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	600		610		610		ns
		$\begin{split} 1.8 \ V & (2.4 \ V^{\text{Note } 2}) \leq V_{\text{DD}} < 3.3 \ V, \\ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note } 3}, \\ C_{\text{b}} &= 100 \ \text{pF}, \ R_{\text{b}} = 5.5 \ \text{k}\Omega \end{split}$	610		610		610		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)



(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)

Parameter	Symbol	Conditions	HS (high main)		LS (low main)	•	LV (low- main)	-	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/f _{мск+} 135 ^{Note 4}		1/f _{МСК} + 190 ^{Note 4}		1/f _{МСК} + 190 ^{Note 4}		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/f _{МСК} + 135 ^{Note 4}		1/f _{МСК} + 190 ^{Note 4}		1/f _{МСК} + 190 ^{Note 4}		ns
		4.0 V \leq V _{DD} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	1/f _{МСК} + 190 ^{Note 4}		1/f _{МСК} + 190 ^{Note 4}		1/f _{МСК} + 190 ^{Note 4}		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/f _{мск+} 190 ^{Note 4}		1/f _{МСК} + 190 ^{Note 4}		1/f _{МСК} + 190 ^{Note 4}		ns
		$\begin{split} & 1.8 \ V \ (2.4 \ V^{\text{Note } 2}) \leq V_{\text{DD}} < 3.3 \ V, \\ & 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note } 3}, \\ & C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 5.5 \ \text{k}\Omega \end{split}$	1/f _{МСК} + 190 ^{Note 4}		1/f _{МСК} + 190 ^{Note 4}		1/f _{МСК} + 190 ^{Note 4}		ns
Data hold time (transmission)	thd:dat	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	305	0	305	0	305	ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	305	0	305	0	305	ns
		$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$	0	355	0	355	0	355	ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	355	0	355	0	355	ns
		$ \begin{split} & 1.8 \ \text{V} \ (2.4 \ \text{V}^{\text{Note 2}}) \leq \text{V}_{\text{DD}} < 3.3 \ \text{V}, \\ & 1.6 \ \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \ \text{V}^{\text{Note 3}}, \\ & \text{C}_{\text{b}} = 100 \ \text{pF}, \ \text{R}_{\text{b}} = 5.5 \ \text{k}\Omega \end{split} $	0	405	0	405	0	405	ns

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

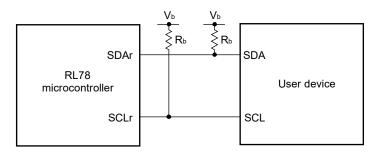
- 2. Condition in HS (high-speed main) mode
- **3.** Use it with $V_{DD} \ge V_b$.
- **4.** Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".
- Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

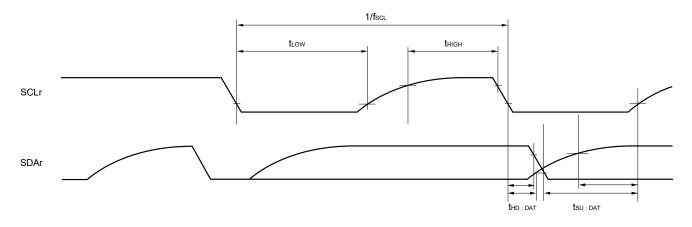


RL78/L13

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remarks 1.** R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage
 - **2.** r: IIC number (r = 00, 10), g: PIM, POM number (g = 0, 1)
 - fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00, 02)



2.5.2 Serial interface IICA

(1) I²C standard mode (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	C	Conditions		h-speed Mode	-	/-speed Mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock	fsc∟	Normal	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0	100	0	100	0	100	kHz
frequency		mode: fcьк ≥ 1 MHz	1.8 V (2.4 V ^{Note 3}) ≤ V _{DD} ≤ 5.5 V	0	100	0	100	0	100	kHz
			$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	-	_	_	_	0	100	kHz
Setup time of	tsu:sta	2.7 V ≤ V _{DD} ≤	≤5.5 V	4.7		4.7		4.7		μs
restart condition		1.8 V (2.4 V	Note ³) \leq V _{DD} \leq 5.5 V	4.7		4.7		4.7		μs
		1.6 V ≤ V _{DD} ≤	≤5.5 V	_	_	_	_	4.7		μs
Hold time ^{Note 1}	thd:sta	2.7 V ≤ V _{DD} ≤	≤5.5 V	4.0		4.0		4.0		μs
		1.8 V (2.4 V	Note 3) \leq VDD \leq 5.5 V	4.0		4.0		4.0		μs
		1.6 V ≤ V _{DD} ≤	≤5.5 V	_	_	_	_	4.0		μs
Hold time when	t∟ow	2.7 V ≤ V _{DD} ≤	≤5.5 V	4.7		4.7		4.7		μs
SCLA0 = "L"		1.8 V (2.4 V	Note 3) \leq VDD \leq 5.5 V	4.7		4.7		4.7		μs
		1.6 V ≤ V _{DD} ≤	≤5.5 V	_	_	_	_	4.7		μs
Hold time when	tніgн	2.7 V ≤ V _{DD} ≤	≤5.5 V	4.0		4.0		4.0		μs
SCLA0 = "H"		1.8 V (2.4 V	Note 3) \leq VDD \leq 5.5 V	4.0		4.0		4.0		μs
		1.6 V ≤ V _{DD} ≤	≤ 5.5 V	-	_	_	_	4.0		μs

(Notes, Caution and Remark are listed on the next page.)



(1) I²C standard mode (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditions	Conditions HS (high-speed LS (low-speed LV (low-v main) Mode main) Mode main) M		•	Unit			
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time	tsu:dat	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	250		250		250		ns
(reception)		$1.8 \text{ V} (2.4 \text{ V}^{\text{Note 3}}) \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	250		250		250		ns
		$1.6 V \le V_{DD} \le 5.5 V$	_	_	_	_	250		ns
Data hold time	thd:dat	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0	3.45	0	3.45	0	3.45	μs
(transmission) ^{Note 2}		$1.8 \text{ V} (2.4 \text{ V}^{\text{Note 3}}) \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	0	3.45	0	3.45	0	3.45	μs
		1.6 V ≤ V _{DD} ≤ 5.5 V	_	_	_	_	0	3.45	μs
Setup time of stop	tsu:sto	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	4.0		4.0		4.0		μs
condition		$1.8 \text{ V} (2.4 \text{ V}^{\text{Note 3}}) \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	4.0		4.0		4.0		μs
		1.6 V ≤ V _{DD} ≤ 5.5 V	_	_	_	_	4.0		μs
Bus-free time	t BUF	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	4.7		4.7		4.7		μs
		$1.8 \text{ V} (2.4 \text{ V}^{\text{Note 3}}) \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	4.7		4.7		4.7		μs
		$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	_	_	_	_	4.7		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the:DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

- 3. Condition in HS (high-speed main) mode
- Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 k Ω



(2) I²C fast mode

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	C	Conditions		h-speed Mode	``	/-speed Mode	`	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fclk	2.7 V ≤ V _{DD} ≤ 5.5 V	0	400	0	400	0	400	kHz
		≥ 3.5 MHz	1.8 V (2.4 V ^{Note 3}) ≤ V _{DD} ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of	tsu:sta	2.7 V ≤ V _{DD}	≤ 5.5 V	0.6		0.6		0.6		μs
restart condition		1.8 V (2.4 V	Note ³) \leq V _{DD} \leq 5.5 V	0.6		0.6		0.6		μs
Hold time ^{Note 1}	thd:sta	2.7 V ≤ V _{DD}	≤ 5.5 V	0.6		0.6		0.6		μs
		1.8 V (2.4 V	Note ³) \leq V _{DD} \leq 5.5 V	0.6		0.6		0.6		μs
Hold time when	t LOW	2.7 V ≤ V _{DD}	≤ 5.5 V	1.3		1.3		1.3		μs
SCLA0 ="L"		1.8 V (2.4 V	Note ³) \leq V _{DD} \leq 5.5 V	1.3		1.3		1.3		μs
Hold time when	tніgн	$2.7 \text{ V} \leq \text{V}_{\text{DD}}$	≤ 5.5 V	0.6		0.6		0.6		μs
SCLA0 ="H"		1.8 V (2.4 V	Note ³) \leq V _{DD} \leq 5.5 V	0.6		0.6		0.6		μs
Data setup time	tsu:dat	2.7 V ≤ V _{DD}	≤ 5.5 V	100		100		100		ns
(reception)		1.8 V (2.4 V	Note ³) \leq V _{DD} \leq 5.5 V	100		100		100		ns
Data hold time	thd:dat	2.7 V ≤ V _{DD}	≤ 5.5 V	0	0.9	0	0.9	0	0.9	μs
(transmission) ^{Note 2}		1.8 V (2.4 V	Note ³) \leq V _{DD} \leq 5.5 V	0	0.9	0	0.9	0	0.9	μs
Setup time of stop	tsu:sto	$2.7 \text{ V} \leq \text{V}_{\text{DD}}$	≤ 5.5 V	0.6		0.6		0.6		μs
condition		1.8 V (2.4 V	Note ³) \leq V _{DD} \leq 5.5 V	0.6		0.6		0.6		μs
Bus-free time	t BUF	2.7 V ≤ V _{DD}	≤ 5.5 V	1.3		1.3		1.3		μs
		1.8 V (2.4 V	Note ³) \leq V _{DD} \leq 5.5 V	1.3		1.3		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the:DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

- **3.** Condition in HS (high-speed main) mode
- Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 k Ω



(3) I²C fast mode plus

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions		n-speed Mode	-	/-speed Mode		-voltage Mode	Unit		
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.			
SCLA0 clock frequency	fscL	Fast mode plus: fc⊥ĸ ≥ 10 MHz	2.7 V ≤ V _{DD} ≤ 5.5 V	0	1000	-		_		kHz		
Setup time of restart condition	tsu:sta	2.7 V ≤ V _{DD} ≤	≦5.5 V	0.26		-		-		-		μs
Hold time ^{Note 1}	thd:sta	2.7 V ≤ V _{DD} ≤	≦5.5 V	0.26		-	_	-	_	μs		
Hold time when SCLA0 ="L"	t∟ow	2.7 V ≤ V _{DD} ≤	≤5.5 V	0.5				-				
Hold time when SCLA0 ="H"	tніgн	2.7 V ≤ V _{DD} ≤	≤5.5 V	0.26			-	-	-	μs		
Data setup time (reception)	tsu:dat	2.7 V ≤ V _{DD} ≤	\$5.5 V	50			_	-	_	ns		
Data hold time (transmission) ^{Note 2}	thd:dat	2.7 V ≤ V _{DD} ≤	\$5.5 V	0	0.45		_		_	μs		
Setup time of stop condition	tsu:sto	2.7 V ≤ V _{DD} ≤	\$5.5 V	0.26			_		_	μs		
Bus-free time	t BUF	2.7 V ≤ V _{DD} ≤	5.5 V	0.5			_	-	_	μs		

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

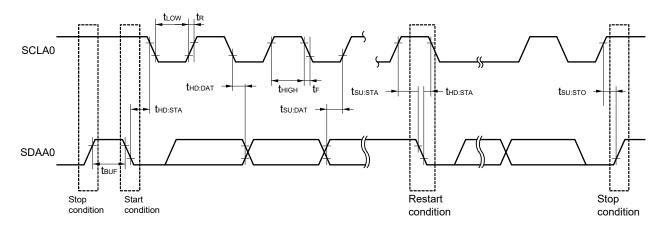
2. The maximum value (MAX.) of the:DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: C_b = 120 pF, R_b = 1.1 k Ω



IICA serial transfer timing





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2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (–) = Vss	Reference voltage (+) = VBGR Reference voltage (–) = AVREFM
ANIO, ANI1	_	See 2.6.1 (2) .	See 2.6.1 (3) .
ANI16 to ANI25	See 2.6.1 (1) .		
Internal reference voltage Temperature sensor output voltage	See 2.6.1 (1) .		_

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pins: ANI16 to ANI25, internal reference voltage, and temperature sensor output voltage

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V}, \text{ Reference voltage (+) = AV}_{REFP}, \text{ Reference voltage (-) = } \text{ of } (T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V}, \text{ Reference voltage (+) = } \text{AV}_{REFP}, \text{ Reference voltage (-) = } \text{ of } (T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V}, \text{ Reference voltage (+) = } \text{AV}_{REFP}, \text{ Reference voltage (-) = } \text{AV}_{REFP}$
AVREFM = 0 V)

Parameter	Symbol	0	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	$1.8 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$		±1.2	±5.0	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}^{\text{Note 4}}$		±1.2	10 ±5.0 ±8.5 39 39 39 39 39 39 39 39 39 39 39 39 39 39 39 39 39 10.0 ±0.35 ±0.60 ±0.60 ±0.60 ±0.60 ±0.60 ±2.5 AVREFP	LSB
Conversion time	t CONV	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin:	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.1875		39	μs
		ANI16 to ANI25	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
			$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	57		95	μs
		10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.375		39	μs
		Target pin: Internal	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.5625		39	μs
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale errorNotes 1, 2	Ezs	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
		AV _{REFP} = V _{DD} ^{Note 3}	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}^{\text{Note 4}}$			±0.60	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution	$1.8 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$			±0.35	%FSR
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}^{\text{Note 4}}$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$1.8 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$			±3.5	LSB
		AV _{REFP} = V _{DD} ^{Note 3}	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}^{\text{Note 4}}$			±6.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	$1.8 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$			±2.0	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}^{\text{Note 4}}$			±2.5	LSB
Analog input voltage	VAIN	ANI16 to ANI25		0		AVREFP	V
		Internal reference vol (2.4 V \leq V _{DD} \leq 5.5 V,	tage HS (high-speed main) mode))		±0.60 ±0.35 ±0.60 ±3.5 ±6.0 ±2.0 ±2.5 AVREFP VBGR ^{Note 5}	V	
		Temperature sensor out (2.4 V \leq V _{DD} \leq 5.5 V, H	output voltage HS (high-speed main) mode))	,	V _{TMPS25} Note 5		V

(Notes are listed on the next page.)



Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.

 Overall error:
 Add ±4 LSB to the MAX. value when AV_{REFP} = V_{DD}.

 Zero-scale error/Full-scale error:
 Add ±0.2%FSR to the MAX. value when AV_{REFP} = V_{DD}.

 Integral linearity error/ Differential linearity error:
 Add ±2 LSB to the MAX. value when AV_{REFP} = V_{DD}.
- 4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).
- 5. See 2.6.2 Temperature sensor/internal reference voltage characteristics.



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(2) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{ss} (ADREFM = 0), target pins: ANI0, ANI1, ANI16 to ANI25, internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Со	nditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Notes 1, 2}	AINL	10-bit resolution	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		±1.2	±7.0	LSB
			$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}^{\text{Note 3}}$		±1.2	±10.5	LSB
Conversion time	t _{CONV}	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin:	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.1875		39	μs
		ANI0, ANI1, ANI16 to ANI25 ^{Note 3}	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
			$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	57		95	μs
		10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.375		39	μs
		Target pin: Internal	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.5625		39	μs
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.60	%FSR
			1.6 V \leq V _{DD} \leq 5.5 V ^{Note 3}			±0.85	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.60	%FSR
			$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}^{\text{Note 3}}$			±0.85	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±4.0	LSB
			$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}^{\text{Note 3}}$			±6.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±2.0	LSB
			$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}^{\text{Note 3}}$			±2.5	LSB
Analog input voltage	VAIN	ANI0, ANI1, ANI16 to A	NI25	0		Vdd	V
nalog input voltage		Internal reference volta (2.4 V \leq V _{DD} \leq 5.5 V, HS	V _{BGR} Note 4			V	
		Temperature sensor output voltage (2.4 V \leq V _{DD} \leq 5.5 V, HS (high-speed main) mode))			/TMPS25 ^{Note}	4	V

T 40 to 105°C 4 6 V < V < E E V	/ Vaa = 0.V/ Deference veltere /+	-) = VDD, Reference voltage (-) = Vss)
 $IA = -40 IO + 05 C. 1.0 V \ge VDD \ge 5.5 V$	\cdot vss = 0 v. Reference voltage (τ	-) = vDD. Reference voltage (-) = vss)

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).

4. See 2.6.2 Temperature sensor/internal reference voltage characteristics.



(3) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pins: ANI0, ANI16 to ANI25

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{\text{BGR}^{\text{Note 3}}},$ Reference voltage (-) = AV_{REFM}^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±1.0	LSB
Analog input voltage	VAIN			0		$V_{\text{BGR}}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. See 2.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage $(-) = V_{SS}$, the MAX. values are as follows.Zero-scale error:Add $\pm 0.35\%$ FSR to the AVREFM MAX. value.Integral linearity error:Add ± 0.5 LSB to the AVREFM MAX. value.Differential linearity error:Add ± 0.2 LSB to the AVREFM MAX. value.



2.6.2 Temperature sensor /internal reference voltage characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	ADS register = 80H, T _A = +25°C		1.05		V
Internal reference output voltage	VBGR	ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvtmps	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp				5	μs

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{HS (high-speed main) mode)}$

2.6.3 Comparator characteristics

(TA = -40 to +85°C, 1.6 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
Input voltage range	lvref					Vdd – 1.4	V
	lvcmp			-0.3		V _{DD} + 0.3	V
Output delay	td	V _{DD} = 3.0 V Input slew rate > 50 mV/µs	Comparator high-speed mode, standard mode			1.2	μs
			Comparator high-speed mode, window mode			2.0	μs
			Comparator low-speed mode, standard mode		3.0	5.0	μs
High-electric-potential reference voltage	VTW+	Comparator high-speed mod window mode	omparator high-speed mode, indow mode		0.76Vdd	0.86Vdd	V
Low-electric-potential reference voltage	VTW–	Comparator high-speed mod window mode	omparator high-speed mode, indow mode		0.24V _{DD}	0.34Vdd	V
Operation stabilization wait time	tсмр						μs
Internal reference output voltage ^{Note}	Vbgr	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \text{ HS}$ (high	n-speed main) mode	1.38	1.45	1.50	V

Note Cannot be used in LS (low-speed main) mode, LV (low-voltage main) mode, subsystem clock operation, and STOP mode.

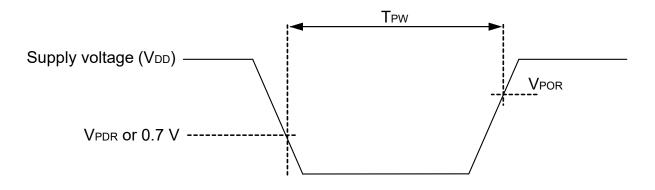


2.6.4 POR circuit characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	The power supply voltage is rising.	1.47	1.51	1.55	V
	VPDR	The power supply voltage is falling.	1.46	1.50	1.54	V
Minimum pulse width ^{Note}	TPW		300			μs

Note This is the time required for the POR circuit to execute a reset operation when V_{DD} falls below V_{PDR}. When the microcontroller enters STOP mode and when the main system clock (f_{MAIN}) has been stopped by setting bit 0 (HIOSTOP) and bit 7 (MSTOP) of the clock operation status control register (CSC), this is the time required for the POR circuit to execute a reset operation between when V_{DD} falls below 0.7 V and when V_{DD} rises to V_{POR} or higher.





2.6.5 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(T_A = -40 to +85°C, V_{PDR} \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	VLVD0	When power supply rises	3.98	4.06	4.14	V
voltage			When power supply falls	3.90	3.98	4.06	V
		VLVD1	When power supply rises	3.68	3.75	3.82	V
			When power supply falls	3.60	3.67	3.74	V
		VLVD2	When power supply rises	3.07	3.13	3.19	V
			When power supply falls	3.00	3.06	3.12	V
		VLVD3	When power supply rises	2.96	3.02	3.08	V
			When power supply falls	2.90	2.96	3.02	V
		VLVD4	When power supply rises	2.86	2.92	2.97	V
			When power supply falls	2.80	2.86	2.91	V
		VLVD5	When power supply rises	2.76	2.81	2.87	V
			When power supply falls	2.70	2.75	2.81	V
		VLVD6	When power supply rises	2.66	2.71	2.76	V
			When power supply falls	2.60	2.65	2.70	V
		VLVD7	When power supply rises	2.56	2.61	2.66	V
			When power supply falls	2.50	2.55	2.60	V
		VLVD8	When power supply rises	2.45	2.50	2.55	V
			When power supply falls	2.40	2.45	2.50	V
		VLVD9	When power supply rises	2.05	2.09	2.13	V
			When power supply falls	2.00	2.04	2.08	V
		VLVD10	When power supply rises	1.94	1.98	2.02	V
			When power supply falls	1.90	1.94	1.98	V
		VLVD11	When power supply rises	1.84	1.88	1.91	V
			When power supply falls	1.80	1.84	1.87	V
		VLVD12	When power supply rises	1.74	1.77	1.81	V
			When power supply falls	1.70	1.73	1.77	V
		VLVD13	When power supply rises	1.64	1.67	1.70	V
			When power supply falls	1.60	1.63	1.66	V
Minimum pu	Ilse width	tLw		300			μs
Detection de	elay time					300	μs



LVD Detection Voltage of Interrupt & Reset Mode

(T_A = -40 to +85°C, V_{PDR} \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol		Cond	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVD13	Vpoc2,	VPOC1, VPOC0 = 0, 0, 0,	falling reset voltage	1.60	1.63	1.66	V
mode	VLVD12		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVD11		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	VLVD4		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVD11	Vpoc2,	VPOC1, VPOC0 = 0, 0, 1,	falling reset voltage	1.80	1.84	1.87	V
	VLVD10		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	VLVD9		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
VLVD2		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V	
			Falling interrupt voltage	3.00	3.06	3.12	V	
	VLVD8	Vpoc2,	DC2, VPOC1, VPOC0 = 0, 1, 0, falling reset voltage	falling reset voltage	2.40	2.45	2.50	V
	VLVD7		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	VLVD6		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	VLVD1		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	VLVD5	VPOC2,	VPOC1, VPOC0 = 0, 1, 1,	falling reset voltage	2.70	2.75	2.81	V
	VLVD4		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVD3		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	VLVD0		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.6.6 Supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
VDD rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.



2.7 LCD Characteristics

2.7.1 External resistance division method

(1) Static display mode

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, V_{L4} \text{ (MIN.)} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.0		Vdd	V

(2) 1/2 bias method, 1/4 bias method

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, V_{L4} \text{ (MIN.)} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.7		Vdd	V

(3) 1/3 bias method

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, V_{L4} \text{ (MIN.)} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.5		Vdd	V



2.7.2 Internal voltage boosting method

(1) 1/3 bias method

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	VL1	C1 to C4 ^{Note 1}	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 µF ^{Note 2}	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	VL2	C1 to C4 ^{Note 1} =	0.47 µF	2 V _{L1} – 0.10	2 VL1	2 VL1	V
Tripler output voltage	VL4	C1 to C4 ^{Note 1} =	0.47 µF	3 VL1 – 0.15	3 VL1	3 VL1	V
Reference voltage setup time ^{Note 2}	tvwait1			5			ms
Voltage boost wait time ^{Note 3}	tvwait2	C1 to C4 ^{Note 1} =	0.47 µF	500			ms

Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between $V_{\mbox{\tiny L1}}$ and GND

C3: A capacitor connected between $V_{\mbox{\tiny L2}}$ and GND

C4: A capacitor connected between $V_{{\scriptscriptstyle L}4}$ and GND

C1 = C2 = C3 = C4 = 0.47 µF ± 30 %

- 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

(2) 1/4 bias method

$(T_A = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	VL1	C1 to C5 ^{Note 1}	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 µF ^{Note 2}	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
Doubler output voltage	VL2	C1 to C5 ^{Note 1} =	0.47 µF	2 VL1-0.08	2 VL1	2 VL1	V
Tripler output voltage	VL3	C1 to C5 ^{Note 1} =	0.47 µF	3 VL1-0.12	3 VL1	3 VL1	V
Quadruply output voltage	VL4	C1 to C5 ^{Note 1} =	0.47 µF	4 VL1-0.16	4 VL1	4 VL1	V
Reference voltage setup time ^{Note 2}	tvwait1			5			ms
Voltage boost wait time ^{Note 3}	tvwait2	C1 to C5 ^{Note 1} =	0.47 µF	500			ms

Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

- C2: A capacitor connected between $V_{\mbox{\tiny L1}}$ and GND
- C3: A capacitor connected between V_{L2} and GND
- C4: A capacitor connected between $V_{\mbox{\tiny L3}}$ and GND
- C5: A capacitor connected between $V_{{\scriptscriptstyle L4}}$ and GND
- $C1 = C2 = C3 = C4 = C5 = 0.47 \ \mu\text{F} \pm 30\%$
- 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).



2.7.3 Capacitor split method

(1) 1/3 bias method

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.2 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
VL4 voltage	VL4	C1 to C4 = 0.47 μ F ^{Note 2}		Vdd		V
V _{L2} voltage	VL2	C1 to C4 = 0.47 µF ^{Note 2}	2/3 V _{L4} – 0.1	2/3 VL4	2/3 V _{L4} + 0.1	V
V∟1 voltage	V _{L1}	C1 to C4 = 0.47 µF ^{Note 2}	1/3 V _{L4} – 0.1	1/3 VL4	1/3 V _{L4} + 0.1	V
Capacitor split wait time ^{Note 1}	tvwait		100			ms

Notes 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

2. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between $V_{\mbox{\tiny L1}}$ and GND

C3: A capacitor connected between $V_{\mbox{\tiny L2}}$ and GND

C4: A capacitor connected between $V_{{\mbox{\tiny L4}}}$ and GND

C1 = C2 = C3 = C4 = 0.47 μ F ± 30%



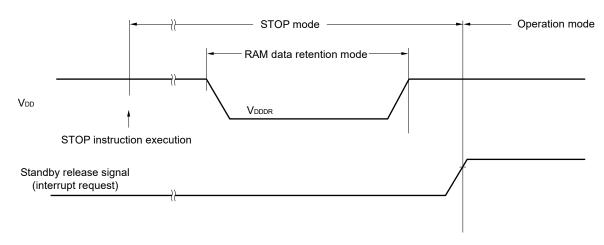
2.8 RAM Data Retention Characteristics

(T_A = -40 to +85°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.

Caution Data in RAM are not retained if the CPU operates outside the specified operating voltage range. Therefore, place the CPU in STOP mode before the operating voltage drops below the specified range.



2.9 Flash Memory Programming Characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclк	1.8 V ≤ VDD ≤ 5.5 V	1		24	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years T _A = 85°C	1,000			Times
Number of data flash rewrites ^{Notes 1, 2, 3}		Retained for 1 year T _A = 25°C		1,000,000		
		Retained for 5 years $T_A = 85^{\circ}C$	100,000			
		Retained for 20 years T _A = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. This characteristic indicates the flash memory characteristic and based on Renesas Electronics reliability test.

Remark When updating data multiple times, use the flash memory as one for updating data.

2.10 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

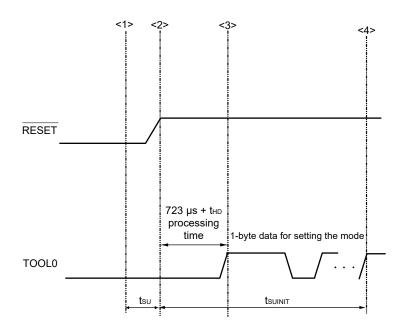


RL78/L13

2.11 Timing Specifications for Switching Flash Memory Programming Modes

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	ts∪	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and completion the baud rate setting.
- **Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.
 - $t_{\mbox{\scriptsize SU:}}$ Time to release the external reset after the TOOL0 pin is set to the low level
 - the: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

3. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to +105°C)

This chapter describes the following electrical specifications. Target products G: Industrial applications $T_A = -40$ to $+105^{\circ}C$

> R5F10WLAGFB, R5F10WLCGFB, R5F10WLDGFB, R5F10WLEGFB, R5F10WLFGFB, R5F10WLGGFB R5F10WMAGFB, R5F10WMCGFB, R5F10WMDGFB, R5F10WMEGFB, R5F10WMFGFB, R5F10WMGGFB

- Cautions 1. The RL78/L13 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 With functions for each product in the RL78/L13 User's Manual.
 - Consult Renesas salesperson and distributor for derating when the product is used at T_A = +85°C to +105°C. Note that derating means "systematically lowering the load from the rated value to improve reliability".
- **Remark** When RL78/L13 is used in the range of $T_A = -40$ to $+85^{\circ}C$, see **CHAPTER 2 ELECTRICAL** SPECIFICATIONS ($T_A = -40$ to $+85^{\circ}C$).



Fields of Application	A: Consumer applications	G: Industrial applications
Operating ambient temperature	$T_{A} = -40 \text{ to } +85^{\circ}\text{C}$	TA = -40 to +105°C
Operation mode operating voltage range	HS (high-speed main) mode: 2.7 V \leq V _{DD} \leq 5.5 V@1 MHz to 24 MHz 2.4 V \leq V _{DD} \leq 5.5 V@1 MHz to 16 MHz LS (low-speed main) mode: 1.8 V \leq V _{DD} \leq 5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V \leq V _{DD} \leq 5.5 V@1 MHz to 4 MHz	HS (high-speed main) mode only: 2.7 V \leq V _{DD} \leq 5.5 V@1 MHz to 24 MHz 2.4 V \leq V _{DD} \leq 5.5 V@1 MHz to 16 MHz
High-speed on-chip oscillator clock accuracy	$\begin{array}{l} 1.8 \ V \leq V_{DD} \leq 5.5 \ V: \\ \pm 1.0 \ \% \ @ \ TA = -20 \ to \ +85^{\circ}C \\ \pm 1.5 \ \% \ @ \ TA = -40 \ to \ -20^{\circ}C \\ 1.6 \ V \leq V_{DD} < 1.8 \ V: \\ \pm 5.0 \ \% \ @ \ TA = -20 \ to \ +85^{\circ}C \\ \pm 5.5 \ \% \ @ \ TA = -40 \ to \ -20^{\circ}C \end{array}$	2.4 V \leq V _{DD} \leq 5.5 V: ±2.0 % @ T _A = +85 to +105°C ±1.0 % @ T _A = -20 to +85°C ±1.5 % @ T _A = -40 to -20°C
Serial array unit	UART Simplified SPI (CSI): fcLk/2 (16 Mbps supported), fcLk/4 Simplified I ² C	UART Simplified SPI (CSI): fcLK/4 Simplified I ² C
IICA	Standard mode Fast mode Fast mode plus	Standard mode Fase mode
Voltage detector	 Rising: 1.67 V to 4.06 V (14 levels) Falling: 1.63 V to 3.98 V (14 levels) 	 Rising: 2.61 V to 4.06 V (8 levels) Falling: 2.55 V to 3.98 V (8 levels)

"G: Industrial applications (T_A = -40 to +105°C) differ from "A: Consumer applications" in function as follows:

Remark Electrical specifications of G: Industrial applications (T_A = -40 to +105°C) differ from "A: Consumer applications". For details, see **3.1** to **3.11** below.



3.1 Absolute Maximum Ratings

Absolute	Maximum	Ratings	(1/3)
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Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V_{DD} +0.3^{Note 1}	V
Input voltage	Vii	P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P121 to P127, P130, P137	-0.3 to V _{DD} +0.3 ^{Note 2}	V
	V _{I2}	P60 and P61 (N-ch open-drain)	-0.3 to +6.5	V
	VI3	EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	V ₀₁	P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P121 to P127, P130, P137	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	Val1	ANI0, ANI1, ANI16 to ANI26	-0.3 to V_{DD} +0.3 and -0.3 to AV_{REF(+)} +0.3^{Notes 2, 3}	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed $AV_{REF(+)}$ + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** AV_{REF (+)}: + side reference voltage of the A/D converter.
 - 3. Vss: Reference voltage



Parameter	Symbol		Conditions	Ratings	Unit
LCD voltage	VL1	V _{L1} voltage ^{Note 1}	VL1 voltage ^{Note 1}		V
	VL2	VL2 voltage ^{Note 1}		-0.3 to VL4 +0.3 ^{Note 2}	V
	VL3	VL3 voltage ^{Note 1}		-0.3 to V _{L4} +0.3 ^{Note 2}	V
	VL4	VL4 voltage ^{Note 1}		-0.3 to +6.5	V
	VLCAP	CAPL, CAPH voltage ^{Note 1}		-0.3 to VL4 +0.3 ^{Note 2}	V
	Vout	COM0 to COM7	External resistance division method	-0.3 to V _{DD} +0.3 ^{Note 2}	V
		SEG0 to SEG50	Capacitor split method	-0.3 to V _{DD} +0.3 ^{Note 2}	V
		output voltage	Internal voltage boosting method	-0.3 to VL4 +0.3 ^{Note 2}	V

Absolute Maximum Ratings (2/3)

- Notes 1. This value only indicates the absolute maximum ratings when applying voltage to the V_{L1}, V_{L2}, V_{L3}, and V_{L4} pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to Vss via a capacitor (0.47 μF ± 30%) and connect a capacitor (0.47 μF ± 30%) between the CAPL and CAPH pins.
 - **2.** Must be 6.5 V or lower.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Vss: Reference voltage



Parameter	Symbol		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P125 to P127, P130	-40	mA
		Total of all pins –170 mA	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P125 to P127, P130	-170	mA
	Іон2	Per pin	P20, P21	-0.5	mA
		Total of all pins		-1	mA
Output current, low	lol1	Per pin	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P125 to P127, P130	40	mA
		Total of all pins	P40 to P47, P130	70	mA
		170 mA	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P50 to P57, P60, P61, P70 to P77, P125 to P127	100	mA
	IOL2	Per pin	P20, P21	1	mA
		Total of all pins		2	mA
Operating ambient	TA	In normal operation	on mode	-40 to +105	°C
temperature		In flash memory p	programming mode		°C
Storage temperature	Tstg			–65 to +150	°C

Absolute Maximum Ratings (TA = 25°C) (3/3)

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.



3.2 Oscillator Characteristics

3.2.1 X1 and XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	1.0		20.0	MHz
frequency (fx) ^{Note}	crystal resonator	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	1.0		16.0	
XT1 clock oscillation frequency (fxT) ^{Note}	Crystal resonator		32	32.768	35	kHz

- **Note** Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.
- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- Remark When using the X1 oscillator and XT1 oscillator, see 5.4 System Clock Oscillator in the RL78/L13 User's Manual.



3.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditions			TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	fін			1		24	MHz
High-speed on-chip oscillator		+85 to +105°C	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	-2		+2	%
clock frequency accuracy		–20 to +85°C	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	-1		+1	%
		–40 to –20°C	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	-1.5		+1.5	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. The high-speed on-chip oscillator frequency is selected by bits 0 to 4 of the option byte (000C2H/010C2H) and bits 0 to 2 of the HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for the instruction execution time.



3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	2.4 V ≤ V _{DD} ≤ 5.5 V			-3.0 ^{Note 2}	mA
		Total of P00 to P07, P10 to P17,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			-45.0	mA
		P22 to P27, P30 to P35, P40 to P47, P50	$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}$			-15.0	mA
		to P57, P70 to P77, P125 to P127, P130 (When duty = 70% ^{Note 3})	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$			-7.0	mA
	Іон2	Per pin for P20 and P21	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty = 70% ^{Note 3})	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			-0.2	mA

Notes 1. Value of the current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin

- 2. Do not exceed the total current value.
- 3. Output current value under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IOH × 0.7)/(n × 0.01)

<Example> Where n = 80% and IoH = -45.0 mA

Total output current of pins = (-45.0 × 0.7)/(80 × 0.01) = -39.375 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 do not output high level in N-ch open-drain mode.



Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	lol1	Per pin for P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130				8.5 ^{Note 2}	mA
		Per pin for P60 and P61				15.0 ^{Note 2}	mA
		Total of P40 to P47, P130	$4.0~\text{V} \leq \text{V}_\text{DD} \leq 5.5~\text{V}$			40.0	mA
		(When duty = 70% ^{Note 3})	$2.7~\text{V} \leq \text{V}_{\text{DD}} < 4.0~\text{V}$			15.0	mA
			$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$			9.0	mA
		Total of P00 to P07, P10 to P17,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			60.0	mA
		P22 to P27, P30 to P35, P50 to P57, P70 to P77, P125 to P127	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$			35.0	mA
		(When duty = $70\%^{\text{Note 3}}$)	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$			20.0	mA
		Total of all pins (When duty = 70% ^{Note 3})				100.0	mA
	IOL2	Per pin for P20 and P21				0.4 ^{Note 2}	mA
		Total of all pins (When duty = 70% ^{Note 3})	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			0.8	mA

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

- Notes 1. Value of the current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin
 - 2. Do not exceed the total current value.
 - **3.** Output current value under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoL × 0.7)/(n × 0.01)
- <Example> Where n = 80% and IoL = 40.0 mA

Total output current of pins = $(40.0 \times 0.7)/(80 \times 0.01) = 35.0 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.



Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	ViH1	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130, P137	Normal input buffer	0.8Vdd		Vdd	V
	VIH2	P03, P05, P06, P16, P17, P34, P43, P44, P46, P47, P53, P55	TTL input buffer 4.0 V ≤ V _{DD} ≤ 5.5 V	2.2		Vdd	V
			TTL input buffer $3.3 V \le V_{DD} < 4.0 V$	2.0		VDD VDD VDD 6.0	V
			TTL input buffer 1.5 2.4 V ≤ V _{DD} < 3.3 V	Vdd	V		
	VIH3	P20, P21		0.7Vdd		Vdd	V
	VIH4	P60, P61		0.7Vdd		6.0	V
	VIH5	P121 to P124, P137, EXCLK, EXCLKS	S, RESET	0.8Vdd		Vdd	V
Input voltage, low	VIL1	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130, P137	Normal input buffer	0		VDD 0.2VDD	V
	VIL2	P03, P05, P06, P16, P17, P34, P43, P44, P46, P47, P53, P55	TTL input buffer 4.0 V ≤ V _{DD} ≤ 5.5 V	0		0.8	V
			TTL input buffer $3.3 V \le V_{DD} < 4.0 V$	0		0.5	V
			TTL input buffer 2.4 V ≤ V _{DD} < 3.3 V	0		0.32	V
	VIL3	P20, P21		0		0.3VDD	V
	VIL4	P60, P61		0		0.3VDD	V
	VIL5	P121 to P124, P137, EXCLK, EXCLKS	, RESET	0		0.2VDD	V

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

- Caution The maximum value of V_I of pins P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 is V_{DD}, even in the N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57,	4.0 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −3.0 mA	Vdd - 0.7			V
		P70 to P77, P125 to P127, P130	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OH1}} = -2.0 \text{ mA}$	Vdd - 0.6			V
			2.4 V ≤ V _{DD} ≤ 5.5 V, I _{OH1} = −1.5 mA	Vdd - 0.5			V
	V _{OH2} P20 and P2	P20 and P21	2.4 V ≤ V _{DD} ≤ 5.5 V, I _{OH2} = −100 μA	Vdd - 0.5			V
Output voltage, low	Vol1	P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	$4.0 V \le V_{DD} \le 5.5 V$, $I_{OL1} = 8.5 mA$			0.7	V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 3.0 \text{ mA}$			0.6	V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 1.5 \text{ mA}$			0.4	V
			$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 0.6 \text{ mA}$			0.4	V
	Vol2	P20 and P21	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL2}} = 400 \ \mu\text{A}$			0.4	V
	Vol3	P60 and P61	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL3}} = 15.0 \text{ mA}$			2.0	V
			$4.0 V \le V_{DD} \le 5.5 V$, $I_{OL3} = 5.0 mA$			0.4	V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL3}} = 3.0 \text{ mA}$			0.4	V
			$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL3}} = 2.0 \text{ mA}$			0.4	V

Caution P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 do not output high level in N-ch open-drain mode.



Parameter	Symbol	Condition	าร		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Іцні	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130, P137	5, 7,				1	μA
	ILIH2	P20 and P21, RESET	$V_I = V_{DD}$				1	μA
	Іцнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port mode and when external clock is input			1	μA
				Resonator connected			10 µA	μA
Input leakage current, low	ILIL1	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130, P137	Vi = Vss				-1	μA
	ILIL2	P20 and P21, RESET	VI = VSS				-1	μA
	Ililis	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = Vss	In input port mode and when external clock is input			-1	μA
				Resonator connected			-10	μA
On-chip pull-up resistance	Ruı	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P45 to P47, P50 to P57, P70 to P77, P125 to P127, P130	Vi = Vss		10	20	100	kΩ
	Ru2	P40 to P44	VI = Vss		10	20	100	kΩ



3.3.2 Supply current characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	(1/2 Unit
Supply	IDD1 ^{Note 1}	Operating	HS (high-	fносо = 48 MHz ^{Note 3} ,	Basic	V _{DD} = 5.0 V	IVIIIN.	2.0	IVIAA.	mA
current	וטטו	mode	speed main)	$f_{\rm IH} = 24 \text{ MHz}^{\rm Note 3}$	operation	$V_{DD} = 3.0 V$		2.0		mA
			mode ^{Note 5}		Normal	V _{DD} = 5.0 V		3.8	7.0	mA
					operation	$V_{DD} = 3.0 V$		3.8	7.0	mA
				fносо = 24 MHz ^{Note 3} ,	Basic	VDD = 5.0 V		1.7	7.0	mA
				$f_{\rm IH} = 24 \text{ MHz}^{\rm Note 3}$	operation	V _{DD} = 3.0 V		1.7		mA
					Normal	V _{DD} = 5.0 V		3.6	6.5	mA
					operation	V _{DD} = 3.0 V		3.6	6.5	mA
				fносо = 16 MHz ^{Note 3} ,	Normal	V _{DD} = 5.0 V		2.7	5.0	mA
				$f_{\rm IH} = 16 \rm MHz^{Note 3}$		V _{DD} = 3.0 V		2.7	5.0	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.0	5.4	mA
			speed main)		operation	Resonator connection		3.2	5.6	mA
			mode ^{Note 5}	f _{MX} = 20 MHz ^{Note 2} , Normal	Square wave input		2.9	5.4	mA	
				V _{DD} = 3.0 V	operation	Resonator connection		3.2	5.6	mA
				f _{MX} = 10 MHz ^{Note 2} ,	Normal	Square wave input		1.9	3.2	mA
	$V_{DD} = 5.0 \text{ V}$ $f_{MX} = 10 \text{ MHz}^{\text{Note 2}}$	V _{DD} = 5.0 V	operation	Resonator connection		1.9	3.2	mA		
		f _{MX} = 10 MHz ^{Note 2} ,	Normal	Square wave input		1.9	3.2	mA		
				V _{DD} = 3.0 V	operation	Resonator connection		1.9	3.2	mA
			Subsystem	fsuв =	Normal	Square wave input		4.0	5.4	μA
			clock operation	32.768 kHz ^{Note 4} , o T _A = -40°C	operation	Resonator connection		4.3	5.4	μA
				fsuв =	Normal	Square wave input		4.0	5.4	μA
				32.768 kHz ^{Note 4} , T _A = +25°C	⁴ , operation R	Resonator connection		4.3	5.4	μA
				fsuв =	Normal	Square wave input		4.1	7.1	μA
				32.768 kHz ^{Note 4} , T _A = +50°C	operation	Resonator connection		4.4	7.1	μA
				fsuв =	Normal	Square wave input		4.3	8.7	μA
T _A = +70°C f _{SUB} = 32.768 kHz	32.768 kHz ^{Note 4} , T _A = +70°C	operation	Resonator connection		4.7	8.7	μA			
		Normal	Square wave input		4.7	12.0	μA			
	32.768 kHz ^{Note 4} , T _A = +85°C	operation	Resonator connection		5.2	12.0	μA			
				fsuв =	Normal	Square wave input		6.4	35.0	μA
				32.768 kHz ^{Note 4} , T _A = +105°C	operation	Resonator connection		6.6	35.0	μA

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main) mode.
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the LCD controller/driver, A/D converter, LVD circuit, comparator, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the real-time clock 2.

- 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- 3. When high-speed system clock and subsystem clock are stopped.
- **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When setting ultra-low power consumption oscillation (AMPHS1 = 1).
- 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 24 MHz
 2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fHOCO: High-speed on-chip oscillator clock frequency (48 MHz max.)
 - 3. fin: High-speed on-chip oscillator clock frequency (24 MHz max.)
 - **4.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 5. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

(2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	DD2Note 2	HALT	HS (high-	fHOCO = 48 MHz ^{Note 4} ,	V _{DD} = 5.0 V		0.71	2.55	mA
current ^{Note 1}		mode	speed main) mode ^{Note 6}	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 3.0 V		0.71	2.55	mA
				fносо = 24 MHz ^{Note 4} ,	V _{DD} = 5.0 V		0.49	1.95	mA
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 3.0 V		0.49	1.95	mA
				fносо = 16 MHz ^{Note 4} ,	V _{DD} = 5.0 V		0.43	1.50	mA
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 3.0 V		0.43	1.50	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$ $V_{\text{DD}} = 5.0 \text{ V}$	Square wave input		0.31	1.76	mA
			speed main) mode ^{Note 6}		Resonator connection		0.48	1.92	mA
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.29	1.76	mA
				V _{DD} = 3.0 V	Resonator connection		0.48	1.92	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.20	0.96	mA
				V _{DD} = 5.0 V	Resonator connection		0.28	1.07	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.19	0.96	mA
				V _{DD} = 3.0 V	Resonator connection		0.28	1.07	mA
		Subsystem	fsue = 32.768 kHz ^{Note 5} ,	Square wave input		0.34	0.62	μA	
		clock	$T_{A} = -40^{\circ}C$	Resonator connection		0.51	0.80	μA	
			operation	f _{SUB} = 32.768 kHz ^{Note 5} , T _A = +25°C	Square wave input		0.38	0.62	μA
					Resonator connection		0.57	0.80	μA
				f _{SUB} = 32.768 kHz ^{Note 5} , T _A = +50°C	Square wave input		0.46	2.30	μA
					Resonator connection		0.67	2.49	μA
				fsuв = 32.768 kHz ^{Note 5} ,	Square wave input		0.65	4.03	μA
				T _A = +70°C	Resonator connection		0.91	4.22	μA
				fsuв = 32.768 kHz ^{Note 5} ,	Square wave input		1.00	8.04	μA
				T _A = +85°C	Resonator connection		1.31	8.23	μA
				fsub = 32.768 kHz ^{Note 5} ,	Square wave input		3.05	27.00	μA
				T _A = +105°C	Resonator connection		3.24	27.00	μA
	IDD3	STOP	T _A = -40°C				0.18	0.52	μA
		mode ^{Note 7}	T _A = +25°C				0.24	0.52	μA
			T _A = +50°C				0.33	2.21	μA
			T _A = +70°C				0.53	3.94	μA
		T _A = +85°C	λ = +85°C			0.93	7.95	μA	
			T _A = +105°C				2.91	25.00	μA

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main) mode.
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the LCD controller/driver, A/D converter, LVD circuit, comparator, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the real-time clock 2.

In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- 2. During HALT instruction execution by flash memory.
- 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- 4. When high-speed system clock and subsystem clock are stopped.
- When high-speed on-chip oscillator and high-speed system clock are stopped.
 When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 24 MHz
 - $2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}_{\odot} 1 \text{ MHz}$ to 16 MHz
- 7. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

- 2. fHOCO: High-speed on-chip oscillator clock frequency (48 MHz max.)
- 3. fin: High-speed on-chip oscillator clock frequency (24 MHz max.)
- **4.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C



$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol		Conditi	ons		MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	I _{FIL} Note 1						0.20		μA
RTC2 operating current	RTC ^{Notes 1, 2, 3}	fsuв = 32.768 kHz					0.02		μA
12-bit interval timer operating current	I _{TMKA} Notes 1, 2, 4						0.04		μA
Watchdog timer operating current	WDT ^{Notes 1, 2, 5}	f⊪ = 15 kHz					0.22		μA
A/D converter operating current	ADC ^{Notes 1, 6}	When conversion at maximum speed	-	e, AV _{REFP} = Vi mode. AV _{REFF}	DD = 5.0 V $P = V_{DD} = 3.0 V$		1.3 0.5	1.7 0.7	mA mA
A/D converter reference voltage current	ADREF ^{Note 1}						75.0		μA
Temperature sensor operating current	_{TMPS} Note 1						75.0		μA
LVD operating current	ILVD ^{Notes 1, 7}						0.08		μA
Comparator	ICMP ^{Notes 1, 11}	V _{DD} = 5.0 V,	Window mod	le			12.5		μA
operating current		Regulator output	Comparator	high-speed m	node		6.5		μA
		voltage = 2.1 V	Comparator	low-speed mo	ode		1.7		μA
		V _{DD} = 5.0 V,	Window mod	le			8.0		μA
		Regulator output voltage = 1.8 V	Comparator	high-speed m	node		4.0		μA
		Voltage = 1.0 V	Comparator	low-speed mo	ode		1.3		μA
Self- programming operating current	_{FSP} Notes 1, 9						2.00	12.20	mA
BGO operating current	BGO ^{Notes 1, 8}						2.00	12.20	mA
SNOOZE	ISNOZ ^{Note 1}	ADC operation	While the mo	ode is shifting	Note 10		0.50	0.60	mA
operating current			0	conversion, in P = V _{DD} = 3.0	0		1.20	1.44	mA
		Simplified SPI (CSI)/	UART operati	on			0.70	0.84	mA
LCD operating current	_{LCD1} Notes 1, 12, 13	External resistance division method	fьcd = fsub LCD clock = 128 Hz	1/3 bias, four time slices	V _{DD} = 5.0 V, V _{L4} = 5.0 V		0.04	0.20.	μA
	I _{LCD2} Note 1, 12	Internal voltage boosting method	f _{LCD} = f _{SUB} LCD clock = 128 Hz	1/3 bias, four time slices	$V_{DD} = 3.0 V,$ $V_{L4} = 3.0 V$ $(V_{LCD} = 04H)$		0.85	2.20	μA
					$V_{DD} = 5.0 V,$ $V_{L4} = 5.1 V$ $(V_{LCD} = 12H)$		1.55	3.70	μA
	I _{LCD3} Note 1, 12	Capacitor split method	fьcd = fsub LCD clock = 128 Hz	1/3 bias, four time slices	V _{DD} = 3.0 V, V _{L4} = 3.0 V		0.20	0.50	μA

(Notes and Remarks are listed on the next page.)



- Notes 1. Current flowing to VDD.
 - 2. When high speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the real-time clock 2 (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The value of the current for the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock 2 operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of real-time clock 2.
 - 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The value of the current for the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and ITMKA, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
 - 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.
 - **6.** Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.
 - 7. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit operates.
 - 8. Current flowing only during data flash rewrite.
 - 9. Current flowing only during self programming.
 - 10. For shift time to the SNOOZE mode, see 21.3.3 SNOOZE mode in the RL78/L13 User's Manual.
 - **11.** Current flowing only to the comparator circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ICMP when the comparator circuit operates.
 - 12. Current flowing only to the LCD controller/driver. The value of the current for the RL78 microcontrollers is the sum of the supply current (IDD1 or IDD2) and LCD operating current (ILCD1, ILCD2, or ILCD3), when the LCD controller/driver operates in operation mode or HALT mode. However, not including the current flowing into the LCD panel. Conditions of the TYP. value and MAX. value are as follows.
 - Setting 20 pins as the segment function and blinking all
 - Selecting fsub for system clock when LCD clock = 128 Hz (LCDC0 = 07H)
 - Setting four time slices and 1/3 bias
 - **13.** Not including the current flowing into the external division resistor when using the external resistance division method.
- **Remarks 1.** fil: Low-speed on-chip oscillator clock frequency
 - **2.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fcLK: CPU/peripheral hardware clock frequency
 - **4.** The temperature condition for the TYP. value is $T_A = 25^{\circ}C$.



3.4 AC Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol		Co	nditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсч	Main system	HS (high	n-speed	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.0417		1	μs
instruction execution time)		clock (fmain) operation	main) m	ode	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs
		Subsystem clock (fsub) $2.4 V \le V_{DD} \le 5.5 V$ operation			28.5	30.5	31.3	μs	
		In the self	HS (high	n-speed	$2.7~V \leq V_{DD} \leq 5.5~V$	0.0417		1	μs
		programming mode	main) m	ode	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs
External system clock	fex	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		1.0		20.0	MHz		
frequency		$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$				1.0		16.0	MHz
	fexs							35	kHz
External system clock input	texн, texL	$2.7 V \leq V_{DD} \leq \xi$	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			24			ns
high-level width, low-level		$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$				30			ns
width	texhs, texls					13.7			μs
TI00 to TI07 input high-level width, low-level width	t⊤ıн, t⊤ı∟					1/fмск+ 10			ns
TO00 to TO07, TKBO00 ^{Note} ,	fто	HS (high-speed main) mode		4.0 V ≤	V _{DD} ≤ 5.5 V			12	MHz
TKBO01-0 to TKBO01-2 ^{Note}				2.7 V ≤	V _{DD} < 4.0 V			8	MHz
output frequency				$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$				4	MHz
PCLBUZ0, PCLBUZ1 output	f PCL	HS (high-spee	d main)	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$				16	MHz
frequency		mode		2.7 V ≤ V _{DD} < 4.0 V				8	MHz
				$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$				4	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0 to INTP	97	2.4 V ≤	V _{DD} ≤ 5.5 V	1			μs
Key interrupt input high-level width, low-level width	tkrh, tkrl	KR0 to KR7		2.4 V ≤	$V_{DD} \leq 5.5 V$	250			ns
IH-PWM output restart input high-level width	tihr	INTP0 to INTP	7			2			fськ
TMKB2 forced output stop input high-level width	tihr	INTP0 to INTP	2			2			fськ
RESET low-level width	trsl					10			μs

(Note and Remark are listed on the next page.)

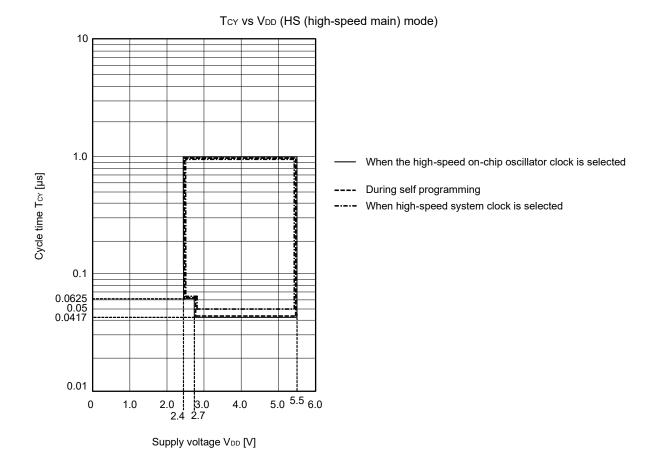


Note Specification under conditions where the duty factor is 50%.

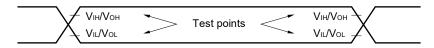
Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn) m: Unit number (m = 0), n: Channel number (n = 0 to 7))

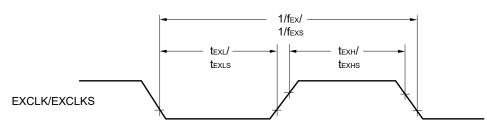
Minimum Instruction Execution Time during Main System Clock Operation



AC Timing Test Points

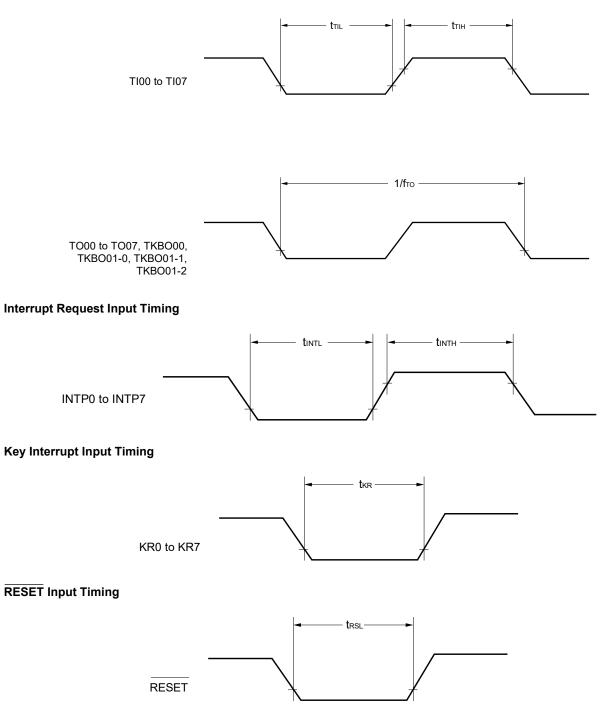


External System Clock Timing





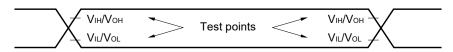
TI/TO Timing





3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

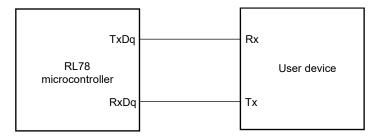
(1) During communication at same potential (UART mode) ($T_A = -40$ to +105°C, 2.4 V $\leq V_{DD} \leq 5.5$ V, Vss = 0 V)

Parameter	Symbol	Conditions	Conditions HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate ^{Note}				fмск/12	bps
		Theoretical value of the maximum transfer rate f_{CLK} = 24 MHz, f_{MCK} = f_{CLK}		2.0	Mbps

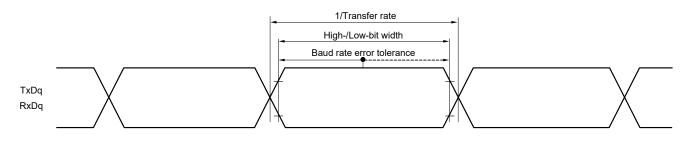
Note Transfer rate in the SNOOZE mode is 4800 bps only.

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)

2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions	HS (high-spee	ed main) Mode	Unit
			MIN.	MAX.	
SCKp cycle time	tkcy1	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	334 ^{Note 1}		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	500 ^{Note 1}		ns
SCKp high-/low-level width	t кн1,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	tксү1/2 — 24		ns
	tĸ∟1	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	tксү1/2 — 36		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	tксү1/2 — 76		ns
SIp setup time (to SCKp↑) ^{Note 2}	tsıĸı	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	66		ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	66		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	113		ns
SIp hold time (from SCKp↑) ^{Note 3}	tksi1		38		ns
Delay time from SCKp↓ to SOp output ^{Note 4}	tkso1	C = 30 pF ^{Note 5}		50	ns

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Notes 1. The value must also be equal to or more than 4/fcLK.

- **2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **5.** C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. p: CSI number (p = 00, 10), m: Unit number (m = 0), n: Channel number (n = 0, 2), g: PIM and POM numbers (g = 0, 1)
 - fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02))



(3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Con	ditions	HS (high-spee	d main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time ^{Note 5}	t ксү2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	fмск > 20 MHz	16/fмск		ns
			fмск ≤ 20 MHz	12/fмск		ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	fмск > 16 MHz	16/fмск		ns
			fмск ≤ 16 MHz	12/fмск		ns
		$2.4 V \le V_{DD} \le 5.5 V$		12/fмск and 1000		ns
SCKp high-/low-level width	tкн2, tкL2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tĸcy2/2–14		ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tксү2/2–16		ns
		2.4 V ≤ V _{DD} ≤ 5.5 V		tkcy2/2–36		ns
SIp setup time	tsik2	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		1/fмск+40		ns
(to SCKp↑) ^{Note 1}		2.4 V ≤ V _{DD} ≤ 5.5 V		1/fмск+60		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi2			1/fмск+62		ns
Delay time from SCKp↓ to	tkso2	C = 30 pF ^{Note 4}	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		2/fмск+66	ns
SOp output ^{Note 3}			$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		2/fмск+113	ns

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

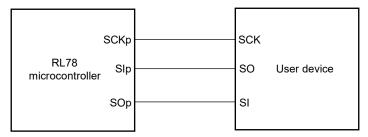
- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SOp output lines.
- 5. Transfer rate in SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

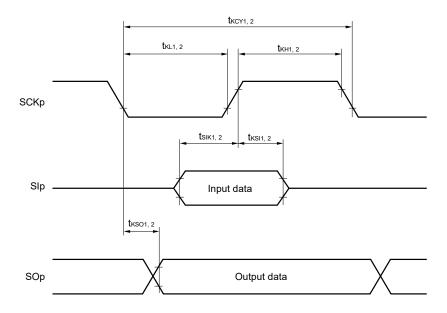
- **Remarks 1.** p: CSI number (p = 00, 10), m: Unit number (m = 0), n: Channel number (n = 0, 2), g: PIM number (g = 0, 1)
 - fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02))



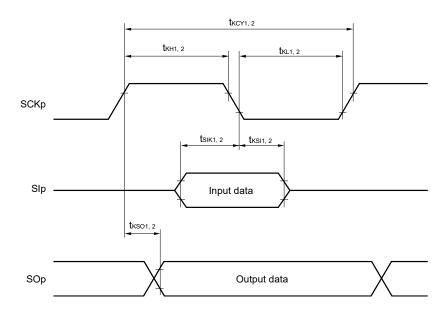
Simplified SPI (CSI) mode connection diagram (during communication at same potential)

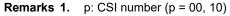


Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)





2. m: Unit number, n: Channel number (mn = 00, 02)



Parameter	Symbol	Conditions	HS (high-speed	l main) Mode	Unit
			MIN.	MAX.	
SCLr clock frequency	fsc∟	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega$		400 ^{Note 1}	kHz
		$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 3 \text{ k}\Omega$		100 ^{Note 1}	kHz
Hold time when SCLr = "L"	tLOW	2.7 V \leq V _{DD} \leq 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	1200		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 3 \text{ k}\Omega$	4600		ns
Hold time when SCLr = "H"	tніgн	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega$	1200		ns
		$2.4 V \le V_{DD} \le 5.5 V$, $C_b = 100 \text{ pF}$, $R_b = 3 \text{ k}\Omega$	4600		ns
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega$	1/f _{MCK} + 220 ^{Note 2}		ns
		$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 3 \text{ k}\Omega$	1/f _{MCK} + 580 ^{Note 2}		ns
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega$	0	770	ns
		$2.4 V \le V_{DD} \le 5.5 V$, $C_b = 100 \text{ pF}$, $R_b = 3 \text{ k}\Omega$	0	1420	ns

(4) During communication at same potential (simplified I²C mode)



Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

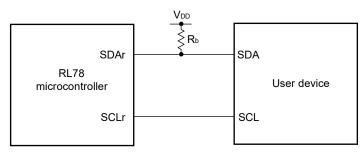
2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg).

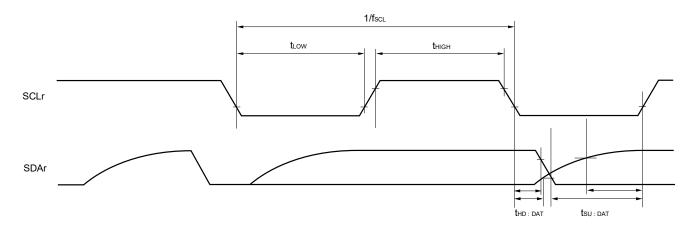
(Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- **Remarks 1.** R_b[Ω]: Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance
 - **2.** r: IIC number (r = 00, 10), g: PIM and POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0-3), mn = 00-03, 10-13)



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-spee	ed main) Mode	Unit
				MIN.	MAX.	
Transfer rate		Reception	$4.0 V \le V_{DD} \le 5.5 V,$ $2.7 V \le V_b \le 4.0 V$		fмск/12 ^{Note}	bps
			Theoretical value of the maximum transfer rate f_{CLK} = 24 MHz, f_{MCK} = f_{CLK}		2.0	Mbps
			$2.7 V \le V_{DD} < 4.0 V,$ $2.3 V \le V_b \le 2.7 V$		fмск/12 ^{Note}	bps
		Theoretical value of the maximum transfer rate f_{CLK} = 24 MHz, f_{MCK} = f_{CLK}		2.0	Mbps	
			$2.4 V \le V_{DD} < 3.3 V,$ $1.6 V \le V_b \le 2.0 V$		fмск/12 ^{Note}	bps
			Theoretical value of the maximum transfer rate f_{CLK} = 24 MHz, f_{MCK} = f_{CLK}		2.0	Mbps

Note Transfer rate in SNOOZE mode is 4800 bps only.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

- **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)
- fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

(T_A = −40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol		Conditions	HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate		Transmission	$4.0 V \le V_{DD} \le 5.5 V,$ $2.7 V \le V_b \le 4.0 V$		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 k Ω , V_b = 2.7 V		2.0 ^{Note 2}	Mbps
			$2.7 V \le V_{DD} < 4.0 V,$ $2.3 V \le V_b \le 2.7 V$		Note 3	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 k Ω , V_b = 2.3 V		1.2 ^{Note 4}	Mbps
			$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		Note 5	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 k Ω , V_b = 1.6 V		0.43 ^{Note 6}	Mbps

Notes 1. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \,[\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- **3.** The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq V_DD < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.



Notes 5. The smaller maximum transfer rate derived by using f_{MCK}/12 or the following expression is the valid maximum transfer rate.

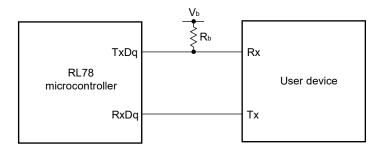
Expression for calculating the transfer rate when 2.4 V \leq V_DD < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

Maximum transfer rate = $\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$ [bps]

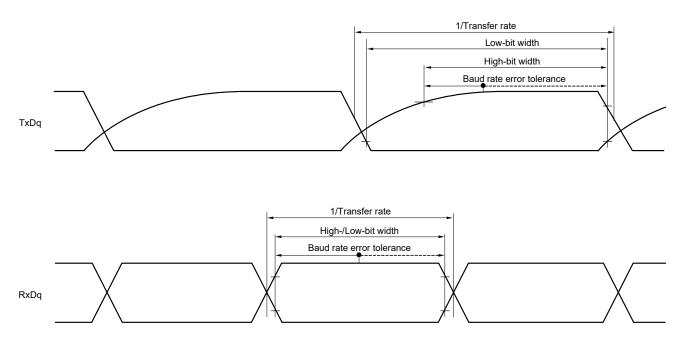
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 5** above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)







UART mode bit width (during communication at different potential) (reference)

- **Remarks 1.** R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage
 - 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output) (1/2)

Parameter	Symbol Conditions		HS (high-speed	Unit		
				MIN.	1	
SCKp cycle time	tkcy1	tксү1 ≥ 4/fc∟к		600		ns
			$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1000		ns
			$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 1.8 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	2300		ns
SCKp high-level width	tкнı	4.0 V ≤ V _{DD} ≤ C _b = 30 pF, F	£ 5.5 V, 2.7 V ≤ V♭ ≤ 4.0 V, R♭ = 1.4 kΩ	tксү1/2 – 150		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$ 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}, $ R _b = 2.7 kΩ	tkcy1/2 - 340		ns
			$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$			ns
SCKp low-level width	tĸ∟1			tkcy1/2 - 24		ns
				tkcy1/2 - 36		ns
		2.4 V ≤ V _{DD} < C _b = 30 pF, F	: 3.3 V, 1.6 V ≤ V♭ ≤ 2.0 V, ₨ = 5.5 kΩ	tkcy1/2 – 100		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸ1	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$		162		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$ 4.0 V, 2.3 V \le V_b \le 2.7 V, $ $ R_b = 2.7 kΩ $	354		ns
		$\begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \; 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$		958		ns
SIp hold time (from SCKp↑) ^{Note 1}	tksi1	4.0 V ≤ V _{DD} ≤ C _b = 30 pF, F	5.5 V, 2.7 V ≤ V₅ ≤ 4.0 V, R₅ = 1.4 kΩ	38		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$4.0 V, 2.3 V \le V_b \le 2.7 V,$ R _b = 2.7 kΩ	38		ns
		$\label{eq:VDD} \begin{split} 2.4 \ V &\leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V, \\ C_{\text{b}} &= 30 \ \text{pF}, \ R_{\text{b}} = 5.5 \ \text{k}\Omega \end{split}$		38		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	4.0 V ≤ V _{DD} ≤ C _b = 30 pF, F	$ 5.5 V, 2.7 V \le V_b \le 4.0 V, $ $ R_b = 1.4 kΩ $		200	ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$ 4.0 V, 2.3 V \le V_b \le 2.7 V, $ $ R_b = 2.7 kΩ $		390	ns
		2.4 V ≤ V _{DD} < C _b = 30 pF, F	 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, R_b = 5.5 kΩ 		966	ns

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

(Note, Caution and Remark are listed on the next page.)

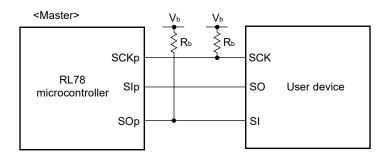


(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output) (2/2)

Parameter	Symbol	Conditions	HS (high-spe	Unit	
			MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note 2}	tsiĸ1	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 20 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	88		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	88		ns
		$\begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \; 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	220		ns
SIp hold time (from SCKp↓) ^{Note 2}	tksi1	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 20 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	38		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	38		ns
		$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	38		ns
Delay time from SCKp↑ to SOp output ^{Note 2}	tkso1	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 20 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$		50	ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		50	ns
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V},$ $C_{b} = 30 \text{ pF}, R_{b} = 5.5 \text{ k}\Omega$		50	ns

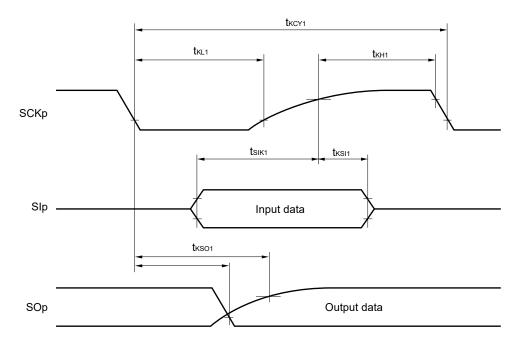
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

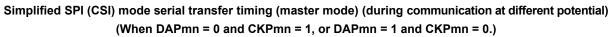


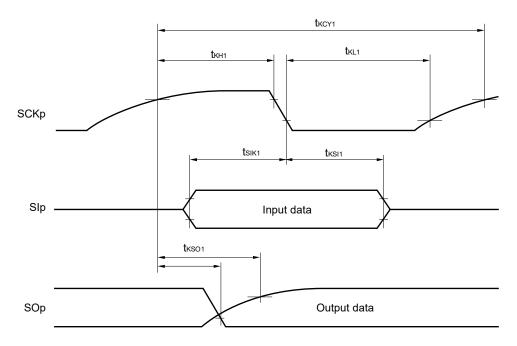
- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
 - 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - p: CSI number (p = 00, 10), m: Unit number, n: Channel number (mn = 00, 02),
 g: PIM and POM number (g = 0, 1)
 - fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

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Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark p: CSI number (p = 00, 10), m: Unit number, n: Channel number (mn = 00, 02), g: PIM and POM number (g = 0, 1)

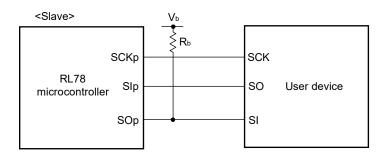
(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Conditions		HS (high-spe	ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tксү2	$4.0 V \le V_{DD} \le 5.5 V$,	20 MHz < fмск	24/f мск		ns
		$2.7~V \leq V_b \leq 4.0~V$	8 MHz < fмск ≤ 20 MHz	20/f мск		ns
			4 MHz < fмск ≤ 8 MHz	16/ f мск		ns
			fмск ≤ 4 MHz	12/f мск		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	20 MHz < fмск	32/f мск		ns
		$2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}$	16 MHz < fмск ≤ 20 MHz	28/f мск		ns
			8 MHz < fмск ≤ 16 MHz	24/f мск		ns
			4 MHz < fмск ≤ 8 MHz	16/f мск		ns
			fмск ≤ 4 MHz	12/fмск		ns
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V},$	20 MHz < fмск	72/f мск		ns
	1.6 V ≤ V _b ≤ 2.0 V	16 MHz < fмск ≤ 20 MHz	64/f мск		ns	
			8 MHz < fмск ≤ 16 MHz	52/f мск		ns
			4 MHz < fмск ≤ 8 MHz	32/f мск		ns
			fмск ≤ 4 MHz	20/f мск		ns
SCKp high-/low-level width	tkh2, tkl2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$, 2.7 V \leq V _b \leq 4.0 V	tkcy2/2 – 24		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}$, 2.3 V \leq V _b \leq 2.7 V	tkcy2/2 – 36		ns
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$, 1.6 V ≤ V _b ≤ 2.0 V	tксү2/2 – 100		ns
SIp setup time	tsik2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$, 2.7 V \leq V _b \leq 4.0 V	1/fмск + 40		ns
(to SCKp↑) ^{Note 2}		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}$, 2.3 V \leq V _b \leq 2.7 V	1/fмск + 40		ns
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		1/fмск + 60		ns
SIp hold time	tĸsı2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$, 2.7 V \leq V _b \leq 4.0 V	1/fмск + 62		ns
(from SCKp↑) ^{Note 3}		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 4.0 \text{ V}$, 2.3 V ≤ V _b ≤ 2.7 V	1/fмск + 62		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 3.3 \text{ V}$, 1.6 V ≤ V _b ≤ 2.0 V	1/fмск + 62		ns
Delay time from SCKp↓ to tksoz SOp output ^{Note 4}	tkso2	$4.0 V \le V_{DD} \le 5.5 V$ $C_b = 30 \text{ pF}, R_b = 1.4$, 2.7 V ≤ V♭ ≤ 4.0 V, 4 kΩ		2/fмск + 240	ns
		$2.7 V \le V_{DD} < 4.0 V$ $C_b = 30 \text{ pF}, R_b = 2.7$, 2.3 V ≤ V♭ ≤ 2.7 V, 7 kΩ		2/fмск + 428	ns
		$2.4 V \le V_{DD} < 3.3 V$ $C_b = 30 \text{ pF}, R_b = 5.8$, 1.6 V ≤ V₅ ≤ 2.0 V, 5 kΩ		2/fмск + 1146	ns

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

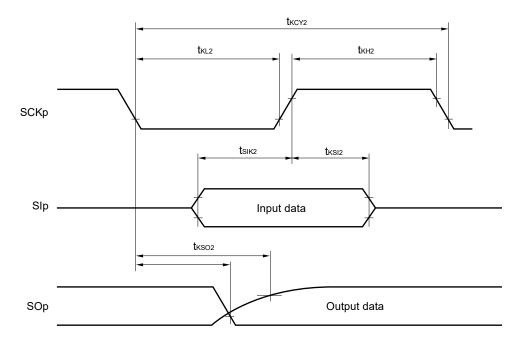
(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

Simplified SPI (CSI) mode connection diagram (during communication at different potential)



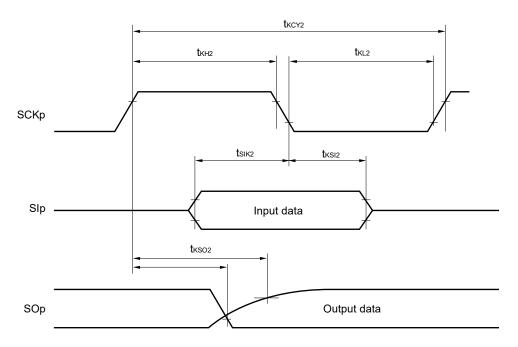
- **Notes 1.** Transfer rate in SNOOZE mode: MAX. 1 Mbps
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.





Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- Remarks 1. $R_b[\Omega]$: Communication line (SOp) pull-up resistance, $C_b[F]$: Communication line (SOp) load capacitance, $V_b[V]$: Communication line voltage
 - p: CSI number (p = 00, 10), m: Unit number, n: Channel number (mn = 00, 02), g: PIM and POM number (g = 0, 1)
 - fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn)
 m: Unit number, n: Channel number (mn = 00, 02))

RENESAS

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (1/2)

Parameter	Symbol	Conditions	HS (high-spe	Unit	
			MIN.	MAX.	
SCLr clock frequency	fsc∟			400 ^{Note 1}	kHz
				400 ^{Note 1}	kHz
				100 ^{Note 1}	kHz
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		100 ^{Note 1}	kHz
		$\begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \; 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$		100 ^{Note 1}	kHz
Hold time when SCLr = "L"	t.ow		1200		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1200		ns
			4600		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	4600		ns
		$\begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \; 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	4650		ns
Hold time when SCLr = "H"	tніgн		620		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	500		ns
			2700		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	2400		ns
		$\begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \; 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	1830		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)



0

1215

ns

Parameter	Symbol	Conditions	HS (high-speed	Unit		
			MIN.	MAX.	1	
Data setup time (reception)	tsu:dat		1/f _{MCK} + 340 ^{Note 2}		ns	
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/f _{MCK} + 340 ^{Note 2}		ns	
		$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_{b} \leq 4.0 \; V, \\ C_{b} = 100 \; pF, \; R_{b} = 2.8 \; k\Omega \end{array}$	1/f _{мск} + 760 ^{Note 2}		ns	
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/f _{мск} + 760 ^{Note 2}		ns	
		$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	1/f _{мск} + 570 ^{Note 2}		ns	
Data hold time (transmission)	thd:dat	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	770	ns	
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	770	ns	
		$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_{b} \leq 4.0 \; V, \\ C_{b} = 100 \; pF, \; R_{b} = 2.8 \; k\Omega \end{array}$	0	1420	ns	
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	1420	ns	

 $2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$

 C_b = 100 pF, R_b = 5.5 k Ω

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

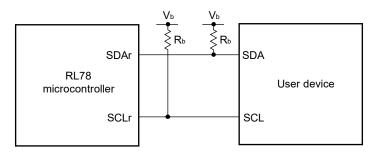
2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

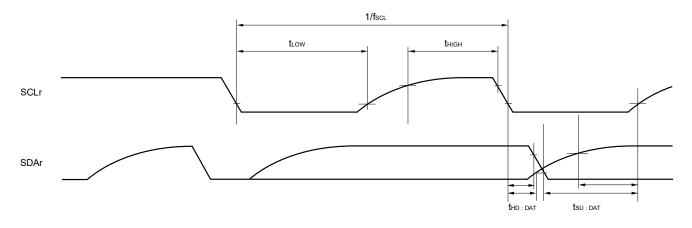
(**Remarks** are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remarks 1.** R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage
 - **2.** r: IIC number (r = 00, 10), g: PIM, POM number (g = 0, 1)
 - fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02)



3.5.2 Serial interface IICA

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS	HS (high-speed main) Mode		Unit	
			Standar	d Mode	Fast Mode		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fsc∟	Fast mode: fc∟κ≥ 3.5 MHz	-	_	0	400	kHz
		Normal mode: fc∟k ≥ 1 MHz	0	100	_	_	kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μs
Hold time ^{Note 1}	thd:sta		4.0		0.6		μs
Hold time when SCLA0 = "L"	t∟ow		4.7		1.3		μs
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μs
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	3.45	0	0.9	μs
Setup time of stop condition	tsu:sto		4.0		0.6		μs
Bus-free time	t BUF		4.7		1.3		μs

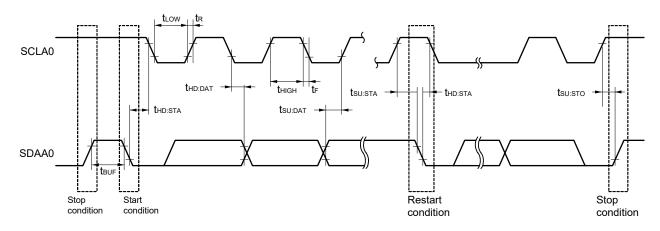
Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the:DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

 $\begin{array}{lll} \mbox{Standard mode:} & C_b = 400 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ } k\Omega \\ \mbox{Fast mode:} & C_b = 320 \mbox{ pF}, \mbox{ R}_b = 1.1 \mbox{ } k\Omega \\ \end{array}$

IICA serial transfer timing





3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage	Reference voltage (+) = AV _{REFP} Reference voltage (–) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (–) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (–) = AV _{REFM}
ANIO, ANI1	_	See 3.6.1 (2) .	See 3.6.1 (3) .
ANI16 to ANI25	See 3.6.1 (1) .		
Internal reference voltage Temperature sensor output voltage	See 3.6.1 (1) .		_

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pins: ANI16 to ANI25, internal reference voltage, and temperature sensor output voltage

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = 100 \text{ cm}^{-1}$:
AV _{REFM} = 0 V)	

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		±1.2	±5.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI16 to ANI25	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.1875		39	μs
			$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
		10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.375		39	μs
		Target pin: Internal reference	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.5625		39	μs
		voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$			±3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±2.0	LSB
Analog input voltage	VAIN	ANI16 to ANI25		0		AVREFP	V
		Internal reference voltage (2.4 V ≤ V₀₀ ≤ 5.5 V, HS (high-speed main) mode))		V _{BGR} Note 4			V
		Temperature sensor output voltage (2.4 V \leq V _{DD} \leq 5.5 V, HS (high-speed main) mode))		,	VTMPS25 ^{Note 4}	L .	V

(Notes are listed on the next page.)



Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.

 Overall error:
 Add ±4 LSB to the MAX. value when AV_{REFP} = V_{DD}.

 Zero-scale error/Full-scale error:
 Add ±0.2%FSR to the MAX. value when AV_{REFP} = V_{DD}.

 Integral linearity error/ Differential linearity error:
 Add ±2 LSB to the MAX. value when AV_{REFP} = V_{DD}.
- 4. See 3.6.2 Temperature sensor/internal reference voltage characteristics.



<R>

(2) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{ss} (ADREFM = 0), target pins: ANI0, ANI1, ANI16 to ANI25, internal reference voltage, and temperature sensor output voltage

					-		-
Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit	
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		±1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin:	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.1875		39	μs
		ANI0, ANI1, ANI16 to ANI25	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
		10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.375		39	μs
		Target pin: Internal reference	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.5625		39	μs
		voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.60	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±4.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±2.0	LSB
Analog input voltage	VAIN	ANI0, ANI1, ANI16 to ANI25		0		Vdd	V
	Internal reference voltage (2.4 V \leq V _{DD} \leq 5.5 V, HS (high Temperature sensor output vo (2.4 V \leq V _{DD} \leq 5.5 V, HS (high	Internal reference voltage (2.4 V ≤ V₀₀ ≤ 5.5 V, HS (high-speed main) mode))			VBGR ^{Note 3}		V
		0	V _{TMPS25} Note 3		V		

(T _A = -40 to +105°C, 2.4 V ≤ V _{DD} ≤ 5.5 V, V _{SS} = 0 V, Reference voltage (+) = V _{DD} , Reference voltage (-) =	Vss)
--	------

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. See 3.6.2 Temperature sensor/internal reference voltage characteristics.



(3) When reference voltage (+) = internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pins: ANI0, ANI16 to ANI25

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{BGR}^{Note 3},$ Reference voltage (-) = AV_{REFM}^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conc	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8		bit
Conversion time	t CONV	8-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±1.0	LSB
Analog input voltage	VAIN			0		$V_{\text{BGR}}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. See 3.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (-) = Vss, the MAX. values are as follows.Zero-scale error:Add $\pm 0.35\%$ FSR to the AVREFM MAX. value.Integral linearity error:Add ± 0.5 LSB to the AVREFM MAX. value.Differential linearity error:Add ± 0.2 LSB to the AVREFM MAX. value.



3.6.2 Temperature sensor/internal reference voltage characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	ADS register = 80H, T _A = +25°C		1.05		V
Internal reference output voltage	VBGR	ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp				5	μs

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{HS (high-speed main) mode)}$

3.6.3 Comparator

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
Input voltage range	lvref			0		Vdd – 1.4	V
	lvcmp			-0.3		V _{DD} + 0.3	V
Output delay	td	V _{DD} = 3.0 V Input slew rate > 50 mV/µs	Comparator high-speed mode, standard mode			1.2	μs
			Comparator high-speed mode, window mode			2.0	μs
			Comparator low-speed mode, standard mode		3.0	5.0	μs
High-electric-potential reference voltage	VTW+	Comparator high-speed mode window mode	ə,	0.66Vdd	0.76Vdd	0.86Vdd	V
Low-electric-potential reference voltage	VTW–	Comparator high-speed mode window mode	э,	0.14Vdd	0.24V _{DD}	0.34Vdd	V
Operation stabilization wait time	tсмр			100			μs
Internal reference output voltage ^{Note}	Vbgr	2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-	speed main) mode	1.38	1.45	1.50	V

Note Cannot be used in subsystem clock operation and STOP mode.

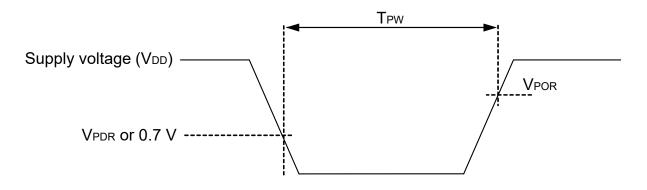


3.6.4 POR circuit characteristics

(T_A = -40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	The power supply voltage is rising.	1.45	1.51	1.57	V
	VPDR	The power supply voltage is falling.	1.44	1.50	1.56	V
Minimum pulse width ^{Note}	TPW		300			μs

Note This is the time required for the POR circuit to execute a reset operation when V_{DD} falls below V_{PDR}. When the microcontroller enters STOP mode and when the main system clock (f_{MAIN}) has been stopped by setting bit 0 (HIOSTOP) and bit 7 (MSTOP) of the clock operation status control register (CSC), this is the time required for the POR circuit to execute a reset operation between when V_{DD} falls below 0.7 V and when V_{DD} rises to V_{POR} or higher.





3.6.5 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	VLVD0	When power supply rises	3.90	4.06	4.22	V
voltage			When power supply falls	3.83	3.98	4.13	V
		VLVD1	When power supply rises	3.60	3.75	3.90	V
			When power supply falls	3.53	3.67	3.81	V
		VLVD2	When power supply rises	3.01	3.13	3.25	V
			When power supply falls	2.94	3.06	3.18	V
		VLVD3	When power supply rises	2.90	3.02	3.14	V
			When power supply falls	2.85	2.96	3.07	V
		VLVD4	When power supply rises	2.81	2.92	3.03	V
			When power supply falls	2.75	2.86	2.97	V
		VLVD5	When power supply rises	2.71	2.81	2.92	V
			When power supply falls	2.64	2.75	2.86	V
		VLVD6	When power supply rises	2.61	2.71	2.81	V
			When power supply falls	2.55	2.65	2.75	V
		VLVD7	When power supply rises	2.51	2.61	2.71	V
			When power supply falls	2.45	2.55	2.65	V
Minimum pu	Ilse width	tLW		300			μs
Detection de	elay time					300	μs



LVD Detection Voltage of Interrupt & Reset Mode

(TA = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVD5	Vpoc2,	VPOC1, VPOC0 = 0, 1, 1,	falling reset voltage	2.64	2.75	2.86	V
mode	VLVD4		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	VLVD3		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V
	VLVD0		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
				Falling interrupt voltage	3.83	3.98	4.13	V

3.6.6 Supply voltage rise time

(T_A = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V _{DD} rise slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.



3.7 LCD Characteristics

3.7.1 External resistance division method

(1) Static display mode

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{L4} \text{ (MIN.)} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.0		Vdd	V

(2) 1/2 bias method, 1/4 bias method

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{L4} \text{ (MIN.)} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.7		Vdd	V

(3) 1/3 bias method

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{L4} \text{ (MIN.)} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.5		Vdd	V



3.7.2 Internal voltage boosting method

(1) 1/3 bias method

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	VL1	C1 to C4 ^{Note 1}	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 µF ^{Note 2}	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	VL2	C1 to C4 ^{Note 1} =	0.47 µF	2 V _{L1} -0.10	2 VL1	2 VL1	V
Tripler output voltage	VL4	C1 to C4 ^{Note 1} = 0.47 µF 3		3 VL1-0.15	3 VL1	3 VL1	V
Reference voltage setup time ^{Note 2}	tvwait1			5			ms
Voltage boost wait time ^{Note 3}	tvwait2	C1 to C4 ^{Note 1} =	0.47 µF	500			ms

Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between $V_{\mbox{\tiny L1}}$ and GND

C3: A capacitor connected between V_{L2} and GND

C4: A capacitor connected between $V_{{\mbox{\tiny L4}}}$ and GND

C1 = C2 = C3 = C4 = 0.47 µF ± 30%

- 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

(2) 1/4 bias method

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	VL1	C1 to C5 ^{Note 1}	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 µF ^{Note 2}	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
Doubler output voltage	VL2	C1 to C5 ^{Note 1} =	0.47 µF	2 VL1-0.08	2 VL1	2 VL1	V
Tripler output voltage	VL3	C1 to C5 ^{Note 1} =	0.47 µF	3 VL1-0.12	3 VL1	3 VL1	V
Quadruply output voltage	VL4	C1 to C5 ^{Note 1} =	0.47 µF	4 VL1-0.16	4 VL1	4 VL1	V
Reference voltage setup time ^{Note 2}	tvwait1			5			ms
Voltage boost wait time ^{Note 3}	tvwait2	C1 to C5 ^{Note 1} =	0.47 µF	500			ms

Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

- C2: A capacitor connected between V_{L1} and GND
- C3: A capacitor connected between V_{L2} and GND
- C4: A capacitor connected between $V_{\mbox{\tiny L3}}$ and GND
- C5: A capacitor connected between $V_{\mbox{\tiny L4}}$ and GND
- $C1 = C2 = C3 = C4 = C5 = 0.47 \ \mu\text{F} \pm 30\%$
- 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).



3.7.3 Capacitor split method

(1) 1/3 bias method

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
VL4 voltage	VL4	C1 to C4 = 0.47 µF ^{Note 2}		Vdd		V
VL2 voltage	VL2	C1 to C4 = 0.47 µF ^{Note 2}	2/3 V _{L4} – 0.1	2/3 V _{L4}	2/3 V _{L4} + 0.1	V
V _{L1} voltage	VL1	C1 to C4 = 0.47 µF ^{Note 2}	1/3 V _{L4} – 0.1	1/3 VL4	1/3 V _{L4} + 0.1	V
Capacitor split wait time ^{Note 1}	tvwai⊤		100			ms

Notes 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

2. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between $V_{\mbox{\tiny L1}}$ and GND

C3: A capacitor connected between $V_{\mbox{\tiny L2}}$ and GND

C4: A capacitor connected between $V_{{\scriptscriptstyle L4}}$ and GND

C1 = C2 = C3 = C4 = 0.47 pF±30 %

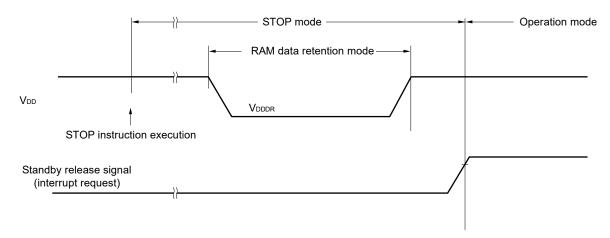


3.8 RAM Data Retention Characteristics

(T_A = -40 to +105°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.9 Flash Memory Programming Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclĸ	2.4 V ≤ VDD ≤ 5.5 V	1		24	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years T _A = 85°C ^{Note 4}	1,000			Times
Number of data flash rewrites ^{Notes 1, 2, 3}		Retained for 1 year T _A = 25°C		1,000,000		
		Retained for 5 years $T_A = 85^{\circ}C^{Note 4}$	100,000			-
		Retained for 20 years T _A = 85°C ^{Note 4}	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- 3. This characteristic indicates the flash memory characteristic and based on Renesas Electronics reliability test.
- 4. This temperature is the average value at which data are retained.

Remark When updating data multiple times, use the flash memory as one for updating data.

3.10 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

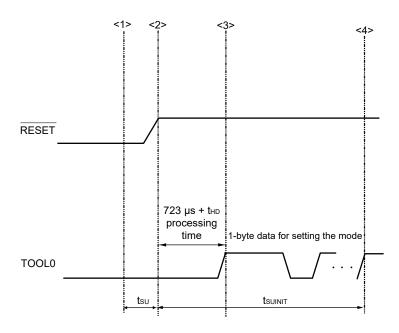
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



3.11 Timing Specifications for Switching Flash Memory Programming Modes

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	ts∪	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and completion the baud rate setting.
- **Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.
 - t_{SU} : Time to release the external reset after the TOOL0 pin is set to the low level
 - the: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

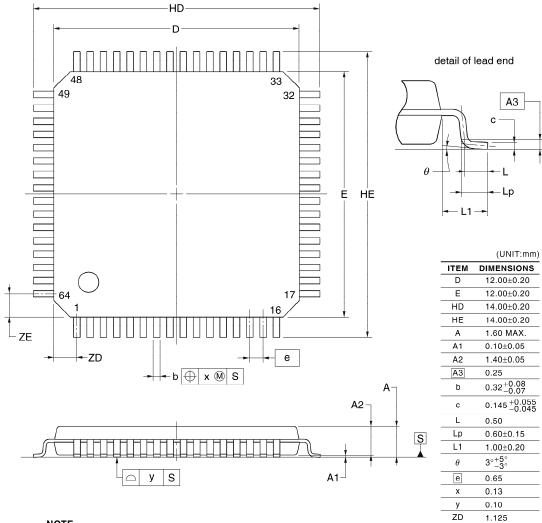


4. PACKAGE DRAWINGS

4.1 64-pin Products

R5F10WLAAFA, R5F10WLCAFA, R5F10WLDAFA, R5F10WLEAFA, R5F10WLFAFA, R5F10WLGAFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51



NOTE

Each lead centerline is located within 0.13 mm of its true position at maximum material condition.

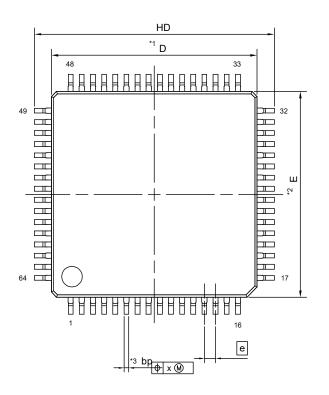
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ZE

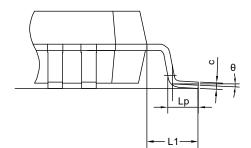
1.125

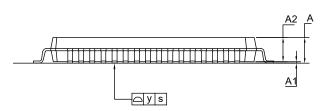


JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LQFP64-12x12-0.65	PLQP0064JB-A	0.50



detail of lead end





NOTE

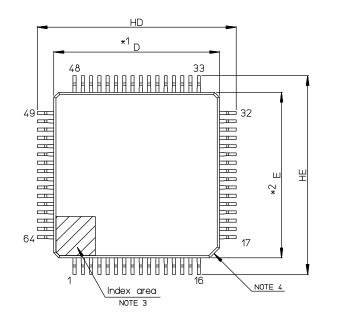
1.DIMENSIONS "*1" AND "*2"DO NOT INCLUDE MOLD FLASH. 2.DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference	Dimen	sion in Milli	imeters
Symbol	Min.	Nom.	Max.
E	11.90	12.00	12.10
D	11.90	12.00	12.10
A ₂	-	1.40	-
H _D	13.80	14.00	14.20
H _E	13.80	14.00	14.20
А	_	—	1.70
A ₁	0.05	—	0.15
Lp	0.45	0.60	0.75
L1		1.00	—
b _p	0.27	0.32	0.37
с	0.09	—	0.20
е		0.65	-
θ	0.00	3.50	8.00
x		—	0.08
у	_	—	0.08

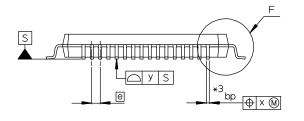


R5F10WLAAFB, R5F10WLCAFB, R5F10WLDAFB, R5F10WLEAFB, R5F10WLFAFB, R5F10WLGAFB, R5F10WLAGFB, R5F10WLCGFB, R5F10WLDGFB, R5F10WLEGFB, R5F10WLFGFB, R5F10WLGGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP64-10x10-0.50	PLQP0064KB-C		0.3g

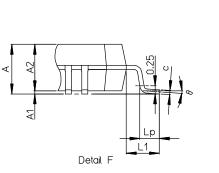






NOTE) DIMENSIONS '*1' AND '*2' DO NOT INCLUDE MOLD FLASH. DIMENSION '*3' DOES NOT INCLUDE TRIM OFFSET. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA. CHAMFERS AT CORNERS ARE OPTIONAL; SIZE MAY VARY. 1. 2. 3.

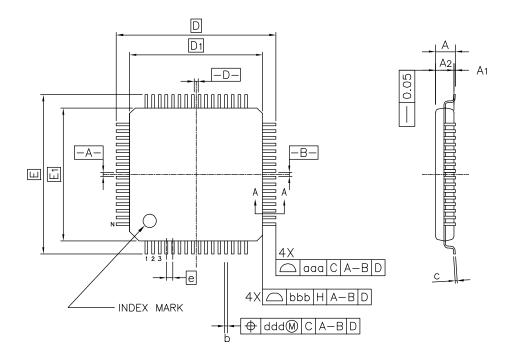
4.

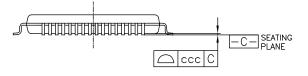


Reference	Dimens	ion in Mil	limeters
Symbol	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A2		1.4	
HD	11.8	12.0	12.2
HE	11.8	12.0	12.2
А			1.7
A1	0.05		0.15
bp	0.15	0.20	0.27
С	0.09		0.20
θ	0"	3.5 [°]	8 "
е		0.5	
×			0.08
У			0.08
Lp	0.45	0.6	0.75
L1		1.0	



JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LFQFP064-10x10-0.50	PLQP0064KL-A	0.36





GAUGE PLANE	
SECTION A-A	

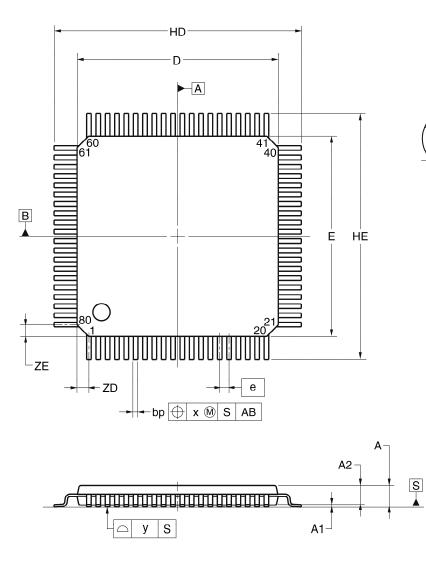
Reference	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.
A	-	-	1.60
A ₁	0.05	—	0.15
A ₂	1.35	1.40	1.45
D	-	12.00	—
D ₁		10.00	—
E	-	12.00	—
E1	-	10.00	—
N		64	—
e	-	0.50	—
b	0.17	0.22	0.27
С	0.09	—	0.20
θ	0°	3.5°	7°
L	0.45	0.60	0.75
L	-	1.00	—
aaa	_	_	0.20
bbb	_	_	0.20
ссс	-	—	0.08
ddd	_	—	0.08

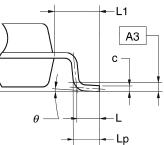


4.2 80-pin Products

R5F10WMAAFA, R5F10WMCAFA, R5F10WMDAFA, R5F10WMEAFA, R5F10WMFAFA, R5F10WMGAFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69

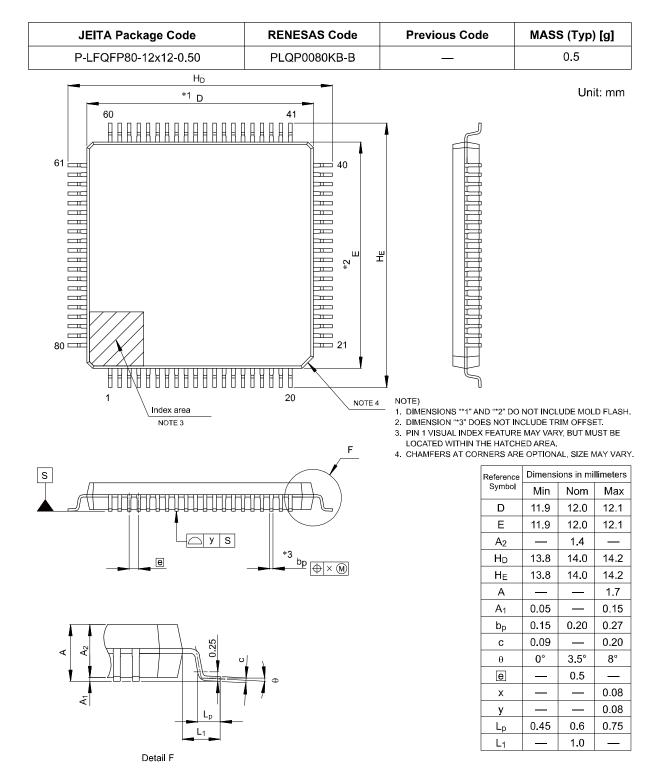




detail of lead end

Referance	Dimension in Millimeters		
Symbol	Min	Nom	Max
D	13.80	14.00	14.20
E	13.80	14.00	14.20
HD	17.00	17.20	17.40
HE	17.00	17.20	17.40
A			1.70
A1	0.05	0.125	0.20
A2	1.35	1.40	1.45
A3		0.25	
bp	0.26	0.32	0.38
с	0.10	0.145	0.20
L		0.80	
Lp	0.736	0.886	1.036
L1	1.40	1.60	1.80
θ	0°	3°	8°
e		0.65	
x			0.13
У			0.10
ZD		0.825	
ZE		0.825	



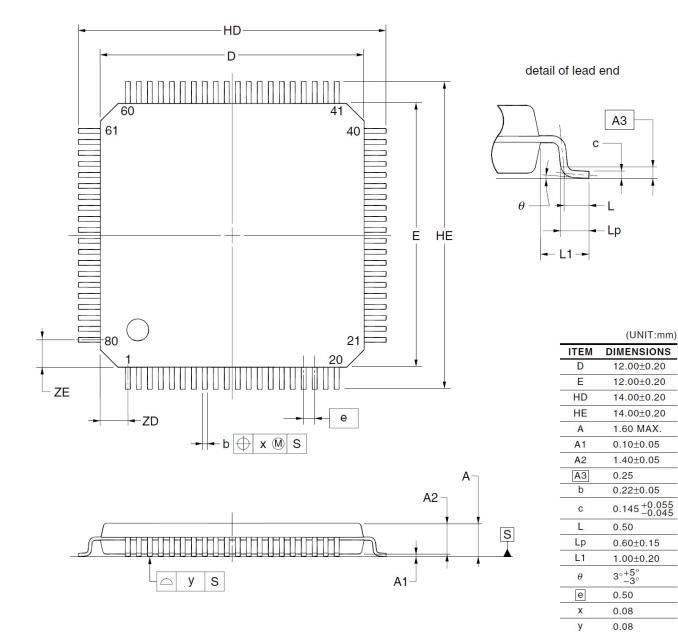


R5F10WMAAFB, R5F10WMCAFB, R5F10WMDAFB, R5F10WMEAFB, R5F10WMFAFB, R5F10WMGAFB, R5F10WMCGFB, R5F10WMCGAFB, R5W10WCGAFB, R5F10WCGAFB, R5W10WCGAFB, R5W10WCGAFA, R5W10WCGAFA, R5W10WCGAFA, R5W10WCGAFA, R5W10WCGAFA, R5W10WCGAFA, R5W10WC

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JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU	0.53



NOTE

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.



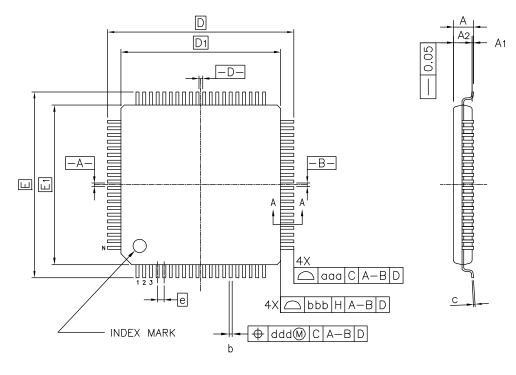
ZD

ZE

1.25

1.25

JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LFQFP80-12x12-0.50	PLQP0080KJ-A	0.49



F

SECTION A-A

Reference	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.
A	_	-	1.60
A ₁	0.05	_	0.15
A ₂	1.35	1.40	1.45
D	—	14.00	—
D ₁	—	12.00	-
E	—	14.00	—
E1	_	12.00	_
N	—	80	—
е	_	0.50	_
b	0.17	0.22	0.27
с	0.09	—	0.20
θ	0°	3.5°	7°
L	0.45	0.60	0.75
Ц	_	1.00	_
aaa	_	_	0.20
bbb	-	_	0.20
ccc	—	—	0.08
ddd	_	_	0.08



Revision History

RL78/L13 Data Sheet

		Description	
Rev.	Date	Page	Summary
0.01	Apr 13, 2012	-	First Edition issued
0.02	Oct 31, 2012	-	Change of the number of segment pins • 64-pin products: 36 pins • 80-pin products: 51 pins
2.10	Aug 12, 2016	1	Modification of features of 16-bit timer and 16-bit timer KB20 (IH) in 1.1 Features
		5	Addition of product name (RL78/L13) and description (Top View) in 1.3.1 64-pin products
		6	Addition of product name (RL78/L13) and description (Top View) in 1.3.2 80-pin products
		10	Modification of functional overview of main system clock in 1.6 Outline of Functions
		15	Modification of description in Absolute Maximum Ratings (3/3)
		17, 18	Modification of description in 2.3.1 Pin characteristics
		38	Modification of remark 3 in 2.5.1 (4) During communication at same potential (simplified I ² C mode)
		68	Modification of the title and note, and addition of caution in 2.8 RAM Data Retention Characteristics
		70	Addition of Remark
		74	Modification of description in Absolute Maximum Ratings (T _A = 25 °C) (3/3)
		76	Modification of description in 3.3.1 Pin characteristics
		95	Modification of remark 3 in 3.5.1 (4) During communication at same potential (simplified I ² C mode)
		118	Modification of the title and note, and addition of caution in 3.8 RAM Data Retention Characteristics
2.20	Sep 17, 2021	3 and 4	Modification of Figure 1-1. Part Number, Memory Size, and Package of RL78/L13
		22	Modification of 2.3.1 Pin characteristics, (T _A = -40 to +85°C, 1.6 V \leq V _{DD} \leq 5.5 V, V _{SS} = 0 V)
		61	Modification of 2.6.1 A/D converter characteristics ($T_A = -40$ to +85°C, 1.6 V $\leq AV_{REFP} \leq V_{DD} \leq 5.5$ V, $V_{SS} = 0$ V, Reference voltage (+) = AV_{REFP} , Reference voltage (–) = $AV_{REFM} = 0$ V)
		74	Modification of 2.11 Timing Specifications for Switching Flash Memory Programming Modes
		75	Deletion of G: INDUSTRIAL APPLICATIONS from the title of CHAPTER 3
		115	3. 5. 2 Serial Interface IICA ($T_A = -40$ to $+105^{\circ}$ C, 2.4 V $\leq V_{DD} \leq 5.5$ V, $V_{SS} = 0$ V): Deletion of Note 3 in the table
		116	Modification of 3.6.1 A/D converter characteristics ($T_A = -40$ to +105°C, 2.4 V $\leq AV_{REFP} \leq V_{DD} \leq 5.5$ V, $V_{SS} = 0$ V, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $AV_{REFM} = 0$ V)
		129	Modification of 3.11 Timing Specifications for Switching Flash Memory Programming Modes

		Description		
Rev. Date		Page Summary		
2.21	Sep 9, 2022	4	Modification of Figure 1-1. Part Number, Memory Size, and Package of RL78/L13	
		131	Addition of package drawing (PLQP0064JB-A).	
		132	Modification of package drawing (PLQP0064KB-C).	
		133	Addition of package drawing (PLQP0064KL-A).	
		135	Modification of package drawing (PLQP0080KB-B).	
		136	Addition of package drawing (PLQP0080KJ-A).	
2.30	Aug 31, 2023	All	"3-Wire Serial I/O" and "3-wire serial" were modified to " Simplified SPI"	
		All	"wait" for IIC was modified to "clock stretch"	
		1	Addition of Note 1 in 1 Features	
		5	Modification of Figure in 1.3.1 64-pin products	
		6, 7	Addition of Table 1-1. Alternate function of 64-pin products	
		8	Modification of Figure in 1.3.2 80-pin products	
		9 to 11	Addition of Table 1-2. Alternate function of 80-pin products	
		29	Modification of Note 1 and Note 4 in 32.3.2 Supply current characteristics ($T_A = -40$ to +85°C, 1.6 V ≤ V _{DD} ≤ 5.5 V, V _{SS} = 0 V) (1/2)	
		31	Modification of Note 1 and Note 5, deletion of Note 6 in 32.3.2 Supply current characteristics ($T_A = -40$ to $+85^{\circ}$ C, 1.6 V $\leq V_{DD} \leq 5.5$ V, $V_{SS} = 0$ V) (2/2)	
		93	Modification of Note 1 and Note 4 in 33.3.2 Supply current characteristics ($T_A = -40$ to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, $V_{SS} = 0$ V) (1/2)	
		95	Modification of Note 1 and Note 5, deletion of Note 6 in 33.3.2 Supply current characteristics ($T_A = -40$ to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) (2/2)	
		136	Modification of package drawing (PLQP0064JB-A).	
2.31	Mar 22, 2024	3	Modification of Figure 1-1. Part Number, Memory Size, and Package of RL78/L13	
		4	Modification of description of table in 1.2 List of Part Numbers	
		141	Addition of package drawing (PLQP0080KE-A)	
2.32	Jan 31, 2025	66	Modification of (1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AVREFM/ANI1 (ADREFM = 1), target pins: ANI16 to ANI25, internal reference voltage, and temperature sensor output voltage	
		68	Modification of (2) When reference voltage (+) = V _{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pins: ANI0, ANI1, ANI16 to ANI25, internal reference voltage, and temperature sensor output voltage	
		121	Modification of (1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AVREFM/ANI1 (ADREFM = 1), target pins: ANI16 to ANI25, internal reference voltage, and temperature sensor output voltage	
		123	Modification of (2) When reference voltage (+) = V _{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V _{SS} (ADREFM = 0), target pins: ANI0, ANI1, ANI16 to ANI25, internal reference voltage, and temperature sensor output voltage	

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The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power is supplied until the power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (Max.) and VIH (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (Max.) and VIH (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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